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(54) **ORGANIC TRANSISTOR, COMPOUND, ORGANIC SEMICONDUCTOR MATERIAL FOR NON-LIGHT-EMITTING ORGANIC SEMICONDUCTOR DEVICE, MATERIAL FOR ORGANIC TRANSISTOR, COATING SOLUTION FOR NON-LIGHT-EMITTING ORGANIC SEMICONDUCTOR DEVICE, METHOD FOR MANUFACTURING ORGANIC TRANSISTOR, METHOD FOR MANUFACTURING ORGANIC SEMICONDUCTOR FILM, ORGANIC SEMICONDUCTOR FILM FOR NON-LIGHT-EMITTING ORGANIC SEMICONDUCTOR DEVICE, AND METHOD FOR SYNTHESIZING ORGANIC SEMICONDUCTOR MATERIAL**

ORGANISCHER TRANSISTOR, VERBINDUNG, ORGANISCHES HALBLEITERMATERIAL FÜR NICHT-LICHTEMITTIERENDES ORGANISCHES HALBLEITERBAUELEMENT, MATERIAL FÜR ORGANISCHEN TRANSISTOR, BESCHICHTUNGSLÖSUNG FÜR NICHT-LICHTEMITTIERENDES ORGANISCHES HALBLEITERBAUELEMENT, VERFAHREN ZUR HERSTELLUNG EINES ORGANISCHEN TRANSISTORS, VERFAHREN ZUR HERSTELLUNG EINER ORGANISCHEN HALBLEITERSCHICHT, ORGANISCHE HALBLEITERSCHICHT FÜR NICHT-LICHTEMITTIERENDES ORGANISCHES HALBLEITERBAUELEMENT UND VERFAHREN ZUR SYNTHETISIERUNG EINES ORGANISCHEN HALBLEITERMATERIALS

TRANSISTOR ORGANIQUE, COMPOSÉ, MATÉRIAU SEMI-CONDUCTEUR ORGANIQUE POUR DISPOSITIF À SEMI-CONDUCTEUR ORGANIQUE NON ÉLECTROLUMINESCENT, MATÉRIAU POUR TRANSISTOR ORGANIQUE, SOLUTION DE REVÊTEMENT POUR DISPOSITIF À SEMI-CONDUCTEUR ORGANIQUE NON ÉLECTROLUMINESCENT, PROCÉDÉ DE FABRICATION DE TRANSISTOR ORGANIQUE, PROCÉDÉ DE FABRICATION DE FILM SEMI-CONDUCTEUR ORGANIQUE, FILM SEMI-CONDUCTEUR ORGANIQUE POUR DISPOSITIF À SEMI-CONDUCTEUR ORGANIQUE NON ÉLECTROLUMINESCENT, ET PROCÉDÉ DE SYNTHÈSE DE MATÉRIAU SEMI-CONDUCTEUR ORGANIQUE

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Remarks:

The file contains technical information submitted after the application was filed and not included in this specification

Description

BACKGROUND OF THE INVENTION

5 1. Field of the Invention

10 [0001] The present invention relates to a compound, an organic semiconductor material for a non-light-emitting organic semiconductor device, a material for an organic transistor, a coating solution for a non-light-emitting organic semiconductor device, a method for manufacturing an organic transistor, a method for manufacturing an organic semiconductor film, an organic semiconductor film for a non-light-emitting organic semiconductor device, and a method for synthesizing an organic semiconductor material. Specifically, the present invention relates to a compound having a fused-ring skeletal structure, an organic transistor containing the compound, an organic semiconductor material for a non-light-emitting organic semiconductor device containing the compound, a material for an organic transistor containing the compound, a coating solution for a non-light-emitting organic semiconductor device containing the compound, a method for manufacturing an organic semiconductor film using the compound, a method for manufacturing an organic transistor using the coating solution for a non-light-emitting organic semiconductor device, an organic semiconductor film for a non-light-emitting organic semiconductor device containing the compound, and a method for synthesizing an organic semiconductor material.

20 2. Description of the Related Art

25 [0002] Devices using organic semiconductor materials are drawing great attention because they are expected to be superior in various aspects to devices using inorganic semiconductor materials of the related art such as silicon. Examples of the devices using organic semiconductor materials include a photoelectric conversion element such as an organic thin-film solar cell or a solid-state imaging element using organic semiconductor materials as photoelectric conversion materials, an organic transistor (referred to as an organic thin-film transistor in some cases) having non-light-emitting properties (in the present specification, "non-light-emitting" refers to properties by which a luminous efficiency of equal to or less than 1 lm/W is obtained in a case where electric currents are applied to a device at a current density of 0.1 mW/cm² at room temperature in the atmosphere; non-light-emitting organic semiconductor devices mean organic semiconductor devices excluding light-emitting organic semiconductor devices such as organic electroluminescence elements), and the like. Compared to the devices using inorganic semiconductor materials, the devices using organic semiconductor materials are likely to make it possible to prepare large area elements at lower temperature and lower costs. Furthermore, the characteristics of the materials can be easily changed by varying the molecular structure thereof. Therefore, the materials show a wide variation and can realize functions or elements that cannot be obtained by inorganic semiconductor materials.

35 [0003] Regarding organic semiconductor materials, the use of compounds having a fused-ring skeletal structure in a semiconductor active layer is examined so as to improve carrier mobility and to improve transistor performances.

40 [0004] For example, CN102206225A describes an organic semiconductor polymer having a fused-ring skeletal structure and a low-molecular weight compound used for synthesizing the organic semiconductor polymer having a fused-ring skeletal structure. In CN102206225A, carrier mobility obtained at the time when the organic semiconductor polymer having a fused-ring skeletal structure is applied to an organic transistor is examined.

45 [0005] Meanwhile, a case is known where a compound having a fused-ring skeletal structure similar to the organic semiconductor polymer having a fused-ring skeletal structure described in CN102206225A is used in an element other than an organic transistor. For example, JP2013-235903A describes a case where an organic semiconductor polymer having a fused-ring skeletal structure is used in a photoelectric conversion layer of an organic thin-film solar cell.

50 [0006] A case is also known where a low-molecular weight compound having a fused-ring skeletal structure similar to the organic semiconductor polymer having a fused-ring skeletal structure described in CN102206225A is used. For example, JP2010-045281A describes an organic electroluminescence element material containing a compound which has, as a partial structure, a fused ring consisting of five aromatic rings having a chalcogen atom-containing aromatic heterocycle as one of the constituents. Furthermore, WO2011/126225A discloses, as a novel compound for an organic electronic material, a compound having a fused-ring skeletal structure consisting of five rings, and discloses a case where the compound is used in an organic electroluminescence element.

55 [0007] JP1988-180960A (JP-S63-180960A) discloses an example of an electrophotographic photoreceptor containing, as a photoconductor, a disazo pigment having a fused-ring skeletal structure.

[0008] In addition, Tetrahedron 66 (2010) 8778-8784 discloses a method for synthesizing a compound C6-TBBT or C12-TBBT obtained by substituting thieno[3,2-f:4,5-f']bis[1]benzothiophene (hereinafter referred to as TBBT as well) with an alkyl group having 6 carbon atoms or an alkyl group having 12 carbon atoms respectively, and discloses absorption/emission spectra and cyclic voltammetry (CV) as physical properties thereof. Although Tetrahedron 66 (2010)

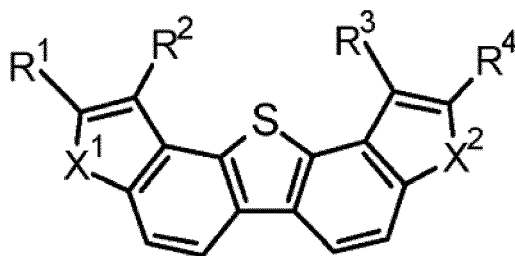
8778-8784 describes the application of the compound to an organic transistor in the introduction part of the document, it does not describe the evaluation of organic transistor characteristics such as mobility.

WO 2015/128779 A1 relates to compounds of formula 1 wherein X1 and X2 are independently from each other O, S or Se, and an electronic device comprising the compounds as semiconducting material.

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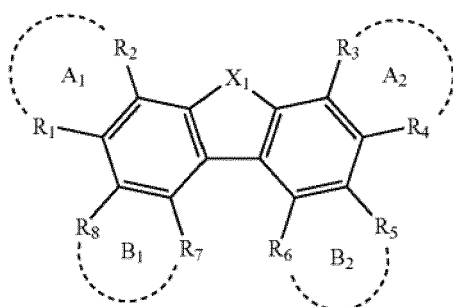
[0009] US2014/034915 A1 relates to a heterocyclic compound represented by Formula 1, as well as an organic light emitting device including a first electrode, a second electrode and an organic layer between the first and second electrodes. The organic layer includes the heterocyclic compound.

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Formula 1

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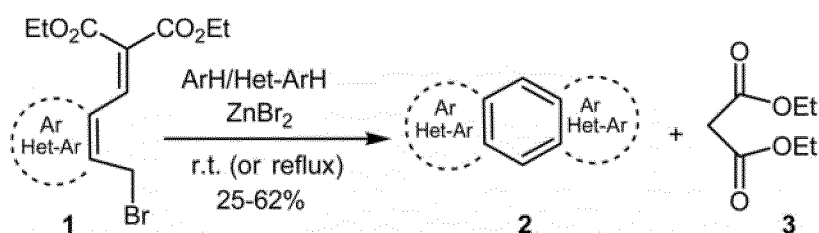


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[0010] Eur. J. Org. Chem. 2011, 922-935 describes the synthesis of aryl/heteroaryl-fused carbazoles according to the following general scheme.

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SUMMARY OF THE INVENTION

[0011] Under the circumstances described above, the inventors of the present invention examined organic transistors using the compounds described in CN102206225A, JP2013-235903A, WO2011/126225A, JP1988-180960A (JP-S63-180960A), and Tetrahedron 66 (2010) 8778-8784. As a result, the inventors found that the organic transistors have low carrier mobility.

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[0012] Therefore, in order to solve the problem of the related art described above, the inventors of the present invention continued examination. An object of the present invention is to provide an organic transistor having high carrier mobility.

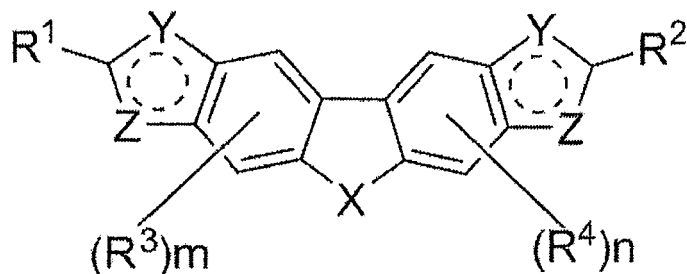
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[0013] As a result of conducting intensive examination for achieving the above object, the inventors obtained knowledge that, by substituting a skeleton having a specific fused-ring structure consisting of five rings with a specific substituent, an organic transistor having high carrier mobility can be obtained. Based on the knowledge, the inventors accomplished the present invention.

[0014] The present invention as specific means for achieving the above object has the following constitution.

[1] An organic transistor comprising a semiconductor active layer which is represented by the following Formula (1) and has a molecular weight of equal to or less than 3,000;

Formula (1)



in Formula (1),

X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR⁵;

Y and Z each independently represent CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷, two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other;

a ring containing Y and Z is an aromatic heterocycle;

any one of R¹ and R² and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups;

any one of R³ and R⁴ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R², R⁵, R⁶, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

R³ and R⁴ each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, in a case where m is 2, R³'s may be the same as or different from each other, and in a case where n is 2, R⁴'s may be the same as or different from each other;

m and n each independently represent an integer of 0 to 2;

here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷ are excluded;

in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R¹ and R² are a hydrogen atom is excluded;

in a case where X is a sulfur atom, Y is CH, Z is a sulfur atom, and both of R¹ and R² are an alkyl group, one of R¹ and R² and the aromatic heterocycle containing Y and Z are bonded to each other through the group A of divalent linking groups; and

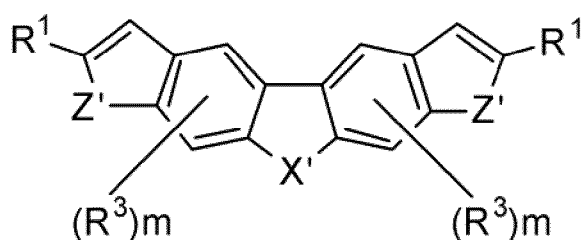
a case where both of R¹ and R² are a hydrogen atom, and both of m and n are 0 is excluded.

[2] The organic transistor described in [1], in which in Formula (1), both of m and n are preferably 0.

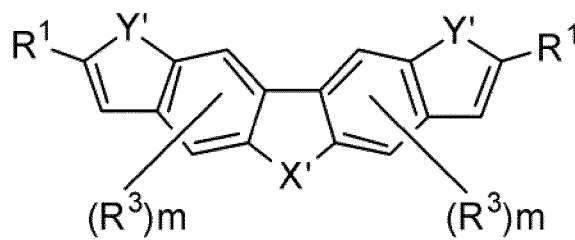
[3] The organic transistor described in [1] or [2], in which in Formula (1), each of R¹ and R² is preferably independently an alkyl group having 20 or less carbon atoms, an aryl group having 20 or less carbon atoms, or a heteroaryl group having 20 or less carbon atoms.

[4] The organic transistor described in any one of [1] to [3], in which the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by the following Formula (2) or (3) and has a molecular weight of equal to or less than 3,000;

Formula (2)



Formula (3)



in Formulae (2) and (3),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

each of Y' and Z' is independently selected from NR⁷, an oxygen atom, a sulfur atom, and a selenium atom; a ring containing Y' and Z' is an aromatic heterocycle;

R¹ and the aromatic heterocycle containing Y' and Z' may be bonded to each other through the following group A of divalent linking groups;

R³ and a benzene ring may be bonded to each other through the following group A of divalent linking groups; the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other;

each R³ independently represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and in a case where m is 2, R³'s may be the same as or different from each other;

each m is independently an integer of 0 to 2;

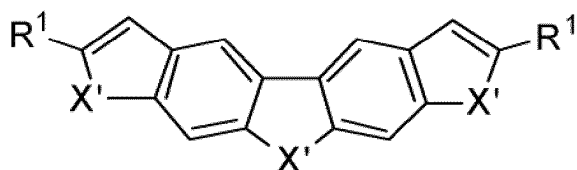
here, a case where both of Y' and Z' are NR⁷ is excluded;

in a case where X', Z', and R¹ in Formula (2) are a sulfur atom, a sulfur atom, and an alkyl group respectively, R¹ and the aromatic heterocycle containing Z' are bonded to each other through the group A of divalent linking groups; and

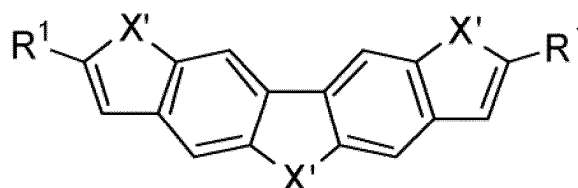
a case where R¹ is a hydrogen atom and all of m's are 0 is excluded.

[5] The organic transistor described in any one of [1] to [4], in which the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by the following Formula (4) or (5) and has a molecular weight of equal to or less than 3,000;

Formula (4)



Formula (5)



in Formulae (4) and (5),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

R¹ and an aromatic heterocycle containing X' may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

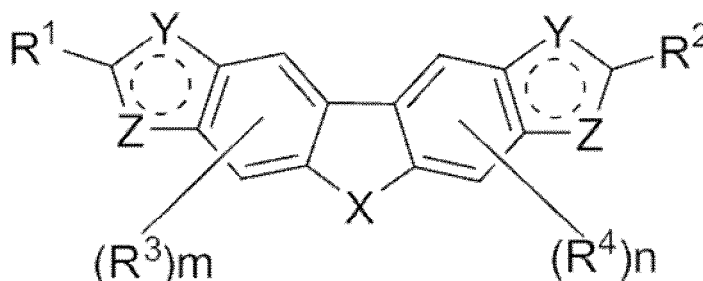
R¹ represents an aryl group having a linear aliphatic hydrocarbon group or a heteroaryl group having a linear aliphatic hydrocarbon group

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R⁸ represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other.

[6] A compound which is represented by the following Formula (1A) and has a molecular weight of equal to or less than 3,000;

Formula (1A)



in Formula (1A),

X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR⁵;

Y and Z each independently represent CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷, two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other;

a ring containing Y and Z is an aromatic heterocycle;

any one of R¹ and R² and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups;

any one of R³ and R⁴ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R², R⁵, R⁶, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

R³ and R⁴ each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, in a case where m is 2, R³'s may be the same as or different from each other, and in a case where n is 2, R⁴'s may be the same as or different from each other;

m and n each independently represent an integer of 0 to 2;

here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷ are excluded;

a case where X is NR⁵, Y is a nitrogen atom, and Z is an oxygen atom is excluded;

in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R¹ and R² are a hydrogen atom is excluded;

in a case where X is a sulfur atom, Y is CH, Z is a sulfur atom, and both of R¹ and R² are an alkyl group, one of R¹ and R² and the aromatic heterocycle containing Y and Z bonded to each other through the group A of divalent linking groups; and

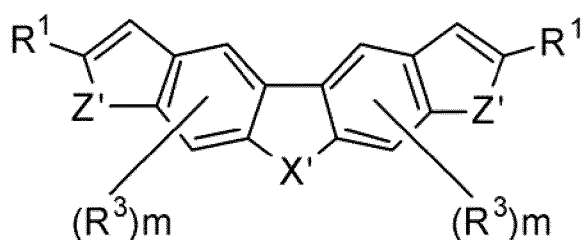
a case where both of R¹ and R² are a hydrogen atom, and both of m and n are 0 is excluded.

[7] The compound described in [6], in which in Formula (1A), both of m and n are preferably 0.

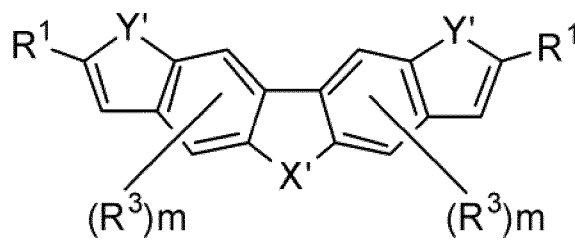
[8] The compound described in [6] or [7], in which in Formula (1A), each of R¹ and R² is preferably independently an alkyl group having 20 or less carbon atoms, an aryl group having 20 or less carbon atoms, or a heteroaryl group having 20 or less carbon atoms.

[9] The compound described in any one of [6] to [8], in which the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by the following Formula (2) or (3) and has a molecular weight of equal to or less than 3,000;

Formula (2)



Formula (3)



in Formulae (2) and (3),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

each of Y' and Z' is independently selected from NR⁷, an oxygen atom, a sulfur atom, and a selenium atom; a ring containing Y' and Z' is an aromatic heterocycle;

R¹ and the aromatic heterocycle containing Y' and Z' may be bonded to each other through the following group A of divalent linking groups;

R³ and a benzene ring may be bonded to each other through the following group A of divalent linking groups; the group A of divalent linking groups represents any one of divalent linking groups among -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹-s may be the same as or different from each other;

each R³ independently represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and in a case where m is 2, R³'s may be the same as or different from each other;

each m is independently an integer of 0 to 2;

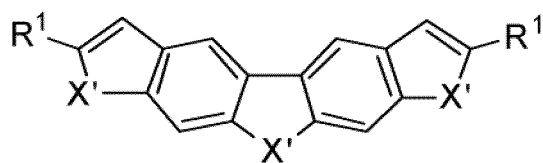
here, a case where both of Y' and Z' are NR⁷ is excluded;

in a case where X', Z', and R¹ in Formula (2) are a sulfur atom, a sulfur atom, and an alkyl group respectively, R¹ and the aromatic heterocycle containing Z' are bonded to each other through the group A of divalent linking groups; and

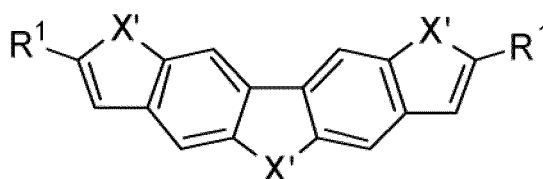
a case where R¹ is a hydrogen atom and all of m's are 0 is excluded.

[10] The compound described in any one of [6] to [9], in which the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by the following Formula (4) or (5) and has a molecular weight of equal to or less than 3,000;

Formula (4)



Formula (5)



in Formulae (4) and (5),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

R¹ and an aromatic heterocycle containing X' may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹ represents an aryl group having a linear aliphatic hydrocarbon group or a heteroaryl group having a linear aliphatic hydrocarbon group

R⁸ represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other.

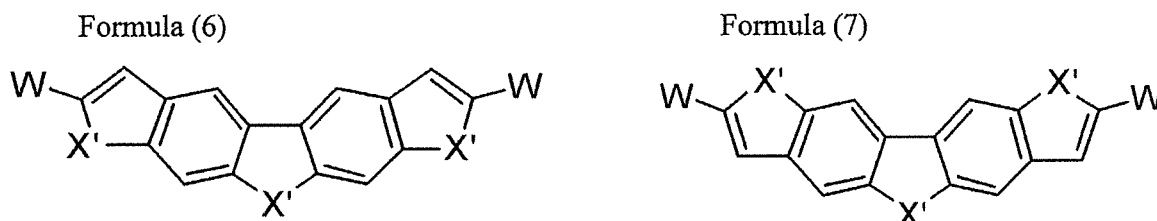
[11] An organic semiconductor material for a non-light-emitting organic semiconductor device containing the compound described in any one of [6] to [10] that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

[12] A coating solution for a non-light-emitting organic semiconductor device containing the compound described in any one of [6] to [10] that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

[13] A method for manufacturing an organic transistor, comprising a step of preparing a semiconductor active layer by coating a substrate with the coating solution for a non-light-emitting organic semiconductor device described in [12] and drying the coating solution.

[14] An organic semiconductor film for a non-light-emitting organic semiconductor device containing the compound described in any one of [6] to [10] that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

[15] A method for synthesizing an organic semiconductor material, in which a compound represented by the following Formula (6) or (7) is reacted with a compound represented by the following Formula (8) by heating in the presence of a transition metal catalyst and an organic solvent such that the compound described in any one of [6] to [10] that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is synthesized;



each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom; and
each W independently represents a halogen atom or a perfluoroalkylsulfonyloxy group;



R¹¹ represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

M represents magnesium, silicon, boron, tin, or zinc;

each R¹² independently represents a halogen atom, an alkyl group, an alkenyl group, an alkynyl group, an alkoxy group, or a hydroxyl group, R¹²'s may be the same as or different from each other and may form a ring; and
i represents an integer of 1 to 3 and equals a valency of M - 1, here, in a case where M is boron, i may be 3.

[0015] According to the present invention, it is possible to provide an organic transistor having high carrier mobility.

BRIEF DESCRIPTION OF THE DRAWINGS

[0016]

Fig. 1 is a schematic view showing a section of an exemplary structure of an organic transistor of the present invention.

Fig. 2 is a schematic view showing a section of the structure of the organic transistor of the present invention.

Figs. 3A to 3C are schematic views showing an example of a method for manufacturing an organic semiconductor film of the present invention. Specifically, Figs. 3A to 3C are schematic views showing an aspect in which in a state where a distance between a substrate A and a member B not being fixed to the substrate A is kept constant, a coating solution is dropped onto a portion within the surface of the substrate A such that the coating solution contacts both of the substrate A and the member B, and the dropped coating solution is slowly dried in a state where the positional relationship between the substrate A and the member B is maintained.

Figs. 4A to 4C are schematic views showing another example of the method for manufacturing an organic semiconductor film of the present invention. Specifically, Figs. 4A to 4C are schematic views showing an aspect in which

in a state where the substrate A and the member B remain in contact with each other, a coating solution is dropped onto a portion within the surface of the substrate A such that the coating solution contacts both of the substrate A and the member B, and the dropped coating solution is slowly dried in a state where the positional relationship between the substrate A and the member B is maintained.

Figs. 5A to 5C are schematic views showing another example of the method for manufacturing an organic semiconductor film of the present invention. Specifically, Figs. 5A to 5C are schematic views showing an aspect in which in a state where the substrate A and the member B remain in contact with each other, a coating solution is dropped onto a portion within the surface of the substrate A such that the coating solution contacts both of the substrate A and the member B, and the dropped coating solution is slowly dried by changing the positional relationship between the substrate A and the member B.

Fig. 6 is a schematic view showing an example of the substrate A and the member B used in the method for manufacturing an organic semiconductor film of the present invention.

DESCRIPTION OF THE PREFERRED EMBODIMENTS

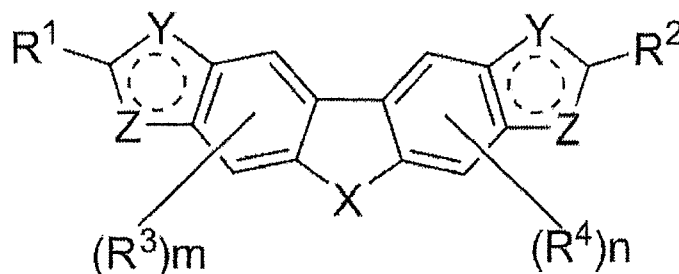
[0017] Hereinafter, the present invention will be specifically described. The constituents described below will be explained based on representative embodiments or specific examples, but the present invention is not limited to the embodiments. In the present specification, a range of numerical values described using "to" means a range including the numerical values listed before and after "to" as a lower limit and an upper limit respectively.

[0018] In the present invention, unless otherwise specified, a hydrogen atom used in the description of each formula represents a hydrogen atom including an isotope (deuterium atom or the like). Furthermore, an atom constituting a substituent represents an atom including an isotope thereof.

[Organic transistor]

[0019] An organic transistor of the present invention contains a compound, which is represented by the following Formula (1) and has a molecular weight of equal to or less than 3,000, in a semiconductor active layer.

Formula (1)



[0020] In Formula (1),

X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR⁵;

Y and Z each independently represent CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷, two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other;

a ring containing Y and Z is an aromatic heterocycle;

any one of R¹ and R² and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups;

any one of R³ and R⁴ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R², R⁵, R⁶, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

R³ and R⁴ each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, in a case where m is 2, R³'s may be the same as or different from each other, and in a case where n is 2, R⁴'s may be the same as or different from each other;

m and n each independently represent an integer of 0 to 2;

here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷

are excluded;

in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R¹ and R² are a hydrogen atom is excluded; in a case where X is a sulfur atom, Y is CH, Z is a sulfur atom, and both of R¹ and R² are an alkyl group, one of R¹ and R² and the aromatic heterocycle containing Y and Z are bonded to each other through the group A of divalent linking groups; and

a case where both of R¹ and R² are a hydrogen atom, and both of m and n are 0 is excluded.

[0021] Due to the above constitution, the organic transistor of the present invention has high carrier mobility.

[0022] The reason why the organic transistor of the present invention has high carrier mobility is not limited and is considered to be as below according to the inventors of the present invention. By the selection of a specific substituent typified by the compound represented by Formula (1) and the selection of a substitution position, overlapping of orbitals between molecules becomes great, anisotropy is reduced, and as a result, carrier mobility can be improved.

[0023] It cannot be said that being useful as a material of an organic electroluminescence (EL) element means being useful as a semiconductor material for an organic transistor. This is because the characteristics required for an organic compound vary between an organic EL element and an organic transistor. A mobility of about 10⁻³ cm²/Vs is enough for driving an organic EL element, and for improving organic EL characteristics, it is more important to improve luminous efficiency than to improve charge transport properties. Therefore, an element having high luminous efficiency and resulting in uniform in-plane luminescence is required. Generally, organic compounds having high crystallinity (high mobility) cause luminescence defectiveness such as non-uniform in-plane field intensity, non-uniform luminescence, and quenching of luminescence. Therefore, as materials for an organic EL element, those having low crystallinity but having high amorphousness (low mobility) are desirable. In contrast, in a semiconductor material for an organic transistor, extremely high mobility is desired. Accordingly, an organic compound showing highly ordered molecular arrangement and having high crystallinity is required.

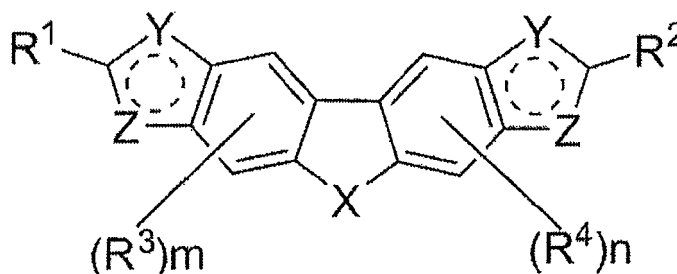
[0024] Furthermore, for the expression of high carrier mobility, a π -conjugate plane is preferably upright against a substrate.

[0025] Hereinafter, preferred aspects of the compound and the organic transistor of the present invention will be described.

[0026] <Compound represented by Formula (1) and having molecular weight of equal to or less than 3,000>

[0027] Hereinafter, the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 will be described.

Formula (1)



[0028] In Formula (1), X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR⁵. From the viewpoint of improving carrier mobility, X is preferably an oxygen atom, a sulfur atom, or a selenium atom, more preferably an oxygen atom or a sulfur atom, and particularly preferably a sulfur atom. In contrast, from the viewpoint of improving solubility, X is preferably a selenium atom.

[0029] In Formula (1), Y and Z each independently represent CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷. Two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other.

[0030] In Formula (1), a ring containing Y and Z is an aromatic heterocycle. Because the ring containing Y and Z is an aromatic heterocycle, for example, there is no case where both of Y and Z are a nitrogen atom and thus the ring becomes a radical compound.

[0031] Here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷ are excluded from the range of Formula (1). In a case where both of Y and Z are CR⁶, the ring does not become an aromatic heterocycle. In a case where both of Y and Z are any one of a nitrogen atom and NR⁷, the highest occupied molecular orbital (HOMO) becomes too deep.

[0032] Each Y independently represents CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷. Y is preferably CR⁶, an oxygen atom, or a sulfur atom, and more preferably CR⁶ or a sulfur atom.

[0033] Two Y's may be the same as or different from each other and are preferably the same as each other.

[0034] Each Z independently represents CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷. Z is preferably CR⁶, an oxygen atom, a sulfur atom, or NR⁷, more preferably CR⁶, an oxygen atom, or a sulfur atom, and particularly preferably CR⁶ or a sulfur atom.

[0035] Two Z's may be the same as or different from each other and are preferably the same as each other.

[0036] Regarding a preferred combination of Y and Z, in a case where Y represents CR⁶, Z is preferably an oxygen atom, a sulfur atom, or NR⁷, more preferably an oxygen atom or a sulfur atom, and particularly preferably a sulfur atom.

[0037] In a case where Y represents an oxygen atom, Z is preferably CR⁶, an oxygen atom, or a sulfur atom, more preferably CR⁶ or a sulfur atom, and particularly preferably CR⁶.

[0038] In a case where Y represents a sulfur atom, Z is preferably CR⁶, an oxygen atom, a sulfur atom, or a nitrogen atom, more preferably CR⁶ or a nitrogen atom, and particularly preferably CR⁶.

[0039] In Formula (1), the ring containing Y and Z is an aromatic heterocycle. Each of the rings is preferably independently any one of a thiophene ring, a furan ring, a pyrrole ring, a thiazole ring, and an oxazole ring, more preferably a furan ring, a pyrrole ring, or a thiophene ring, and particularly preferably a thiophene ring.

[0040] In Formula (1), R¹ and R² each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. Each of R¹ and R² is preferably independently an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group, more preferably an alkyl group, an aryl group, or a heteroaryl group, particularly preferably an alkyl group having 20 or less carbon atoms, an aryl group having 20 or less carbon atoms, or a heteroaryl group having 20 or less carbon atoms, and more particularly preferably a heteroaryl group having 20 or less carbon atoms.

[0041] In a case where R¹ or R² is an alkyl group, the number of carbon atoms of the alkyl group is preferably 1 to 30, more preferably 1 to 15 from the viewpoint of chemical stability and carrier mobility, and even more preferably 3 to 11. It is preferable that the R¹ and R² are preferably the alkyl group of the above range, because then molecular linearity and carrier mobility can be improved.

[0042] In a case where R¹ or R² represents an alkyl group, the alkyl group may be a linear, branched, or cyclic alkyl group. The alkyl group is preferably a linear alkyl group because then molecular linearity and carrier mobility can be improved.

[0043] In a case where R¹ or R² is an alkyl group having a substituent, the substituent is not particularly limited. Examples of the substituent include a halogen atom, an alkyl group (including an alkyl group having 1 to 40 carbon atoms such as a methyl group, an ethyl group, a propyl group, a butyl group, a pentyl group, a hexyl group, a heptyl group, an octyl group, a nonyl group, a decyl group, an undecyl group, a dodecyl group, a tridecyl group, a tetradecyl group, or a pentadecyl group; here, the alkyl group also includes a 2,6-dimethyloctyl group, a 2-decyltetradecyl group, a 2-hexyldodecyl group, a 2-ethyloctyl group, a 2-butyldecyl group, a 1-octylonyl group, a 2-octyltetradecyl group, a 2-ethylhexyl group, a cycloalkyl group, a bicycloalkyl group, a tricycloalkyl group, and the like), an alkenyl group (including a 1-pentenyl group, a cycloalkenyl group, a bicycloalkenyl group, and the like), an alkynyl group (including a 1-pentynyl group, a trimethylsilylethynyl group, a triethylsilylethynyl group, a tri-*i*-propylsilylethynyl group, a 2-*p*-propylphenylethynyl group, and the like), an aryl group (including an aryl group having 6 to 20 carbon atoms such as a phenyl group, a naphthyl group, a *p*-pentylphenyl group, a 3,4-dipentylphenyl group, a *p*-heptoxyphenyl group, a 3,4-diheptoxyphenyl group, and the like), a hetero ring group (may be referred to as a heterocyclic group as well, including a 2-hexylfuran group and the like), a cyano group, a hydroxyl group, a nitro group, an acyl group (including a hexanoyl group, a benzoyl group, and the like), an alkoxy group (including a butoxy group and the like), an aryloxy group, a silyloxy group, a heterocyclic oxy group, an acyloxy group, a carbamoyloxy group, an amino group (including an anilino group), an acylamino group, an aminocarbonylamino group (including a ureido group), alkoxy- and aryloxy-carbonylamino groups, alkyl- and aryl sulfonylamino groups, a mercapto group, alkyl- and arylthio groups (including a methylthio group, an octylthio group, and the like), a heterocyclic thio group, a sulfamoyl group, a sulfo group, alkyl- and aryl sulfinyl groups, alkyl- and aryl sulfonyl groups, alkyloxy- and aryloxy-carbonyl groups, a carbamoyl group, aryl- and heterocyclic azo group, an imido group, a phosphino group, a phosphinyl group, a phosphinyloxy group, a phosphinylamino group, a phosphono group, a silyl group (a ditrimethylsiloxy methylbutoxy group), a hydrazino group, a ureido group, a boronic acid group (-B(OH)₂), a phosphate group (-OPO(OH)₂), a sulfate group (-OSO₃H), and other known substituents.

[0044] Among these, as the substituent adopted in a case where R¹ or R² is an alkyl group, a decyl group is preferable. Here, R¹ or R² is preferably an unsubstituted alkyl group.

[0045] In a case where R¹ or R² is an alkenyl group, the number of carbon atoms of the alkenyl group is preferably 2 to 30, more preferably 2 to 10, and particularly preferably 2 to 4.

[0046] In a case where R¹ or R² is an alkenyl group having a substituent, the substituent is not particularly limited. Examples of the substituent include the same substituents as exemplified above as the substituent adopted in a case where R¹ or R² is an alkyl group.

[0047] In a case where R¹ or R² is an alkynyl group, the number of carbon atoms of the alkynyl group is preferably 2 to 30, more preferably 2 to 10, and particularly preferably 2.

[0048] In a case where R^1 or R^2 is an alkynyl group having a substituent, the substituent is not particularly limited. Examples of the substituent include the same substituents as exemplified above as the substituent adopted in a case where R^1 and R^2 are an alkyl group. The substituent is more preferably a silyl group or an aryl group, particularly preferably a substituted or unsubstituted trialkylsilyl group or a substituted or unsubstituted phenyl group, and more particularly preferably a substituted or unsubstituted trialkylsilyl group. In a case where R^1 or R^2 is an alkynyl group, the substituent of a trialkylsilyl group substituting the alkynyl group is not particularly limited. The substituent is preferably a substituted or unsubstituted alkyl group, and more preferably a branched alkyl group. In this case, the number of carbon atoms of the alkyl group bonded to a Si atom is preferably 1 to 3. For example, the alkyl group is preferably a methyl group, an ethyl group, or an isopropyl group. The alkyl groups bonded to the Si atom may be the same as or different from each other.

[0049] In a case where R^1 or R^2 is an aryl group, the number of carbon atoms of the aryl group is preferably 6 to 30, more preferably 6 to 18, and particularly preferably 6 to 12.

[0050] In a case where R^1 or R^2 is an aryl group having a substituent, the substituent is not particularly limited. Examples of the substituent include the same substituents as exemplified above as the substituent adopted in a case where R^1 or R^2 is an alkyl group. The substituent is preferably an alkyl group. In a case where R^1 or R^2 is an aryl group, a preferred range of the alkyl group substituting the aryl group is the same as the preferred range of the alkyl group represented by R^1 or R^2 .

[0051] In a case where R^1 or R^2 is an aryl group having a substituent, the number of substituents is not particularly limited. The number of substituents is preferably 1 to 3, more preferably 1 or 2, and particularly preferably 1.

[0052] In a case where R^1 or R^2 is a heteroaryl group, the number of carbon atoms of the heteroaryl group is preferably 3 to 30, more preferably 4 to 20, and particularly preferably 4. The heteroaryl group represented by R^1 or R^2 is preferably a furanyl group, a pyrrolyl group (in which a hydrogen atom may be substituted), a pyrazolyl group, an imidazolyl group, a thienyl group, a thiazolyl group, a thienothieryl group, a benzothieryl group, a thienophenyl group, a pyridyl group, a pyrimidinyl group, a pyridazinyl group, or a pyrazinyl group, more preferably a thienyl group or a furyl group, and particularly preferably a thienyl group.

[0053] In a case where R^1 or R^2 is a heteroaryl group having a substituent, the substituent is not particularly limited. Examples of the substituent include the same substituents as exemplified above as the substituent adopted in a case where R^1 or R^2 is an alkyl group. The substituent is preferably an alkyl group. In a case where R^1 or R^2 is a heteroaryl group, a preferred range of the alkyl group substituting the heteroaryl group is the same as the preferred range of the alkyl group represented by R^1 or R^2 .

[0054] In Formula (1), between R^1 and R^2 , each R^1 is more preferably independently a group having a aliphatic hydrocarbon group from the viewpoint of improving carrier mobility, and even more preferably independently an aryl group having a linear aliphatic hydrocarbon group or a heteroaryl group having a linear aliphatic hydrocarbon group from the viewpoint of further improving carrier mobility.

[0055] In Formula (1), the number of carbon atoms contained in R^1 or R^2 is preferably equal to or less than 30 from the viewpoint of carrier mobility. The number of carbon atoms contained in R^1 or R^2 is preferably 1 to 18, more preferably 5 to 18, and particularly preferably 7 to 18. If the total number of carbon atoms contained in R^1 or R^2 is equal to or greater than the lower limit of the above range, carrier mobility is improved.

[0056] In Formula (1), any one of R^1 and R^2 and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups. The group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking group are bonded to each other. Among these, the group A of divalent linking groups is preferably any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂-, more preferably -O- or -S-, and particularly preferably -O-.

[0057] In Formula (1), the combination of X, Y, Z, R^1 , and R^2 is partially limited. From the viewpoint of carrier mobility, in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R^1 and R^2 are a hydrogen atom is excluded from the range represented by Formula (1). Furthermore, in a case where X, Y, and Z in Formula (1) are a sulfur atom, CH, and a sulfur atom respectively, and both of R^1 and R^2 in Formula (1) are an alkyl group, any one of R^1 and R^2 and the aromatic heterocycle containing Y and Z are bonded to each other through the group A of divalent linking groups.

[0058] In Formula (1), R^1 and R^2 are preferably the same as each other.

[0059] In Formula (1), R^3 and R^4 each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. In a case where m in Formula (1) is 2, R^3 's may be the same as or different from each other. In a case where n in Formula (1) is 2, R^4 's may be the same as or different from each other. R^3 and R^4 are preferably an alkyl group having 3 to 11 carbon atoms.

[0060] In Formula (1), the number of carbon atoms contained in R^3 or R^4 is preferably equal to or less than 30 from the viewpoint of carrier mobility.

[0061] In Formula (1), any one of R^3 and R^4 and a benzene ring may be bonded to each other through the group A

of divalent linking groups.

[0062] In Formula (1), R^3 and R^4 are preferably the same as each other.

[0063] In Formula (1), R^5 in NR^5 that can be adopted as X represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. R^5 is preferably an alkyl group having 3 to 11 carbon atoms.

[0064] In Formula (1), R^6 in CR^6 that can be adopted as Y and Z represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. R^6 is preferably a hydrogen atom or an alkyl group, and more preferably a hydrogen atom. A preferred range of the alkyl group that can be adopted as R^6 is the same as the preferred range of the alkyl group that can be adopted as R^1 and R^2 .

[0065] In Formula (1), R^7 in NR^7 that can be adopted as Y and Z represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. R^7 is preferably an alkyl group or an aryl group, and more preferably an alkyl group. A preferred range of the alkyl group that can be adopted as R^7 is the same as the preferred range of the alkyl group that can be adopted as R^1 and R^2 .

[0066] In Formula (1), R^8 in NR^8 that can be adopted as the group A of divalent linking groups represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. R^8 is more preferably an alkyl group or an aryl group.

[0067] In Formula (1), each of m and n is independently an integer of 0 to 2. Each of m and n is preferably 0 or 1, and more preferably 0. It is particularly preferable that both of m and n are 0.

[0068] Here, from the viewpoint of carrier mobility, a case where both of R^1 and R^2 in Formula (1) are a hydrogen atom and both of m and n in Formula (1) are 0 is excluded.

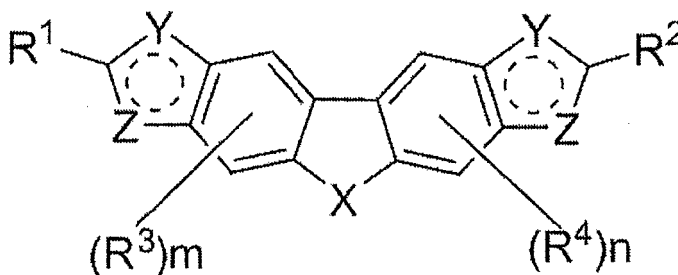
[0069] In Formula (1), m and n are preferably the same as each other.

[0070] From the viewpoint of improving carrier mobility by improving molecular symmetry, R^1 and R^2 in Formula (1) are preferably the same as each other, R^3 and R^4 in Formula (1) are preferably the same as each other, and m and n in Formula (1) are preferably the same as each other.

[0071] (Compound represented by Formula (1A) and having molecular weight of equal to or less than 3,000)

[0072] Among compounds which are represented by Formula (1) and have a molecular weight of equal to or less than 3,000, a compound which is represented by the following Formula (1A) and has a molecular weight of equal to or less than 3,000 is preferable.

Formula (1A)



[0073] In Formula (1A),

X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR^5 ;

Y and Z each independently represent CR^6 , an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR^7 , two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other; a ring containing Y and Z is an aromatic heterocycle;

any one of R^1 and R^2 and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups;

any one of R^3 and R^4 and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, $-NR^8$ -, -CO-, -SO-, and $-SO_2$ - or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other; R^1 , R^2 , R^5 , R^6 , R^7 , and R^8 each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

R^3 and R^4 each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, in a case where m is 2, R^3 's may be the same as or different from each other, and in a case where n is 2, R^4 's may be the same as or different from each other;

m and n each independently represent an integer of 0 to 2;

here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷ are excluded;

a case where X is NR⁵, Y is a nitrogen atom, and Z is an oxygen atom is excluded;

in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R¹ and R² are a hydrogen atom is excluded;

in a case where X is a sulfur atom, Y is CH, Z is a sulfur atom, and both of R¹ and R² are an alkyl group, one of R¹ and R² and an aromatic heterocycle containing Y and Z are bonded to each other through the group A of divalent linking groups; and

a case where both of R¹ and R² are a hydrogen atom, and both of m and n are 0 is excluded.

[0074] The compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is a novel compound. The novel compound is referred to as a compound of the present invention. That is, the compound of the present invention is represented by the following Formula (1A) and has a molecular weight of equal to or less than 3,000. The range of Formula (1A) does not include a case where X, Y, and Z in Formula (1) are NR⁵, a nitrogen atom, and an oxygen atom respectively.

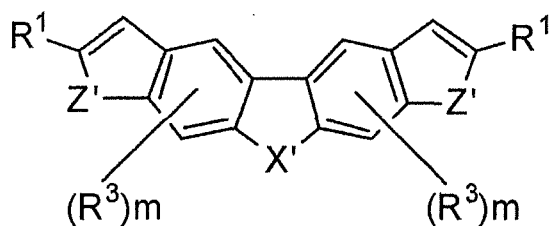
[0075] A preferred range of Formula (1A) is the same as the preferred range of Formula (1).

[0076] Similar to the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000, the compound of the present invention is contained in a semiconductor active layer, which will be described later, of the organic transistor of the present invention. That is, the compound of the present invention can be used as a material for an organic transistor.

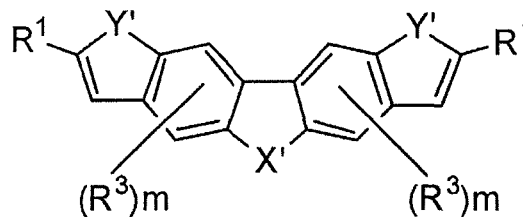
[0077] (Compound represented by Formula (2) or (3) and having molecular weight of equal to or less than 3,000)

[0078] The compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by the following Formula (2) or (3) and has a molecular weight of equal to or less than 3,000.

Formula (2)



Formula (3)



[0079] In Formulae (2) and (3),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

each of Y' and Z' is independently selected from NR⁷, an oxygen atom, a sulfur atom, and a selenium atom;

a ring containing Y' and Z' is an aromatic heterocycle;

R¹ and the aromatic heterocycle containing Y' and Z' may be bonded to each other through the following group A of divalent linking groups;

R³ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other;

each R³ independently represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and in a case where m is 2, R³'s may be the same as or different from each other;

each m is independently an integer of 0 to 2;

here, a case where both of Y' and Z' are NR⁷ is excluded;

in a case where X', Z', and R¹ in Formula (2) are a sulfur atom, a sulfur atom, and an alkyl group respectively, R¹ and the aromatic heterocycle containing Z' are bonded to each other through the group A of divalent linking groups; and

a case where R¹ is a hydrogen atom and both of m's are 0 is excluded.

[0080] In Formulae (2) and (3), a preferred range of X' is the same as the preferred range of X in Formula (1).

[0081] In Formulae (2) and (3), a preferred range of each of Y' and Z' is the same as the preferred range of each of Y and Z in Formula (1).

[0082] In Formulae (2) and (3), a definition and a preferred range of the group A of divalent linking groups are the

same as the definition and the preferred range of the group A of divalent linking groups in Formula (1).

[0083] In Formulae (2) and (3), a preferred range of R^1 is the same as the preferred range of the combination of R^1 and R^2 in Formula (1).

[0084] In Formulae (2) and (3), a preferred range of R^3 is the same as the preferred range of the combination of R^3 and R^4 in Formula (1).

[0085] In Formulae (2) and (3), a preferred range of each of R^7 and R^8 is the same as the preferred range of each of R^7 and R^8 in Formula (1).

[0086] In Formulae (2) and (3), a definition and a preferred range of m is the same as the definition and the preferred range of m in Formula (1).

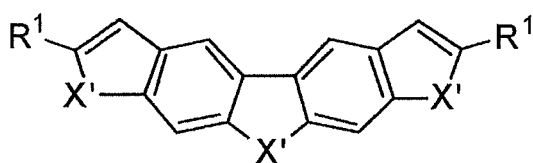
[0087] (Compound represented by Formula (4) or (5) and having molecular weight of equal to or less than 3,000)

[0088] The compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by the following Formula (4) or (5) and has a molecular weight of equal to or less than 3,000.

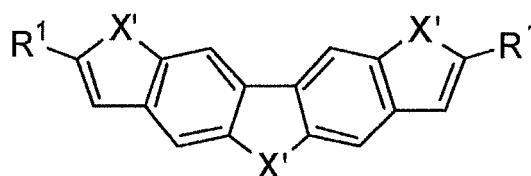
[0089] The compound which is represented by Formula (2) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by Formula (4) and has a molecular weight of equal to or less than 3,000.

[0090] The compound which is represented by Formula (3) and has a molecular weight of equal to or less than 3,000 is preferably a compound which is represented by Formula (5) and has a molecular weight of equal to or less than 3,000.

Formula (4)



Formula (5)



In Formulae (4) and (5),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

R^1 and an aromatic heterocycle containing X' may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups $-O-$, $-S-$, $-NR^8-$, $-CO-$, $-SO-$, and $-SO_2-$ or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R^1 and R^8 each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R^1 's may be the same as or different from each other;

here, in a case where all of X' 's in Formula (4) are a sulfur atom, and R^1 in Formula (4) is an alkyl group, R^1 and the aromatic heterocycle containing X' may be bonded to each other through the group A of divalent linking groups; and a case where R^1 is a hydrogen atom is excluded.

[0091] In Formula (4), a preferred range of X' is the same as the preferred range of the combination of X and Y in Formula (1).

[0092] In Formula (5), a preferred range of X' is the same as the preferred range of the combination of X and Y in Formula (1).

[0093] In Formulae (4) and (5), a definition and a preferred range of the group A of divalent linking groups is the same as the definition and the preferred range of the group A of divalent linking groups in Formula (1).

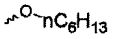
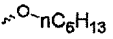
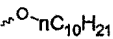
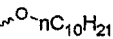
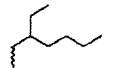
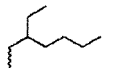
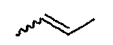
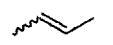


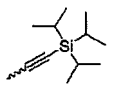
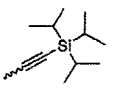
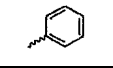
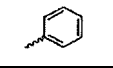
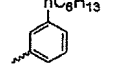
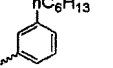
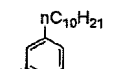
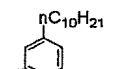
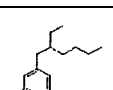
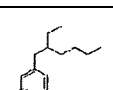
[0094] In Formulae (4) and (5), a preferred range of R^1 is the same as the preferred range of the combination of R^1 and R^2 in Formula (1). R^1 is more preferably a group having an aliphatic hydrocarbon group, and even more preferably an aryl group having a linear aliphatic hydrocarbon group or a heteroaryl group having a linear aliphatic hydrocarbon group.

[0095] Specific examples of the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 will be shown below. However, the compound, which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000, usable in the present invention is not limited to the following specific examples.

[0096] From Table 2, each of the columns in the following tables has the same definition as each of the columns on the first line of Table 1. That is, from Table 2, each of the columns represents X , Y , Z , m , n , R^1 , R^2 , R^3 , and R^4 in this order from left. Furthermore, in a case where Z in each table represents NR^7 , $N(n-C_{10}H_{21})$ is listed.

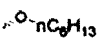
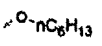
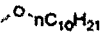
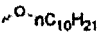
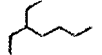
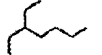

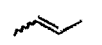


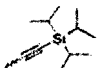
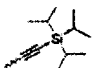

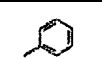
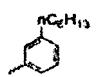
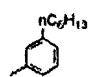
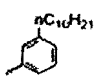
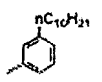

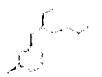
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[Table 1]

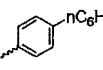
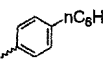
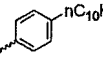
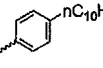
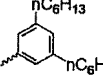
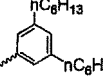
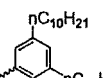
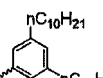
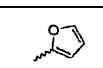
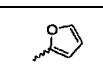
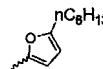
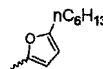
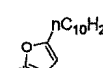
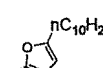
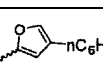
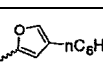
Specific example	X	Y	Z	m	n	R ¹	R ²	R ³	R ⁴
1	O	CH	O	0	0	CH ₃	CH ₃	-	-
2	O	CH	O	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
3	O	CH	O	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
4	O	CH	O	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃		
5	O	CH	O	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
6	O	CH	O	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
7	O	CH	O	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
8	O	CH	O	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
9	O	CH	O	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
10	O	CH	O	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
11	O	CH	O	0	0			-	-
12	O	CH	O	0	0			-	-
13	O	CH	O	0	0			-	-
14	O	CH	O	0	0			-	-
15	O	CH	O	0	0			-	-
16	O	CH	O	0	0			-	-
17	O	CH	O	0	0			-	-
18	O	CH	O	0	0			-	-
19	O	CH	O	0	0			-	-
20	O	CH	O	0	0			-	-
1	O	CH	O	0	0	CH ₃	CH ₃	-	-
2	O	CH	O	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
3	O	CH	O	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
4	O	CH	O	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
5	O	CH	O	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
6	O	CH	O	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
7	O	CH	O	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
8	O	CH	O	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
9	O	CH	O	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-

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(continued)

Specific example	X	Y	Z	m	n	R ¹	R ²	R ³	R ⁴
10	O	CH	O	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
11	O	CH	O	0	0			-	-
12	O	CH	O	0	0			-	-
13	O	CH	O	0	0			-	-
14	O	CH	O	0	0			-	-
15	O	CH	O	0	0			-	-
16	O	CH	O	0	0			-	-
17	O	CH	O	0	0			-	-
18	O	CH	O	0	0			-	-
19	O	CH	O	0	0			-	-
20	O	CH	O	0	0			-	-

[Table 2]

21	O	CH	O	0	0			-	-
22	O	CH	O	0	0			-	-
23	O	CH	O	0	0			-	-
24	O	CH	O	0	0			-	-
25	O	CH	O	0	0			-	-
26	O	CH	O	0	0			-	-
27	O	CH	O	0	0			-	-
28	O	CH	O	0	0			-	-

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(continued)

29	O	CH	O	0	0			-	-
30	O	CH	O	0	0			-	-
31	O	CH	O	0	0			-	-
32	O	CH	O	0	0			-	-
33	O	CH	O	0	0			-	-
34	O	CH	O	0	0			-	-
35	O	CH	O	0	0			-	-
36	O	CH	O	0	0			-	-
37	O	CH	O	0	0			-	-
38	O	CH	O	0	0			-	-
39	O	CH	O	0	0			-	-
40	O	CH	O	0	0			-	-

[Table 3]

41	O	CH	O	0	0			-	-
42	O	CH	O	0	0			-	-
43	O	CH	O	0	0			-	-
44	O	CH	O	0	0			-	-
45	O	CH	O	0	0			-	-
46	O	CH	O	0	0			-	-
47	O	CH	O	0	0			-	-
48	O	CH	O	0	0			-	-

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(continued)

5	49	O	CH	O	0	0			-	-
	50	O	CH	O	0	0			-	-
10	51	O	CH	O	0	0			-	-
	52	O	CH	O	0	0			-	-
15	53	O	CH	O	0	0			-	-
	54	O	CH	O	0	0			-	-
20	55	O	CH	O	0	0			-	-
	56	O	CH	O	0	0			-	-
25	57	O	CH	O	0	0			-	-
	58	O	CH	O	0	0			-	-
30	59	O	CH	O	0	0			-	-
35	60	O	CH	O	0	0			-	-

[Table 4]

40	61	O	CH	O	0	0			-	-
45	62	O	CH	O	0	0			-	-
	63	O	CH	O	0	0			-	-
50	64	O	CH	O	0	0			-	-
55	65	O	CH	O	0	0			-	-

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(continued)

5

10

15

20

25

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66	O	CH	O	0	0			-	-
67	O	CH	O	0	0			-	-
68	O	CH	O	0	0			-	-
69	O	CH	O	0	0			-	-
70	O	CH	O	0	0			-	-
71	O	CH	O	0	0			-	-
72	O	CH	O	0	0			-	-
73	O	CH	O	0	0			-	-
74	O	CH	O	0	0			-	-
75	O	CH	O	0	0			-	-
76	O	CH	O	0	0			-	-
77	O	CH	O	2	2	H	H	n-C6H13	n-C6H13
78	O	CH	O	2	2	H	H	n-C10H21	n-C10H21
79	S	CH	O	0	0	CH ₃	CH ₃	-	-
80	S	CH	O	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-

[Table 5]

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81	S	CH	O	0	0	n-C ₆ H ₁₁	n-C ₅ H ₁₁	-	-
82	S	CH	O	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
83	S	CH	O	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
84	S	CH	O	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
85	S	CH	O	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
86	S	CH	O	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
87	S	CH	O	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
88	S	CH	O	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
89	S	CH	O	0	0			-	-

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(continued)

5	90	S	CH	O	0	0			-	-
	91	S	CH	O	0	0			-	-
10	92	S	CH	O	0	0			-	-
	93	S	CH	O	0	0			-	-
15	94	S	CH	O	0	0			-	-
	95	S	CH	O	0	0			-	-
20	96	S	CH	O	0	0			-	-
	97	S	CH	O	0	0			-	-
25	98	S	CH	O	0	0			-	-
	99	S	CH	O	0	0			-	-
30	100	S	CH	O	0	0			-	-

[Table 6]

35	101	S	CH	O	0	0			-	-
40	102	S	CH	O	0	0			-	-
	103	S	CH	O	0	0			-	-
45	104	S	CH	O	0	0			-	-
	105	S	CH	O	0	0			-	-
50	106	S	CH	O	0	0			-	-
	107	S	CH	O	0	0			-	-

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(continued)

5	108	S	CH	O	0	0			-	-
	109	S	CH	O	0	0			-	-
10	110	S	CH	O	0	0			-	-
	111	S	CH	O	0	0			-	-
15	112	S	CH	O	0	0			-	-
	113	S	CH	O	0	0			-	-
20	114	S	CH	O	0	0			-	-
	115	S	CH	O	0	0			-	-
25	116	S	CH	O	0	0			-	-
	117	S	CH	O	0	0			-	-
30	118	S	CH	O	0	0			-	-
	119	S	CH	O	0	0			-	-
35	120	S	CH	O	0	0			-	-
40										

[Table 7]

45	121	S	CH	O	0	0			-	-
	122	S	CH	O	0	0			-	-
50	123	S	CH	O	0	0			-	-
	124	S	CH	O	0	0			-	-
55	125	S	CH	O	0	0			-	-
	126	S	CH	O	0	0			-	-

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(continued)

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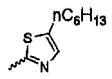
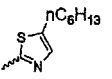
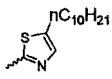
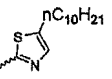
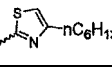
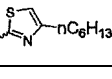
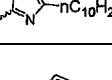
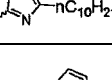
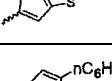
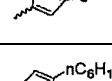
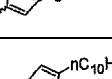
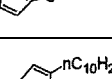
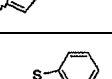
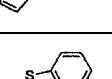
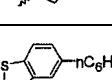
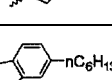
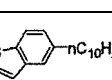
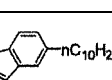
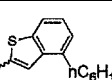
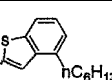
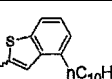
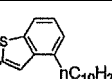
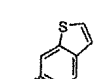
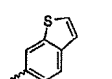
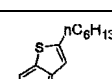
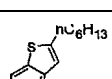

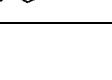
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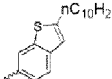
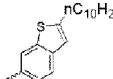
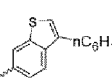
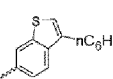
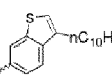
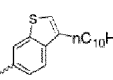
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127	S	CH	O	0	0			-	-
128	S	CH	O	0	0			-	-
129	S	CH	O	0	0			-	-
130	S	CH	O	0	0			-	-
131	S	CH	O	0	0			-	-
132	S	CH	O	0	0			-	-
133	S	CH	O	0	0			-	-
134	S	CH	O	0	0			-	-
135	S	CH	O	0	0			-	-
136	S	CH	O	0	0			-	-
137	S	CH	O	0	0			-	-
138	S	CH	O	0	0			-	-
139	S	CH	O	0	0			-	-
140	S	CH	O	0	0			-	-

[Table 8]

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141	S	CH	O	0	0			-	-
142	S	CH	O	0	0			-	-
143	S	CH	O	0	0			-	-

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(continued)

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144	S	CH	O	0	0			-	-
145	S	CH	O	0	0			-	-
146	S	CH	O	0	0			-	-
147	S	CH	O	0	0			-	-
148	S	CH	O	0	0			-	-
149	S	CH	O	0	0			-	-
150	S	CH	O	0	0			-	-
151	S	CH	O	0	0			-	-
152	S	CH	O	0	0			-	-
153	S	CH	O	0	0			-	-
154	S	CH	O	0	0			-	-
155	S	CH	O	2	2	H	H	n-C6H13	n-C6H13
156	S	CH	O	2	2	H	H	n-C10H21	n-C10H21
157	S	CH	S	0	0	OCH ₃	OCH ₃	-	-
158	S	CH	S	0	0	O-n-O ₄ H ₉	O-n-C ₄ H ₉	-	-
159	S	CH	S	0	0	O-n-O ₅ H ₁₁	O-n-C ₅ H ₁₁	-	-
160	S	CH	S	0	0	O-n-C ₆ H ₁₃	O-n-C ₆ H ₁₃	-	-

(Examples 157-160 arc Reference Examples)

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[0097]

[Table 9]

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161	S	CH	S	0	0	O-n-C ₇ H ₁₅	O-n-C ₇ H ₁₅	-	-
162	S	CH	S	0	0	O-n-O ₈ H ₁₇	O-n-C ₈ H ₁₇	-	-
163	S	CH	S	0	0	O-n-C ₉ H ₁₉	O-n-C ₉ H ₁₉	-	-
164	S	CH	S	0	0	O-n-C ₁₀ H ₂₁	O-n-C ₁₀ H ₂₁	-	-
165	S	CH	S	0	0	O-n-C ₁₁ H ₂₃	O-n-C ₁₁ H ₂₃	-	-
166	S	CH	S	0	0	O-n-C ₁₂ H ₂₅	O-n-C ₁₂ H ₂₅	-	-

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(continued)

5	167	S	CH	S	0	0			-	-
	168	S	CH	S	0	0			-	-
	169	S	CH	S	0	0			-	-
10	170	S	CH	S	0	0			-	-
	171	S	CH	S	0	0			-	-
15	172	S	CH	S	0	0			-	-
	173	S	CH	S	0	0			-	-
20	174	S	CH	S	0	0			-	-
25	175	S	CH	S	0	0			-	-
	176	S	CH	S	0	0			-	-
30	177	S	CH	S	0	0			-	-
	178	S	CH	S	0	0			-	-
35	179	S	CH	S	0	0			-	-
40	180	S	CH	S	0	0			-	-

(161-167 are Reference Examples)

[0098]

[Table 10]

50	181	S	CH	S	0	0			-	-
	182	S	CH	S	0	0			-	-
55	183	S	CH	S	0	0			-	-

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(continued)

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184	S	CH	S	0	0			-	-
185	S	CH	S	0	0			-	-
186	S	CH	S	0	0			-	-
187	S	CH	S	0	0			-	-
188	S	CH	S	0	0			-	-
189	S	CH	S	0	0			-	-
190	S	CH	S	0	0			-	-
191	S	CH	S	0	0			-	-
192	S	CH	S	0	0			-	-
193	S	CH	S	0	0			-	-
194	S	CH	S	0	0			-	-
195	S	CH	S	0	0			-	-
196	S	CH	S	0	0			-	-
197	S	CH	S	0	0			-	-
198	S	CH	S	0	0			-	-
199	S	CH	S	0	0			-	-
200	S	CH	S	0	0			-	-

[Table 11]

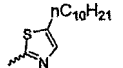
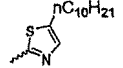
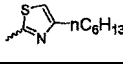
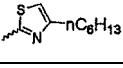
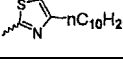
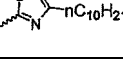


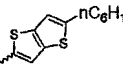
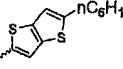
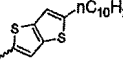
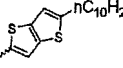


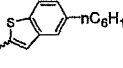
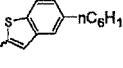
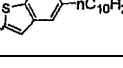
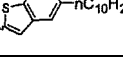
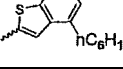
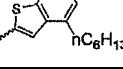
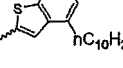
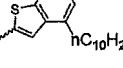


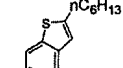
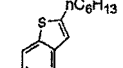
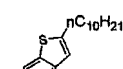
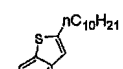
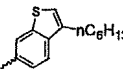
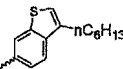
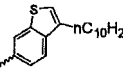
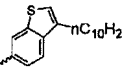


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201	S	CH	S	0	0			-	-
202	S	CH	S	0	0			-	-
203	S	CH	S	0	0			-	-









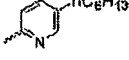
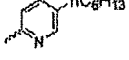
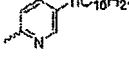
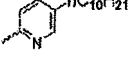
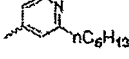
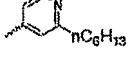
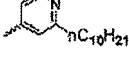
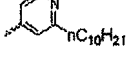
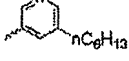
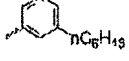
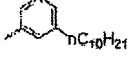
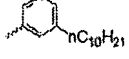
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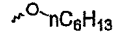
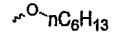
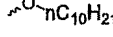
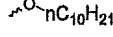
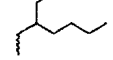
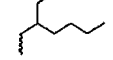
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	205	S	CH	S	0	0			-	-
10	206	S	CH	S	0	0			-	-
	207	S	CH	S	0	0			-	-
15	208	S	CH	S	0	0			-	-
	209	S	CH	S	0	0			-	-
20	210	S	CH	S	0	0			-	-
	211	S	CH	S	0	0			-	-
25	212	S	CH	S	0	0			-	-
	213	S	CH	S	0	0			-	-
30	214	S	CH	S	0	0			-	-
	215	S	CH	S	0	0			-	-
35	216	S	CH	S	0	0			-	-
	217	S	CH	S	0	0			-	-
40	218	S	CH	S	0	0			-	-
	219	S	CH	S	0	0			-	-
45	220	S	CH	S	0	0			-	-
50										
55										

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[Table 12]

221	S	CH	S	0	0			-	-
222	S	CH	S	0	0			-	-
223	S	CH	S	0	0			-	-
224	S	CH	S	0	0			-	-
225	S	CH	S	0	0			-	-
226	S	CH	S	0	0			-	-
227	S	CH	S	0	0			-	-
228	S	CH	S	0	0			-	-
229	S	CH	S	0	0			-	-
230	S	CH	S	0	0			-	-
231	S	S	CH	0	0	CH ₃	CH ₃	-	-
232	S	S	CH	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
233	S	S	CH	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
234	S	S	CH	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
235	S	S	CH	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
236	S	S	CH	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
237	S	S	CH	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
238	S	S	CH	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
239	S	S	CH	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
240	S	S	CH	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-

[Table 13]

241	S	S	CH	0	0			-	-
242	S	S	CH	0	0			-	-
243	S	S	CH	0	0			-	-

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(continued)

244	S	S	CH	0	0			-	-
245	S	S	CH	0	0			-	-
246	S	S	CH	0	0			-	-
247	S	S	CH	0	0			-	-
248	S	S	CH	0	0			-	-
249	S	S	CH	0	0			-	-
250	S	S	CH	0	0			-	-
251	S	S	CH	0	0			-	-
252	S	S	CH	0	0			-	-
253	S	S	CH	0	0			-	-
254	S	S	CH	0	0			-	-
255	S	S	CH	0	0			-	-
256	S	S	CH	0	0			-	-
257	S	S	CH	0	0			-	-
258	S	S	CH	0	0			-	-
259	S	S	CH	0	0			-	-
260	S	S	CH	0	0			-	-

[Table 14]

261	S	S	CH	0	0			-	-
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(continued)

5	262	S	S	CH	0	0			-	-
	263	S	S	CH	0	0			-	-
10	264	S	S	CH	0	0			-	-
	265	S	S	CH	0	0			-	-
15	266	S	S	CH	0	0			-	-
	267	S	S	CH	0	0			-	-
20	268	S	S	CH	0	0			-	-
	269	S	S	CH	0	0			-	-
25	270	S	S	CH	0	0			-	-
	271	S	S	CH	0	0			-	-
30	272	S	S	CH	0	0			-	-
	273	S	S	CH	0	0			-	-
35	274	S	S	CH	0	0			-	-
	275	S	S	CH	0	0			-	-
40	276	S	S	CH	0	0			-	-
	277	S	S	CH	0	0			-	-
45	278	S	S	CH	0	0			-	-
	279	S	S	CH	0	0			-	-
50	280	S	S	CH	0	0			-	-

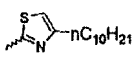
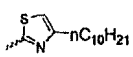


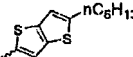
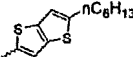
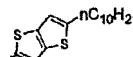
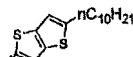


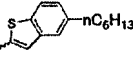
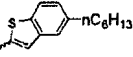
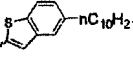
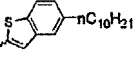
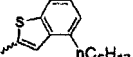
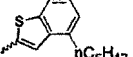
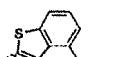



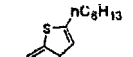
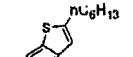
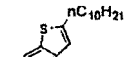
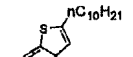
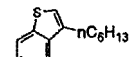
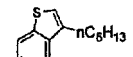
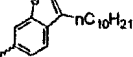
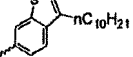








[Table 15]

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

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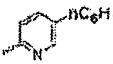
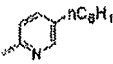
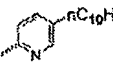
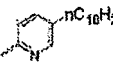
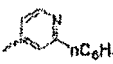
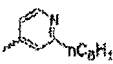
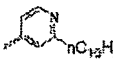
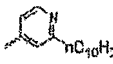
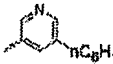
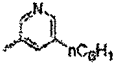
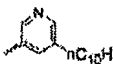
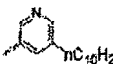








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283	S	S	CH	0	0			-	-
284	S	S	CH	0	0			-	-
285	S	S	CH	0	0			-	-
286	S	S	CH	0	0			-	-
287	S	S	CH	0	0			-	-
288	S	S	CH	0	0			-	-
289	S	S	CH	0	0			-	-
290	S	S	CH	0	0			-	-
291	S	S	CH	0	0			-	-
292	S	S	CH	0	0			-	-
293	S	S	CH	0	0			-	-
294	S	S	CH	0	0			-	-
295	S	S	CH	0	0			-	-
296	S	S	CH	0	0			-	-
297	S	S	CH	0	0			-	-
298	S	S	CH	0	0			-	-
299	S	S	CH	0	0			-	-

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5	300	S	S	CH	0	0			-	-
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[Table 16]

10	301	S	S	CH	0	0			-	-
15	302	S	S	CH	0	0			-	-
20	303	S	S	CH	0	0			-	-
25	304	S	S	CH	0	0			-	-
30	305	S	S	CH	0	0			-	-
35	306	S	S	CH	0	0			-	-
40	307	S	O	CH	0	0	CH ₃	CH ₃	-	-
45	308	S	O	CH	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
50	309	S	O	CH	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
	310	S	O	CH	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
	311	S	O	CH	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
	312	S	O	CH	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
	313	S	O	CH	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
	314	S	O	CH	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
	315	S	O	CH	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
	316	S	O	CH	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
	317	S	O	CH	0	0			-	-
	318	S	O	CH	0	0			-	-
	319	S	O	CH	0	0			-	-
	320	S	O	CH	0	0			-	-

[Table 17]

55	321	S	O	CH	0	0			-	-
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322	S	O	CH	0	0			-	-
323	S	O	CH	0	0			-	-
324	S	O	CH	0	0			-	-
325	S	O	CH	0	0			-	-
326	S	O	CH	0	0			-	-
327	S	O	CH	0	0			-	-
328	S	O	CH	0	0			-	-
329	S	O	CH	0	0			-	-
330	S	O	CH	0	0			-	-
331	S	O	CH	0	0			-	-
332	S	O	CH	0	0			-	-
333	S	O	CH	0	0			-	-
334	S	O	CH	0	0			-	-
335	S	O	CH	0	0			-	-
336	S	O	CH	0	0			-	-
337	S	O	CH	0	0			-	-
338	S	O	CH	0	0			-	-
339	S	O	CH	0	0			-	-

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(continued)

340	S	O	CH	0	0			-	-
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[Table 18]

341	S	O	CH	0	0			-	-
342	S	O	CH	0	0			-	-
343	S	O	CH	0	0			-	-
344	S	O	CH	0	0			-	-
345	S	O	CH	0	0			-	-
346	S	O	CH	0	0			-	-
347	S	O	CH	0	0			-	-
348	S	O	CH	0	0			-	-
349	S	O	CH	0	0			-	-
350	S	O	CH	0	0			-	-
351	S	O	CH	0	0			-	-
352	S	O	CH	0	0			-	-
353	S	O	CH	0	0			-	-
354	S	O	CH	0	0			-	-
355	S	O	CH	0	0			-	-
356	S	O	CH	0	0			-	-
357	S	O	CH	0	0			-	-
358	S	O	CH	0	0			-	-
359	S	O	CH	0	0			-	-

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360	S	O	CH	0	0			-	-
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[Table 19]

361	S	O	CH	0	0			-	-
362	S	O	CH	0	0			-	-
363	S	O	CH	0	0			-	-
364	S	O	CH	0	0			-	-
365	S	O	CH	0	0			-	-
366	S	O	CH	0	0			-	-
367	S	O	CH	0	0			-	-
368	S	O	CH	0	0			-	-
369	S	O	CH	0	0			-	-
370	S	O	CH	0	0			-	-
371	S	O	CH	0	0			-	-
372	S	O	CH	0	0			-	-
373	S	O	CH	0	0			-	-
374	S	O	CH	0	0			-	-
375	S	O	CH	0	0			-	-
376	S	O	CH	0	0			-	-

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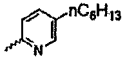
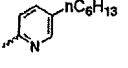
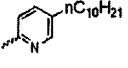
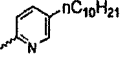
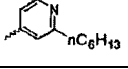
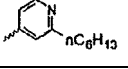
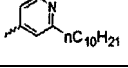
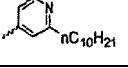
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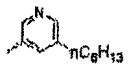
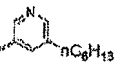
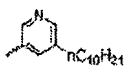
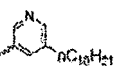
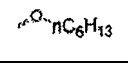
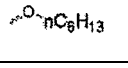
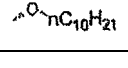
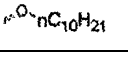
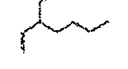


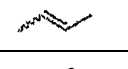
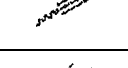
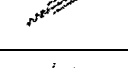

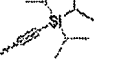
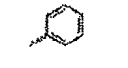
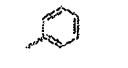
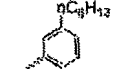
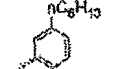
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



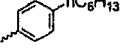
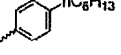
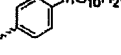
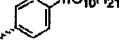
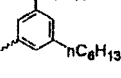
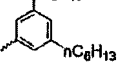
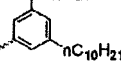
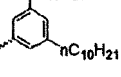




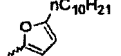
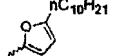
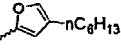
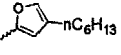
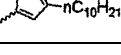
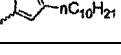






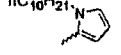
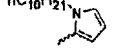




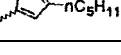
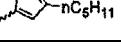
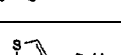
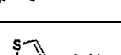
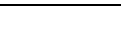
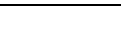
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377	S	O	CH	0	0			-	-
378	S	O	CH	0	0			-	-
379	S	O	CH	0	0			-	-
380	S	O	CH	0	0			-	-

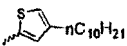
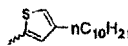
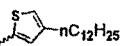
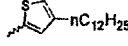
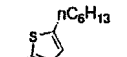
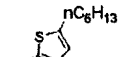
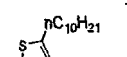
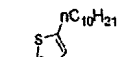
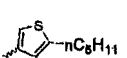
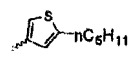
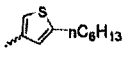
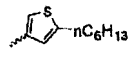
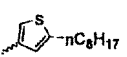
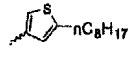
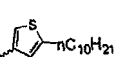
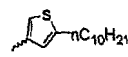
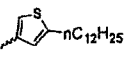
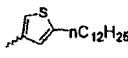

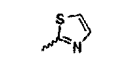
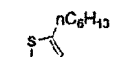
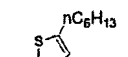
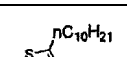
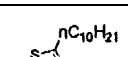
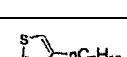
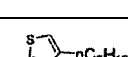


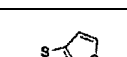

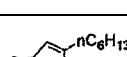
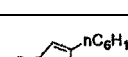
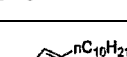
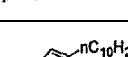
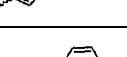
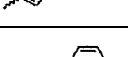
[Table 20]

381	S	O	CH	0	0			-	-
382	S	O	CH	0	0			-	-
383	S	S	N	0	0	CH ₃	CH ₃	-	-
384	S	S	N	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
385	S	S	N	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
386	S	S	N	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
387	S	S	N	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
388	S	S	N	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
389	S	S	N	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
390	S	S	N	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
391	S	S	N	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
392	S	S	N	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
393	S	S	N	0	0			-	-
394	S	S	N	0	0			-	-
395	S	S	N	0	0			-	-
396	S	S	N	0	0			-	-
397	S	S	N	0	0			-	-
398	S	S	N	0	0			-	-
399	S	S	N	0	0			-	-
400	S	S	N	0	0			-	-

[Table 21]

5	401	S	S	N	0	0			-	-
10	402	S	S	N	0	0			-	-
15	403	S	S	N	0	0			-	-
20	404	S	S	N	0	0			-	-
25	405	S	S	N	0	0			-	-
30	406	S	S	N	0	0			-	-
35	407	S	S	N	0	0			-	-
40	408	S	S	N	0	0			-	-
45	409	S	S	N	0	0			-	-
50	410	S	S	N	0	0			-	-
55	411	S	S	N	0	0			-	-
	412	S	S	N	0	0			-	-
	413	S	S	N	0	0			-	-
	414	S	S	N	0	0			-	-
	415	S	S	N	0	0			-	-
	416	S	S	N	0	0			-	-
	417	S	S	N	0	0			-	-
	418	S	S	N	0	0			-	-
	419	S	S	N	0	0			-	-
	420	S	S	N	0	0			-	-

[Table 22]

5	421	S	S	N	0	0			-	-
	422	S	S	N	0	0			-	-
10	423	S	S	N	0	0			-	-
	424	S	S	N	0	0			-	-
15	425	S	S	N	0	0			-	-
	426	S	S	N	0	0			-	-
20	427	S	S	N	0	0			-	-
	428	S	S	N	0	0			-	-
25	429	S	S	N	0	0			-	-
	430	S	S	N	0	0			-	-
30	431	S	S	N	0	0			-	-
	432	S	S	N	0	0			-	-
35	433	S	S	N	0	0			-	-
	434	S	S	N	0	0			-	-
40	435	S	S	N	0	0			-	-
	436	S	S	N	0	0			-	-
45	437	S	S	N	0	0			-	-
	438	S	S	N	0	0			-	-
50										
55										

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(continued)

439	S	S	N	0	0			-	-
440	S	S	N	0	0			-	-

[Table 23]

441	S	S	N	0	0			-	-
442	S	S	N	0	0			-	-
443	S	S	N	0	0			-	-
444	S	S	N	0	0			-	-
446	S	S	N	0	0			-	-
446	S	S	N	0	0			-	-
447	S	S	N	0	0			-	-
448	S	S	N	0	0			-	-
449	S	S	N	0	0			-	-
450	S	S	N	0	0			-	-
451	S	S	N	0	0			-	-
452	S	S	N	0	0			-	-
453	S	S	N	0	0			-	-
454	S	S	N	0	0			-	-
455	S	S	N	0	0			-	-

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(continued)

5	456	S	S	N	0	0			-	-
	457	S	S	N	0	0			-	-
10	458	S	S	N	0	0			-	-
	459	S	O	S	0	0	CH ₃	CH ₃	-	-
	460	S	O	S	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-

[Table 24]

20	461	S	O	S	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
	462	S	O	S	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
	463	S	O	S	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
	464	S	O	S	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
25	465	S	O	S	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
	466	S	O	S	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
	467	S	O	S	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
30	468	S	O	S	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
	469	S	O	S	0	0			-	-
	470	S	O	S	0	0			-	-
35	471	S	O	S	0	0			-	-
	472	S	O	S	0	0			-	-
40	473	S	O	S	0	0			-	-
	474	S	O	S	0	0			-	-
45	475	S	O	S	0	0			-	-
	476	S	O	S	0	0			-	-
50	477	S	O	S	0	0			-	-
55	478	S	O	S	0	0			-	-

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(continued)

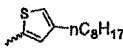
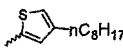
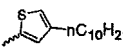
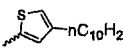
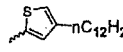
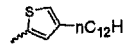
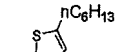
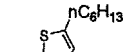
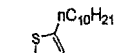
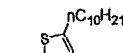
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480	S	O	S	0	0			-	-

[Table 25]

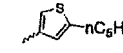
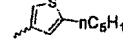
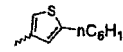
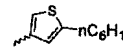
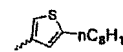
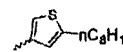
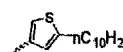
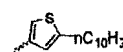
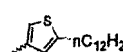
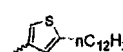


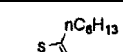
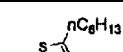
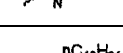
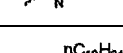
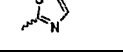
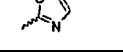
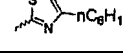
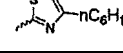


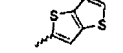
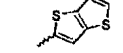
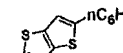
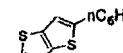




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483	S	O	S	0	0			-	-
484	S	O	S	0	0			-	-
485	S	O	S	0	0			-	-
486	S	O	S	0	0			-	-
487	S	O	S	0	0			-	-
488	S	O	S	0	0			-	-
489	S	O	S	0	0			-	-
490	S	O	S	0	0			-	-
491	S	O	S	0	0			-	-
492	S	O	S	0	0			-	-
493	S	O	S	0	0			-	-
494	S	O	S	0	0			-	-
495	S	O	S	0	0			-	-

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(continued)

5	496	S	O	S	0	0			-	-
	497	S	O	S	0	0			-	-
10	498	S	O	S	0	0			-	-
	499	S	O	S	0	0			-	-
15	500	S	O	S	0	0			-	-

[Table 26]

20	501	S	O	S	0	0			-	-
	502	S	O	S	0	0			-	-
25	503	S	O	S	0	0			-	-
	504	S	O	S	0	0			-	-
30	505	S	O	S	0	0			-	-
	506	S	O	S	0	0			-	-
35	507	S	O	S	0	0			-	-
	508	S	O	S	0	0			-	-
40	509	S	O	S	0	0			-	-
	510	S	O	S	0	0			-	-
45	511	S	O	S	0	0			-	-
	512	S	O	S	0	0			-	-
50	513	S	O	S	0	0			-	-
	514	S	O	S	0	0			-	-
55									-	-

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(continued)

5	515	S	O	S	0	0			-	-
	516	S	O	S	0	0			-	-
10	517	S	O	S	0	0			-	-
	518	S	O	S	0	0			-	-
15	519	S	O	S	0	0			-	-
20	520	S	O	S	0	0			-	-

[Table 27]

25	521	S	O	S	0	0			-	-
	522	S	O	S	0	0			-	-
30	523	S	O	S	0	0			-	-
35	524	S	O	S	0	0			-	-
	525	S	O	S	0	0			-	-
40	526	S	O	S	0	0			-	-
	527	S	O	S	0	0			-	-
45	528	S	O	S	0	0			-	-
	529	S	O	S	0	0			-	-
50	530	S	O	S	0	0			-	-
55	531	S	O	S	0	0			-	-

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(continued)

532	S	O	S	0	0			-	-
533	S	O	S	0	0			-	-
534	S	O	S	0	0			-	-
535	Se	CH	S	0	0	CH ₃	CH ₃	-	-
536	Se	CH	S	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
537	Se	CH	S	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
538	Se	CH	S	0	0	n-C ₆ H ₁₃	n-COH ₁₃	-	-
539	Se	CH	S	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
540	Se	CH	S	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-

[Table 28]

541	Se	CH	S	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
542	Se	CH	S	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
543	Se	CH	S	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
544	Se	CH	S	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-
545	Se	CH	S	0	0			-	-
546	Se	CH	S	0	0			-	-
547	Se	CH	S	0	0			-	-
548	Se	CH	S	0	0			-	-
549	Se	CH	S	0	0			-	-
550	Se	CH	S	0	0			-	-
551	Se	CH	S	0	0			-	-
552	Se	CH	S	0	0			-	-
553	Se	CH	S	0	0			-	-
554	Se	CH	S	0	0			-	-

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(continued)













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	556	Se	CH	S	0	0			-	-
10	557	Se	CH	S	0	0			-	-
	558	Se	CH	S	0	0			-	-
15	559	Se	CH	S	0	0			-	-
20	560	Se	CH	S	0	0			-	-

[Table 29]

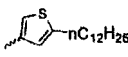
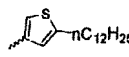


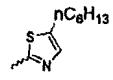
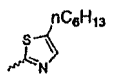
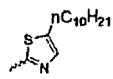
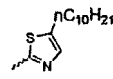
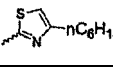
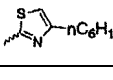
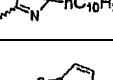
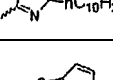


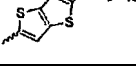
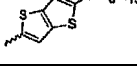
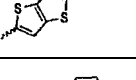
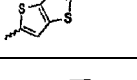


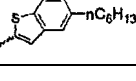
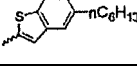
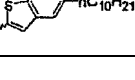
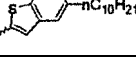
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	562	Se	CH	S	0	0			-	-
30	563	Se	CH	S	0	0			-	-
	564	Se	CH	S	0	0			-	-
35	565	Se	CH	S	0	0			-	-
	566	Se	CH	S	0	0			-	-
40	567	Se	CH	S	0	0			-	-
	568	Se	CH	S	0	0			-	-
45	569	Se	CH	S	0	0			-	-
	570	Se	CH	S	0	0			-	-
50	571	Se	CH	S	0	0			-	-
	572	Se	CH	S	0	0			-	-
55	573	Se	CH	S	0	0			-	-
	574	Se	CH	S	0	0			-	-

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(continued)

575	Se	CH	S	0	0			-	-
576	Se	CH	S	0	0			-	-
577	Se	CH	S	0	0			-	-
578	Se	CH	S	0	0			-	-
579	Se	CH	S	0	0			-	-
580	Se	CH	S	0	0			-	-

[Table 30]

581	Se	CH	S	0	0			-	-
582	Se	CH	S	0	0			-	-
583	Se	CH	S	0	0			-	-
584	Se	CH	S	0	0			-	-
585	Se	CH	S	0	0			-	-
586	Se	CH	S	0	0			-	-
587	Se	CH	S	0	0			-	-
588	Se	CH	S	0	0			-	-
589	Se	CH	S	0	0			-	-
590	Se	CH	S	0	0			-	-
591	Se	CH	S	0	0			-	-
592	Se	CH	S	0	0			-	-

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(continued)

593	Se	CH	S	0	0			-	-
594	Se	CH	S	0	0			-	-
595	Se	CH	S	0	0			-	-
596	Se	CH	S	0	0			-	-
597	Se	CH	S	0	0			-	-
598	Se	CH	S	0	0			-	-
599	Se	CH	S	0	0			-	-
600	Se	CH	S	0	0			-	-

[Table 31]

601	Se	CH	S	0	0			-	-
602	Se	CH	S	0	0			-	-
603	Se	CH	S	0	0			-	-
604	Se	CH	S	0	0			-	-
605	Se	CH	S	0	0			-	-
606	Se	CH	S	0	0			-	-
607	Se	CH	S	0	0			-	-
608	Se	CH	S	0	0			-	-
609	Se	CH	S	0	0			-	-

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(continued)

5	610	Se	CH	S	0	0			-	-
	611	S	CH	N(n-C10H21)	0	0	CH ₃	CH ₃	-	-
	612	S	CH	N(n-C10H21)	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
10	613	S	CH	N(n-C10H21)	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-
	614	S	CH	N(n-C10H21)	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
	615	s	CH	N(n-C10H21)	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
	616	S	CH	N(n-C10H21)	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
15	617	S	CH	N(n-C10H21)	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
	618	S	CH	N(n-C10H21)	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
	619	S	CH	N(n-C10H21)	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
20	620	S	CH	N(n-C10H21)	0	0	n-C ₁₂ H ₂₆	n-C ₁₂ H ₂₆	-	-

[Table 32]

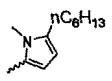
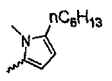
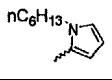
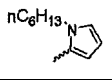
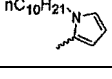
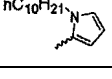
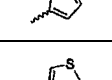
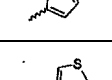
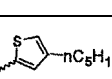
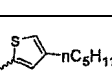
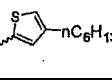
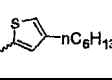
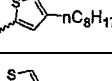
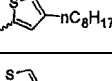
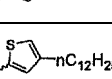
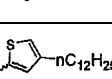
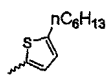
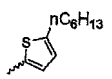
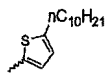
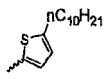
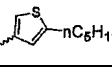
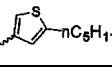
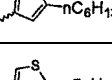
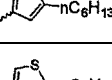
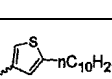
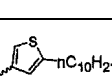






25	601	Se	CH	S	0	0			-	-
	602	Se	CH	S	0	0			-	-
30	603	Se	CH	S	0	0			-	-
	604	Se	CH	S	0	0			-	-
35	605	Se	CH	S	0	0			-	-
	606	Se	CH	S	0	0			-	-
40	607	Se	CH	S	0	0			-	-
	608	Se	CH	S	0	0			-	-
45	609	Se	CH	S	0	0			-	-
50	610	Se	CH	S	0	0			-	-
	611	S	CH	N(n-C10H21)	0	0	CH ₃	CH ₃	-	-
55	612	S	CH	N(n-C10H21)	0	0	n-C ₄ H ₉	n-C ₄ H ₉	-	-
	613	S	CH	N(n-C10H21)	0	0	n-C ₅ H ₁₁	n-C ₅ H ₁₁	-	-

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(continued)

614	S	CH	N(n-C10H21)	0	0	n-C ₆ H ₁₃	n-C ₆ H ₁₃	-	-
615	S	CH	N(n-C10H21)	0	0	n-C ₇ H ₁₅	n-C ₇ H ₁₅	-	-
616	S	CH	N(n-C10H21)	0	0	n-C ₈ H ₁₇	n-C ₈ H ₁₇	-	-
617	S	CH	N(n-C10H21)	0	0	n-C ₉ H ₁₉	n-C ₉ H ₁₉	-	-
618	S	CH	N(n-C10H21)	0	0	n-C ₁₀ H ₂₁	n-C ₁₀ H ₂₁	-	-
619	S	CH	N(n-C10H21)	0	0	n-C ₁₁ H ₂₃	n-C ₁₁ H ₂₃	-	-
620	S	CH	N(n-C10H21)	0	0	n-C ₁₂ H ₂₅	n-C ₁₂ H ₂₅	-	-

[Table 33]

641	S	CH	N(n-C10H21)	0	0			-	-
642	S	CH	N(n-C10H21)	0	0			-	-
643	S	CH	N(n-C10H21)	0	0			-	-
644	S	CH	N(n-C10H21)	0	0			-	-
645	S	CH	N(n-C10H21)	0	0			-	-
646	S	CH	N(n-C10H21)	0	0			-	-
647	S	CH	N(n-C10H21)	0	0			-	-
648	S	CH	N(n-C10H21)	0	0			-	-
649	S	CH	N(n-C10H21)	0	0			-	-
650	S	CH	N(n-C10H21)	0	0			-	-
651	S	CH	N(n-C10H21)	0	0			-	-
652	S	CH	N(n-C10H21)	0	0			-	-
653	S	CH	N(n-C10H21)	0	0			-	-
654	S	CH	N(n-C10H21)	0	0			-	-
655	S	CH	N(n-C10H21)	0	0			-	-
656	S	CH	N(n-C10H21)	0	0			-	-

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(continued)

657	S	CH	N(n-C10H21)	0	0			-	-
658	S	CH	N(n-C10H21)	0	0			-	-
659	S	CH	N(n-C10H21)	0	0			-	-
660	S	CH	N(n-C10H21)	0	0			-	-

[Table 34]

661	S	CH	N(n-C10H21)	0	0			-	-
662	S	CH	N(n-C10H21)	0	0			-	-
663	S	CH	N(n-C10H21)	0	0			-	-
664	S	CH	N(n-C10H21)	0	0			-	-
665	S	CH	N(n-C10H21)	0	0			-	-
666	S	CH	N(n-C10H21)	0	0			-	-
667	S	CH	N(n-C10H21)	0	0			-	-
668	S	CH	N(n-C10H21)	0	0			-	-
669	S	CH	N(n-C10H21)	0	0			-	-
670	S	CH	N(n-C10H21)	0	0			-	-
671	S	CH	N(n-C10H21)	0	0			-	-
672	S	CH	N(n-C10H21)	0	0			-	-
673	S	CH	N(n-C10H21)	0	0			-	-

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(continued)

5	674	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
	675	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
10	676	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
	677	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
15	678	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
	679	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
20	680	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-

[Table 35]

25	681	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
30	682	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
35	683	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
	684	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
40	685	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-
45	686	S	CH	N(n-C ₁₀ H ₂₁)	0	0			-	-

[0099] The molecular weight of the compound, which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000, is preferably equal to or less than 2,000, more preferably equal to or less than 1,000, and particularly preferably equal to or less than 850. It is preferable that the molecular weight is equal to or less than the above upper limit, because then the solubility of the compound in a solvent can be improved.

[0100] From the viewpoint of film quality stability of the film, the molecular weight is preferably equal to or greater than 250, more preferably equal to or greater than 300, and even more preferably equal to or greater than 350.

[0101] In the present invention, the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 may be a compound (so-called oligomer) having a repeating unit. In the present invention, whether a compound has a molecular weight of equal to or less than 3,000 can be checked by the following molecular weight measurement method.

[0102] The molecular weight can be obtained through mass spectrometry using an ionization method such as matrix

assisted laser desorption/ionization (MALDI), atmospheric pressure chemical ionization (APCI), or electrospray ionization (ESI) or obtained by determining a weight-average molecular weight (Mw), expressed in terms of polystyrene, of a compound dissolved in tetrahydrofuran by using gel permeation chromatography (GPC).

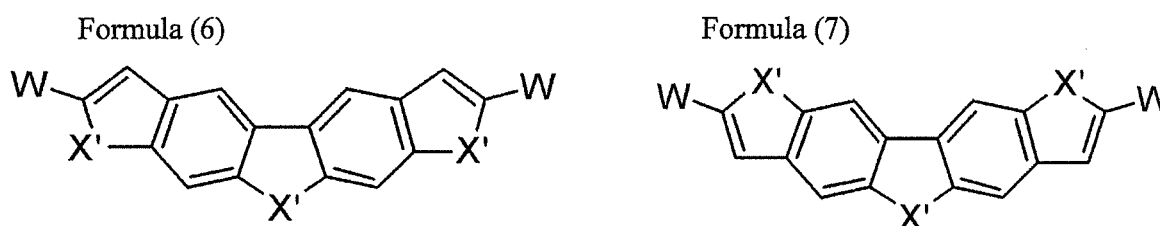
[0103] The compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 can be synthesized with reference to a method for synthesizing an organic semiconductor material of the present invention that will be described later.

[0104] Generally, for synthesizing the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000, any of reaction conditions may be used. As a reaction solvent, any of solvents may be used. Furthermore, in order to accelerate a ring-forming reaction, an acid or a base is preferably used, and an acid is particularly preferably used. Although optimal reaction conditions vary with the structure of the intended compound, they can be set with reference to the specific reaction conditions described in the aforementioned documents.

[0105] A synthetic intermediate having various substituents can be synthesized using known reactions in combination. Furthermore, various substituents may be introduced into the intermediate at any stage. After the intermediate is synthesized, it is preferable to purify the intermediate by column chromatography, recrystallization, or the like and then further purify it by sublimation. By the sublimation purification, it is possible to separate organic impurities and to effectively remove an inorganic salt, a residual solvent, and the like.

<Method for synthesizing organic semiconductor material of the present invention>

[0106] In a method for synthesizing an organic semiconductor material of the present invention, a compound represented by the following Formula (6) or (7) and a compound represented by the following Formula (8) are reacted by heating in the presence of a transition metal catalyst and an organic solvent, and as a result, the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is synthesized.



[0107] In Formulae (6) and (7), each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom; and group; each W independently represents a halogen atom or a perfluoroalkylsulfonyloxy



[0108] First, Formulae (6) and (7) will be described.

[0109] In Formula (6), a preferred range of X' is the same as the preferred range of the combination of X and Z in Formula (1).

[0110] In Formula (7), a preferred range of X' is the same as the preferred range of the combination of X and Y in Formula (1).

[0111] In Formulae (6) and (7), each W independently represents a halogen atom or a perfluoroalkylsulfonyloxy group. W is preferably a halogen atom. In a case where W represents a halogen atom, the halogen atom is not particularly limited, and examples thereof include a fluorine atom, a chlorine atom, a bromine atom, an iodine atom, and the like. Among these, an iodine atom or a bromine atom is preferable, and a bromine atom is more preferable. In a case where W represents a perfluoroalkylsulfonyloxy group, the perfluoroalkylsulfonyloxy group is not particularly limited. The perfluoroalkylsulfonyloxy group is preferably a sulfonyloxy group substituted with a perfluoroalkyl group having 1 to 10 carbon atoms, and more preferably a trifluoromethylsulfonyloxy group.

[0112] Next, Formula (8) will be described.

[0113] R¹¹ represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

M represents magnesium, silicon, boron, tin, or zinc;

each R¹² independently represents a halogen atom, an alkyl group, an alkenyl group, an alkynyl group, an alkoxy group, or a hydroxyl group, and R¹²'s may be the same as or different from each other and may form a ring; and

i represents an integer of 1 to 3 and equals a valency of M - 1, here, in a case where M is boron, i may be 3.

[0114] R¹¹ represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

M represents magnesium, silicon, boron, tin, or zinc;

each R¹² independently represents a halogen atom, an alkyl group, an alkenyl group, an alkynyl group, an alkoxy group, or a hydroxyl group, and R¹²'s may be the same as or different from each other and may form a ring; and

i represents an integer of 1 to 3 and equals a valency of M - 1, here, in a case where M is boron, i may be 3.

Formula (8) $R^{11}\text{-M}(\text{R}^{12})_i$

5 **[0113]** In Formula (8), R^{11} represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent. A preferred range of R^{11} is the same as the preferred range of R^1 or R^2 in Formula (1).

[0114] In Formula (8), M represents magnesium, silicon, boron, tin, or zinc. M is preferably boron, zinc, or tin, and more preferably tin or zinc.

10 **[0115]** In Formula (8), each R^{12} independently represents a halogen atom, an alkyl group, an alkenyl group, an alkynyl group, an alkoxy group, or a hydroxyl group. R^{12} 's may be the same as or different from each other and may form a ring with each other. R^{12} is preferably a halogen atom, an alkyl group, or an alkoxy group.

[0116] In a case where M is boron, R^{12} is preferably an alkoxy group, and more preferably an alkoxy group having 1 to 10 carbon atoms. Furthermore, R^{12} 's may form a ring having 4 to 10 carbon atoms by being bonded to each other.

15 **[0117]** In a case where M is tin, R^{12} is preferably an alkyl group having 1 to 6 carbon atoms, and more preferably a methyl group.

[0118] In a case where M is zinc, R^{12} is preferably a halogen atom.

[0119] In Formula (8), i represents an integer of 1 to 3 and equals a valency of M - 1. Here, in a case where M is boron, i may be 3.

[0120] i is preferably 2 or 3.

20 **[0121]** In a case where M is boron and i is 3, $\text{-B}(\text{R}^{12})_3$ is accompanied by an arbitrary cation $(\text{X}^3)^+$ and represents a salt of $\text{-B}(\text{R}^{12})_3(\text{X}^3)^+$.

25 **[0122]** Examples of the transition metal catalyst used in the method for synthesizing an organic semiconductor material of the present invention include a palladium catalyst such as tetrakis triphenylphosphine palladium (0), tris(dibenzylideneacetone)dipalladium (0), palladium (II) acetate, palladium (II) chloride, a [1,1'-bis(diphenylphosphino)ferrocene]dichloropalladium (II)/dichloroethane complex, [1,3-bis(diphenylphosphino)propane]palladium (II) dichloride, or bis(triphenylphosphine)palladium (II) dichloride, a copper catalyst such as copper (II) chloride, copper (I) chloride, copper (0), cuprous oxide, or copper (II) oxide, a nickel catalyst such as [1,3-bis(diphenylphosphino)propane]nickel (II) dichloride, or dibromobis(triphenylphosphine)nickel (II), bis(1,5-cyclooctadiene)nickel (0), and the like. Among these, a palladium catalyst is preferable. One kind of transition metal catalyst may be used singly, or two or more kinds thereof may be used in combination. Furthermore, these transition metal catalysts can be used in combination with an appropriate ligand.

30 **[0123]** As the ligand, for example, a phosphine ligand such as triphenylphosphine, tri-t-butylphosphine, tricyclohexylphosphine, 4,5-bis(diphenylphosphino)-9,9-dimethylxanthene, diphenylphosphinoferrrocene, 2,2'-bis(diphenylphosphino)-1,1'-binaphthyl, diphenylphosphinopropane, 2-dicyclohexylphosphino-2',4',6'-triisopropylbiphenyl, or 2-dicyclohexylphosphino-2',6'-dimethoxybiphenyl is particularly preferable.

35 **[0124]** The organic solvent used in the method for synthesizing an organic semiconductor material of the present invention is not particularly limited. Examples thereof include organic solvents exemplified as organic solvents usable in a coating solution for a non-light-emitting organic semiconductor device which will be described later. Among these, N,N-dimethylformamide, toluene, tetrahydrofuran, dimethoxyethane, and the like are preferable.

40 **[0125]** As the heating conditions in the method for synthesizing an organic semiconductor material of the present invention, the heating temperature is preferably 20°C to 120°C, and more preferably 40°C to 100°C.

[0126] The heating time is preferably 1 hour to 48 hours, and more preferably 5 hours to 24 hours.

[0127] At the time of heating, it is preferable to perform stirring.

<Structure of organic transistor>

45 **[0128]** The organic transistor of the present invention has a semiconductor active layer containing the compound which is represented by the Formula (1) and has a molecular weight of equal to or less than 3,000.

[0129] The organic transistor of the present invention may further have layers other than the semiconductor active layer.

50 **[0130]** The organic transistor of the present invention is preferably used as an organic field effect transistor (FET), and is more preferably used as an insulated gate-type FET in which the gate is insulated from channels.

[0131] Hereinafter, preferred structural aspects of the organic transistor of the present invention will be specifically described by using drawings, but the present invention is not limited to the aspects.

(Lamination structure)

55 **[0132]** The lamination structure of an organic field effect transistor is not particularly limited, and various known structures can be adopted.

[0133] For example, the organic transistor of the present invention can adopt a structure (bottom gate/top contact

type) in which an electrode, an insulator layer, a semiconductor active layer (organic semiconductor layer), and two electrodes are arranged in this order on the upper surface of a substrate which is a lower most layer. In this structure, the electrode on the upper surface of the substrate as the lower most layer is provided in a portion of the substrate, and the insulator layer is so disposed that it comes into contact with the substrate in a portion other than the electrode. The two electrodes provided on the upper surface of the semiconductor active layer are arranged in a state of being separated from each other.

[0134] Fig. 1 shows the constitution of a bottom gate/top contact-type element. Fig. 1 is a schematic view showing a section of an exemplary structure of the organic transistor manufactured as a substrate for measuring FET characteristics in examples of the present invention. In the organic transistor shown in Fig. 1, a substrate 11 is disposed as a lower most layer, an electrode 12 is provided in a portion of the upper surface thereof, and an insulator layer 13 is provided such that it covers the electrode 12 and contacts the substrate 11 in a portion other than the electrode 12. On the upper surface of the insulator layer 13, a semiconductor active layer 14 is provided, and in a portion of the upper surface thereof, two electrodes 15a and 15b are arranged in a state of being separated from each other.

[0135] In the organic transistor shown in Fig. 1, the electrode 12 is a gate, and the electrode 15a and the electrode 15b are a drain and a source respectively. The organic transistor shown in Fig. 1 is an insulated gate-type FET in which a channel as a path of electric currents between the drain and the source is insulated from the gate.

[0136] As an example of the structure of the organic transistor of the present invention, a bottom gate/bottom contact-type element can be exemplified.

[0137] Fig. 2 shows the constitution of the bottom gate/bottom contact-type element. Fig. 2 is a schematic view showing a section of the structure of an organic transistor manufactured as a substrate for measuring FET characteristics in examples of the present invention. In the organic transistor shown in Fig. 2, a substrate 31 is disposed as a lower most layer, an electrode 32 is provided in a portion of the upper surface thereof, and an insulator layer 33 is provided such that it covers the electrode 32 and comes into contact with the substrate 31 in a portion other than the electrode 32. Furthermore, a semiconductor active layer 35 is provided on the upper surface of the insulator layer 33, and electrodes 34a and 34b are in a lower portion of the semiconductor active layer 35.

[0138] In the organic transistor shown in Fig. 2, the electrode 32 is a gate, and the electrode 34a and the electrode 34b are a drain and a source respectively. The organic transistor shown in Fig. 2 is an insulated gate-type FET in which a channel as a path of electric currents between the drain and the source is insulated from the gate.

[0139] As the structure of the organic transistor of the present invention, a top gate/top contact-type element in which an insulator and a gate electrode are in the upper portion of a semiconductor active layer or a top gate/bottom contact-type element can also be preferably used.

(Thickness)

[0140] In a case where the organic transistor of the present invention needs to be a thinner transistor, the total thickness of the transistor is preferably, for example, 0.1 μm to 0.5 μm .

(Sealing)

[0141] In order to improve the preservation stability of the organic transistor element by blocking the organic transistor element from the atmosphere or moisture, the entirety of the organic transistor element may be sealed with a metal sealing can, glass, an inorganic material such as silicon nitride, a polymer material such as perylene, a low-molecular weight material, or the like.

[0142] Hereinafter, preferred aspects of the respective layers of the organic transistor of the present invention will be described, but the present invention is not limited to the aspects.

<Substrate>

(Material)

[0143] The organic transistor of the present invention preferably includes a substrate.

[0144] The material of the substrate is not particularly limited, and known materials can be used. Examples of the material include a polyester film such as polyethylene naphthalate (PEN) or polyethylene terephthalate (PET), a cycloolefin polymer film, a polycarbonate film, a triacetylcellulose (TAC) film, a polyimide film, a material obtained by bonding these polymer films to extremely thin glass, ceramics, silicon, quartz, glass, and the like. Among these, silicon is preferable.

<Electrode>

(Material)

5 **[0145]** The organic transistor of the present invention preferably includes an electrode.

[0146] As the material constituting the electrode, known conductive materials such as a metal material like Cr, Al, Ta, Mo, Nb, Cu, Ag, Au, Pt, Pd, In, Ni, or Nd, an alloy material of these, a carbon material, and a conductive polymer can be used without particular limitation.

10 (Thickness)

[0147] The thickness of the electrode is not particularly limited, but is preferably 10 nm to 50 nm.

[0148] A gate width (or a channel width) W and a gate length (or a channel length) L are not particularly limited. However, a ratio of W/L is preferably equal to or greater than 10, and more preferably equal to or greater than 20.

15

<Acceptor>

(Material)

20 **[0149]** The organic transistor of the present invention preferably includes an acceptor for accelerating injection of carriers. Preferred examples of the material include known 2,3,5,6-tetrafluoro-7,7,8,8-tetracyanoquinodimethane (F4-TCNQ) and the like.

(Thickness)

25

[0150] The thickness of the acceptor is not particularly limited and is preferably equal to or less than 5 nm.

<Insulating layer>

30 (Material)

[0151] The material constituting the insulating layer is not particularly limited as long as a necessary insulating effect is obtained. Examples of the material include silicon dioxide, silicon nitride, a fluorine polymer-based insulating material such as polytetrafluoroethylene (PTFE) or CYTOP, a polyester insulating material, a polycarbonate insulating material,

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an acryl polymer-based insulating material, an epoxy resin-based insulating material, a polyimide insulating material, a polyvinyl phenol resin-based insulating material, a poly p-xylylene resin-based insulating material, and the like.

[0152] A surface treatment may be performed on the upper surface of the insulating layer. For example, it is possible to preferably use an insulating layer in which the silicon dioxide surface thereof is subjected to the surface treatment by being coated with hexamethyldisilazane (HMDS), octadecyltrichlorosilane (OTS), or β -phenethyltrimethoxysilane.

40

(Thickness)

[0153] The thickness of the insulating layer is not particularly limited. However, in a case where the film needs to be thinned, the thickness of the insulating layer is preferably 10 nm to 500 nm, more preferably 20 nm to 200 nm, and particularly preferably 50 nm to 200 nm.

45

<Semiconductor active layer>

(Material)

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[0154] The organic transistor of the present invention is characterized by having a semiconductor active layer containing the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000.

[0155] The semiconductor active layer may be a layer composed of the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 or a layer further containing a polymer binder (referred to as a polymer or a binder as well), which will be described later, in addition to the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000. Furthermore, the semiconductor active layer may contain a residual solvent used at the time of forming a film.

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[0156] The content of the polymer binder in the semiconductor active layer is not particularly limited. The content of

the polymer binder used is preferably within a range of 0% to 95% by mass, more preferably within a range of 10% to 90% by mass, even more preferably within a range of 20% to 80% by mass, and particularly preferably within a range of 30% to 70% by mass.

5 (Thickness)

[0157] The thickness of the semiconductor active layer is not particularly limited. In a case where the film needs to be thinned, the thickness of the semiconductor active layer is preferably 10 nm to 400 nm, more preferably 10 nm to 200 nm, and particularly preferably 10 nm to 100 nm.

10

[Method for manufacturing organic transistor]

[0158] A method for manufacturing an organic transistor of the present invention is characterized by including a step of preparing a semiconductor active layer by coating a substrate with a coating solution for a non-light-emitting organic semiconductor device of the present invention and drying the coating solution.

15

[0159] The coating solution for a non-light-emitting organic semiconductor device of the present invention will be described later.

[0160] The method for manufacturing an organic transistor of the present invention may or may not include a method for manufacturing an organic semiconductor film of the present invention that will be described later.

20

[0161] First, general methods in the method for manufacturing an organic transistor of the present invention will be described.

(Film forming method)

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[0162] In the method for manufacturing an organic transistor of the present invention, the compound of the present invention may be formed into a film on a substrate by any method.

[0163] At the time of forming the film, the substrate may be heated or cooled. By varying the temperature of the substrate, it is possible to control the film quality or the packing of molecules in the film. The temperature of the substrate is not particularly limited. The temperature is preferably between 0°C to 200°C, more preferably between 15°C to 100°C, and particularly preferably between 20°C to 95°C.

30

[0164] The compound of the present invention can be formed into a film on a substrate by a vacuum process or a solution process, and both of the processes are preferable.

[0165] Specific examples of the film forming method by a vacuum process include a physical vapor deposition method such as a vacuum vapor deposition method, a sputtering method, an ion plating method, or a molecular beam epitaxy (MBE) method and a chemical vapor deposition (CVD) method such as plasma polymerization, and it is particularly preferable to use a vacuum vapor deposition method.

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[0166] Herein, the film forming method by a solution process refers to a method of dissolving an organic compound in a solvent which can dissolve the compound and forming a film by using the solution. Specifically, it is possible to use general methods like a coating method such as a casting method, a dip coating method, a die coater method, a roll coater method, a bar coater method, or a spin coating method, various printing methods such as an ink jet method, a screen printing method, a gravure printing method, a flexographic printing method, an offset printing method, or a micro-contact printing method, and a Langmuir-Blodgett (LB) method. It is particularly preferable to use a casting method, a spin coating method, an ink jet method, a gravure printing method, a flexographic printing method, an offset printing method, or a micro-contact printing method.

40

[0167] The organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention is preferably prepared by a solution coating method. In a case where the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention contains a polymer binder, it is preferable to prepare a coating solution by dissolving or dispersing a material, which will be formed into a layer, and a polymer binder in an appropriate solvent and to form the organic semiconductor film by various coating methods.

45

[0168] Next, more preferred aspects of the method for manufacturing an organic transistor of the present invention will be described.

50

[Method for manufacturing organic semiconductor film]

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[0169] A preferred method for manufacturing an organic semiconductor film of the present invention is characterized in that in a state where a distance between a substrate A and a member B not being fixed to the substrate A is kept constant or in a state where the substrate A and the member B are caused to remain in contact with each other, a coating solution prepared by dissolving the compound, which is represented by Formula (1A) described above and has a mo-

lecular weight of equal to or less than 3,000, in a solvent is dropped onto a portion within the surface of the substrate A such that the coating solution contacts both of the substrate A and the member B, and the dropped coating solution is slowly dried, such that crystals of the compound, which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000, are precipitated and a semiconductor active layer is formed; here, as long as the distance between the substrate A and the member B is kept constant or as long as the substrate A and the member B are caused to remain in contact with each other, the positional relationship between the substrate A and the member B may be maintained or changed when the coating solution is dropped or dried.

[0170] The preferred method for manufacturing an organic semiconductor film of the present invention will be described based on drawings.

[0171] Figs. 3A to 3C are schematic views showing an example of the method for manufacturing an organic semiconductor film of the present invention.

[0172] Fig. 3A shows a state where the coating solution (reference 41) has not yet been dropped onto the substrate A (reference 42). In this state, the distance between the substrate A (reference 42) and the member B (reference 43) not being fixed to the substrate A (reference 42) is kept constant.

[0173] Fig. 3B shows a state where the coating solution (reference 41) is then dropped onto a portion within the surface of the substrate A (reference 42) such that the coating solution contacts both of the substrate A (reference 42) and the member B (reference 43).

[0174] Fig. 3C is a schematic view showing an aspect in which the dropped coating solution (reference 41) is then slowly dried in a state where the positional relationship between the substrate A (reference 42) and the member B (reference 43) is maintained. The coating solution (reference 41) starts to be dried from both edges where the film thickness is small and is crystallized, and in this way, large-sized crystals can be obtained.

[0175] Figs. 4A to 4C are schematic views showing another example of the method for manufacturing an organic semiconductor film of the present invention.

[0176] Fig. 4A shows a state where the coating solution (reference 41) has not yet been dropped onto the substrate A (reference 42). In this state, the substrate A (reference 42) and the member B (reference 43) are caused to remain in contact with each other.

[0177] Fig. 4B1 shows a state where the coating solution (reference 41) is then dropped onto a portion within the surface of the substrate A (reference 42) such that the coating solution contacts both of the substrate A (reference 42) and the member B (reference 43). It is Fig. 4B2 that is obtained when Fig. 4B1 is seen in a vertical direction (Y-axis direction). As is evident from Fig. 4B2, the coating solution (reference 41) is dropped on a portion within the surface of the substrate A (reference 42).

[0178] Fig. 4C is a schematic view showing an aspect in which the dropped coating solution (reference 41) is then slowly dried in a state where the positional relationship between the substrate A (reference 42) and the member B (reference 43) is maintained. The coating solution (reference 41) starts to be dried from both edges where the film thickness is small and is crystallized, and in this way, large-sized crystals can be obtained.

[0179] Comparing the aspect shown in Figs. 3A to 3C with the aspect shown in Figs. 4A to 4C, the aspect shown in Figs. 4A to 4C in which the substrate A (reference 42) and the member B (reference 43) are caused to remain in contact with each other is preferable, because in this aspect, the film quality is excellent, a holding mechanism is not necessary, and the distance between the member B (reference 43) and the substrate A (reference 42) can be accurately maintained.

[0180] Figs. 5A to 5C are schematic vies showing another example of the method for manufacturing an organic semiconductor film of the present invention.

[0181] Fig. 5A shows a state where the coating solution (reference 41) has not yet been dropped onto the substrate A (reference 42). In this state, the substrate A (reference 42) and the member B (reference 43) are caused to remain in contact with each other.

[0182] Fig. 5B shows a state where the coating solution (reference 41) is then dropped onto a portion within the surface of the substrate A (reference 42) such that the coating solution contacts both of the substrate A (reference 42) and the member B (reference 43).

[0183] Fig. 5C is a schematic view showing an aspect in which the dropped coating solution is then slowly dried by changing the positional relationship between the substrate A (reference 42) and the member B (reference 43).

[0184] In the method for manufacturing an organic semiconductor film of the present invention, as long as the state where the distance between the substrate A and the member B is kept constant or as long as the substrate A and the member B are caused to remain in contact with each other, at the time when the coating solution is dropped or dried, the positional relationship between the substrate A and the member B may be maintained or changed. As shown in Fig. 5C, by changing the the positional relationship between the substrate A (reference 42) and the member B (reference 43) in the -X direction on the coordinates, the coating solution (reference 41) starts to be dried from the edge (+X direction on the coordinates) far away from the member B (reference 43) and is crystallized, and in this way, large-sized crystals can be obtained.

[0185] Comparing the aspect shown in Figs. 5A to 5C with the aspect shown in Figs. 4A to 4C, the aspect shown in

Figs. 4A to 4C is preferable because in this aspect, the film quality is excellent, and large-sized crystals are easily obtained.

[0186] Examples of the substrate A used in the method for manufacturing an organic semiconductor film of the present invention include those used as a substrate of the organic transistor of the present invention. As the substrate A, a substrate in which an insulating layer is formed on the substrate of the organic transistor of the present invention is preferable.

[0187] The member B used in the method for manufacturing an organic semiconductor film of the present invention is not particularly limited. The material of the member B is preferably glass; quartz; silicon; Teflon (registered trademark); or plastic such as polyethylene or polypropylene, and more preferably glass.

[0188] The size of the member B (reference 43) (for example, the length of the member B (reference 43) in the X-axis direction and the Y-axis direction in Fig. 4B2) is not particularly limited. The lower limit of the length of one side of the member B (reference 43) is preferably equal to or greater than 0.1% of the length of one side of the substrate A (reference 42), more preferably equal to or greater than 1% of the length one side of the substrate A, particularly preferably equal to or greater than 10% of the length of one side of the substrate A, and more particularly preferably equal to or greater than 20% of the length of one side of the substrate A. The upper limit of the length of one side of the member B (reference 43) is preferably equal to or less than 80% of the length of one side of the substrate A (reference 42), more preferably equal to or less than 70% of the length of one side of the substrate A, and particularly preferably equal to or less than 50% of the length of one side of the substrate A.

[0189] The height of the member B (reference 43) (for example, the length of the member B (reference 43) in the Z-axis direction in Fig. 4B1) is not particularly limited. The height of the member B (reference 43) is preferably 1 mm to 50 mm, and more preferably 5 mm to 20 mm.

[0190] Fig. 6 is a schematic view of the substrate A and the member B. In Fig. 6, d indicates the length of the member B in the x-axis direction in Fig. 4B2; w indicates the length of the member B in the y-axis direction in Fig. 4B2; and h indicates the length of the member B in the z-axis direction in Fig. 4B1. h/d in the member B shown in Fig. 6 is preferably 0.01 to 10, and more preferably 0.1 to 5, because then the member B does not collapse. w/d is preferably 1 to 1,000, and more preferably 5 to 100, because then the region in which crystals are formed widens.

(Film forming method)

[0191] In the method for manufacturing an organic semiconductor film of the present invention, at the time of forming a film, the substrate may be heated or cooled. By varying the temperature of the substrate, it is possible to control the film quality or the packing of molecules in the film. The temperature of the substrate is not particularly limited. However, it is preferably between 0°C to 200°C, more preferably between 15°C to 100°C, and particularly preferably between 20°C to 95°C.

[0192] When the compound of the present invention is formed into a film on the substrate, a solution process is used for forming the film.

[0193] Herein, the film forming method by a solution process refers to a method of dissolving an organic compound in a solvent which can dissolve the compound and forming a film by using the solution. Specifically, it is possible to use general methods like various printing methods such as a drop casting method, an ink jet method, a screen printing method, a gravure printing method, a flexographic printing method, an offset printing method, and a micro-contact printing method. Among these, an ink jet method, a gravure printing method, a flexographic printing method, an offset printing method, and a micro-contact printing method are preferably used, and a flexographic printing method, a micro-contact printing method, and an ink jet method are particularly preferably used.

(Coating solution/coating solution for non-light-emitting organic semiconductor device)

[0194] Hereinafter, a coating solution for a non-light-emitting organic semiconductor device of the present invention that can be used as a coating solution for the method for manufacturing an organic semiconductor film of the present invention will be described.

[0195] The present invention also relates to a coating solution for a non-light-emitting organic semiconductor device containing the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000.

[0196] In a case where a film is formed on a substrate by using a solution process, by using a coating solution, which is obtained by dissolving or dispersing a material for forming a layer in an appropriate organic solvent (for example, a hydrocarbon-based solvent such as hexane, octane, decane, toluene, xylene, mesitylene, ethylbenzene, amylbenzene, decalin, 1-methylnaphthalene, 1-ethylnaphthalene, 1,6-dimethylnaphthalene, or tetralin, a ketone-based solvent such as acetone, methyl ethyl ketone, methyl isobutyl ketone, cyclohexanone, acetophenone, propiophenone, or butyroph- enone, a halogenated hydrocarbon-based solvent such as dichloroethane, chloroform, tetrachloromethane, dichlo- roethane, trichloroethane, tetrachloroethane, chlorobenzene, 1,2-dichlorobenzene, 1,2,4-trichlorobenzene, chlorotolu- ene, or 1-fluoronaphthalene, a heterocyclic solvent such as pyridine, picoline, quinoline, thiophene, 3-butylthiophene,

or thieno[2,3-b]thiophene, a halogenated heterocyclic solvent such as 2-chlorothiophene, 3-chlorothiophene, 2,5-dichlorothiophene, 3,4-dichlorothiophene, 2-bromothiophene, 3-bromothiophene, 2,3-dibromothiophene, 2,4-dibromothiophene, 2,5-dibromothiophene, 3,4-dibromothiophene, or 3,4-dichloro-1,2,5-thiadiazole, an ester-based solvent such as ethyl acetate, butyl acetate, amyl acetate, 2-ethylhexyl acetate, γ -butyrolactone, or phenyl acetate, an alcohol-based solvent such as methanol, propanol, butanol, pentanol, hexanol, cyclohexanol, methyl cellosolve, ethyl cellosolve, or ethylene glycol, an ether-based solvent such as dibutyl ether, tetrahydrofuran, dioxane, dimethoxyethane, anisole, ethoxybenzene, propoxybenzene, isopropoxybenzene, butoxybenzene, 2-methylanisole, 3-methylanisole, 4-methylanisole, 4-ethylanisole, dimethylanisole (any of 2,3-, 2,4-, 2,5-, 2,6-, 3,4-, 3,5-, and 3,6-dimethylanisoles), or 1,4-benzodioxane, an amide/imide-based solvent such as N,N-dimethylformamide, N,N-dimethylacetamide, 1-methyl-2-pyrrolidone, 1-methyl-2-imidazolidinone, or 1,3-dimethyl-2-imidazolidinone, a sulfoxide-based solvent such as dimethylsulfoxide, a phosphoric acid ester-based solvent such as trimethyl phosphate, a nitrile-based solvent such as acetonitrile or benzonitrile, a nitro-based solvent such as nitromethane or nitrobenzene) and/or water, a film can be formed by various coating methods. One kind of solvent may be used singly, or plural kinds thereof may be used in combination. Among these, a hydrocarbon-based solvent, a halogenated hydrocarbon-based solvent, a heterocyclic solvent, a halogenated heterocyclic solvent, or an ether-based solvent is preferable, toluene, xylene, mesitylene, amylbenzene, tetralin, acetophenone, propiophenone, butyrophenone, dichlorobenzene, anisole, ethoxybenzene, propoxybenzene, isopropoxybenzene, butoxybenzene, 2-methylanisole, 3-methylanisole, 4-methylanisole, 1-fluoronaphthalene, 3-chlorothiophene, and 2,5-dibromothiophene are more preferable, and toluene, xylene, tetralin, acetophenone, propiophenone, butyrophenone, anisole, ethoxybenzene, propoxybenzene, butoxybenzene, 2-methylanisole, 3-methylanisole, 4-methylanisole, 1-fluoronaphthalene, 3-chlorothiophene, and 2,5-dibromothiophene are particularly preferable.

[0197] Among the above solvents, it is preferable to use solvents having a boiling point of equal to or higher than 100°C for the coating solution for a non-light-emitting organic semiconductor device of the present invention, because then the film quality becomes excellent, and crystals with a large area are easily obtained. The solvent having a boiling point of equal to or higher than 100°C is preferably used in the method for manufacturing an organic semiconductor film of the present invention.

[0198] Among the above solvents, examples of the solvents having a boiling point of equal to or higher than 100°C include toluene, xylene, mesitylene, tetralin, acetophenone, propiophenone, butyrophenone, dichlorobenzene, anisole, ethoxybenzene, propoxybenzene, isopropoxybenzene, butoxybenzene, 2-methylanisole, 3-methylanisole, and 4-methylanisole. Among these, toluene, xylene, tetralin, acetophenone, propiophenone, butyrophenone, anisole, ethoxybenzene, propoxybenzene, butoxybenzene, 2-methylanisole, 3-methylanisole, and 4-methylanisole are more preferable.

[0199] From the viewpoint of environmental load and toxicity to human beings, the solvents having a boiling point of equal to or higher than 100°C are preferably non-halogen-based solvents.

[0200] The concentration of the compound, which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000, in the coating solution is preferably 0.005% to 5% by mass, more preferably 0.01% to 3% by mass, and particularly preferably 0.02% to 1% by mass. If the concentration is within the above range, it is easy to form a film at any thickness. In the coating solution for a non-light-emitting organic semiconductor device, the concentration of the compound represented by Formula (1A) is particularly preferably equal to or greater than 0.4% by mass, because then a coating film composed of large-sized crystals is easily formed. In Tetrahedron 66 (2010) 8778-8784, a film for measuring oxidation-reduction potential is manufactured using a coating solution containing C6-TBBT or C12-TBBT at low concentration. For the same reason as described above, it is preferable that the concentration of the coating solution for a non-light-emitting organic semiconductor device is high.

[0201] In the method for manufacturing an organic semiconductor film of the present invention, the coating solution is dropped onto a portion within the surface of the substrate A such that the coating solution contacts both of the substrate A and the member B.

[0202] At the time of dropping the coating solution, it is preferable to drop a single drop of the coating solution or to drop the coating solution drop by drop in a case where two or more drops of the coating solution are dropped, because then a portion in which a film of the coating solution having a small thickness is easily formed on the substrate A, and it is easy to accelerate drying of the coating solution from edge.

[0203] In a case where the coating solution is dropped, the volume of a single drop of the coating solution is preferably 0.01 ml to 0.2 ml, and more preferably 0.02 ml to 0.1 ml.

[0204] By dropping the coating solution onto a portion within the surface of the substrate A such that the coating solution contacts both of the substrate A and the member B, it is possible to reduce the film thickness at the edge of the coating solution.

[0205] The contact angle between the coating solution and the substrate A is preferably 0° to 90°, and more preferably 10° to 80°.

[0206] The coating solution and the member B preferably form a meniscus, and more preferably form a concave meniscus from the viewpoint of the film quality.

[0207] Usually, in order to form a film by a solution process, the material needs to dissolve in the solvent exemplified

above, but simply dissolving in a solvent is not good enough. Generally, even the material formed into a film by a vacuum process can dissolve in a solvent to some extent. The solution process includes a step of coating a substrate with a material by dissolving the material in a solvent and then forming a film by evaporating the solvent, and many of the materials not being suitable for being formed into a film by the solution process have high crystallinity. Therefore, the material is inappropriately crystallized (aggregated) in the aforementioned step, and hence it is difficult to form an excellent film. This problem has been considered in the related art. In contrast, according to the method for manufacturing an organic semiconductor film of the present invention, it is possible to form an organic semiconductor film in a state of causing the precipitation of crystals.

[0208] For the coating solution for a non-light-emitting organic semiconductor device of the present invention, an aspect is also preferable in which the coating solution contains the compound, which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000, but does not contain a polymer binder.

[0209] Furthermore, the coating solution for a non-light-emitting organic semiconductor device of the present invention may contain the compound, which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000, and a polymer binder. In this case, by using a coating solution obtained by dissolving or dispersing a material for forming a layer and the polymer binder in an appropriate solvent described above, a film can be formed by various coating methods. The polymer binder can be selected from those described above.

[0210] From the viewpoint of the uniformity of the film quality of the coating film to be formed, the coating solution for a non-light-emitting organic semiconductor device preferably contains a polymer.

[0211] The coating solution for a non-light-emitting organic semiconductor device may contain only one kind of compound represented by Formula (2) or contain two or more kinds thereof. From the viewpoint of the storage stability (inhibition of crystal precipitation during storage) of the coating solution, the coating solution preferably contains two or more kinds of compound represented by Formula (2).

[0212] From the viewpoint of the suitability for various printing methods, the coating solution for a non-light-emitting organic semiconductor device preferably has a viscosity of equal to or greater than 10 mPa·s.

[0213] The coating solution for a non-light-emitting organic semiconductor device may contain additives other than a polymer binder, such as a surfactant, an antioxidant, a crystallization control agent, and a crystal orientation control agent.

[0214] Examples of the surfactant are not particularly limited and include nonionic surfactants such as polyoxyethylene alkyl ethers, polyoxyethylene alkyl allyl ethers, polyoxyethylene-polyoxypropylene block copolymers, sorbitan fatty acid esters, and a polyoxyethylene sorbitan fatty acid ester; fluorine-based surfactants such as MEGAFACE F171 and F176 (manufactured by DIC Corporation), FLUORAD FC430 (manufactured by Sumitomo 3M Ltd.), SURFYNOL E1004 (manufactured by ASAHI GLASS CO., LTD.), and PF656 and PF6320 manufactured by OMNOVA Solutions Inc.; and organosiloxane polymers such as polysiloxane polymers KP-341 (manufactured by Shin-Etsu Chemical Co., Ltd.), KF-410 (manufactured by Shin-Etsu Chemical Co., Ltd.), KF-412 (manufactured by Shin-Etsu Chemical Co., Ltd.), KF-96-100cs (manufactured by Shin-Etsu Chemical Co., Ltd.), BYK-322 (manufactured by BYK Additives & Instruments), and BYK-323 (manufactured by BYK Additives & Instruments).

[0215] The content of the surfactant in the coating solution is preferably about 0.001% to about 1% by mass.

[0216] Examples of the antioxidant include a phenol-based antioxidant, a phosphorus-based antioxidant, a sulfur-based antioxidant, and the like.

[0217] Specific examples of the phenol-based antioxidant include 2,6-di-*t*-butyl-4-methylphenol, *n*-octadecyl-3-(3',5'-di-*t*-butyl-4'-hydroxyphenyl)propionate, tetrakis [methylene-3-(3,5-di-*t*-butyl-4-hydroxyphenyl)propionate]methane, tris(3,5-di-*t*-butyl-4-hydroxybenzyl)isocyanurate, 4,4'-butylidenebis-(3-methyl-6-*t*-butylphenol), triethylene glycol bis[3-(3-*t*-butyl-4-hydroxy-5-methylphenyl)propionate], and 3,9-bis[2-[3-(3-*t*-butyl-4-hydroxy-5-methylphenyl)propionyloxy]-1,1-dimethylethyl]-2,4,8,10-tetraoxaspiro[5,5]undecane.

[0218] Examples of commercially available products of the phenol-based antioxidant include IRGANOX 1010, IRGANOX 1035, IRGANOX 1076, IRGANOX 1135, IRGANOX 245, IRGANOX 259, IRGANOX 295, and IRGANOX 3114 (all manufactured by BASF SE), ADEKA STAB AO-20, ADEKA STAB AO-30, ADEKA STAB AO-40, ADEKA STAB AO-50, ADEKA STAB AO-60, ADEKA STAB AO-70, ADEKA STAB AO-80, ADEKA STAB AO-90, and ADEKA STAB AO-330 (all manufactured by ADEKA Corporation), SUMILIZER BHT, SUMILIZER BP-101, SUMILIZER GA-80, SUMILIZER MDP-S, SUMILIZER BBM-S, SUMILIZER GM, SUMILIZER GS(F), and SUMILIZER GP (all manufactured by Sumitomo Chemical Co., Ltd.), HOSTANOX O10, HOSTANOX 016, HOSTANOX 014, and HOSTANOX O3 (all manufactured by CLARIANT), ANTAGE BHT, ANTAGE W-300, ANTAGE W-400, and ANTAGE W-500 (all manufactured by Kawaguchi Chemical Industry Co., LTD.), SEENOX 224M and SEENOX 326 M (all manufactured by SHIPRO KASEI KAISHA, LTD.), YOSHINOX BHT, YOSHINOX BB, TOMINOX TT, and TOMINOX 917 (all manufactured by YOSHITOMI PHARMACEUTICAL INDUSTRIES, LTD.), TTHP (manufactured by TORAY INDUSTRIES, INC.), and the like.

[0219] Specific examples of the phosphorus-based antioxidant include trisnonylphenyl phosphite, tris(2,4-di-*t*-butylphenyl)phosphite, distearyl pentaerythritol diphosphite, bis(2,4-di-*t*-butylphenyl)pentaerythritol phosphite, bis(2,6-di-*t*-butyl-4-methylphenyl)pentaerythritol phosphite, 2,2-methylenebis(4,6-di-*t*-butylphenyl)octylphosphite, tetrakis(2,4-di-*t*-butylphenyl)-4,4-biphenylene-di-phosphonite, and the like. Examples of commercially available products of the phos-

phorus-based antioxidant include ADEKA STAB 1178 (manufactured by ADEKA Corporation), SUMILIZER TNP (manufactured by Sumitomo Chemical Co., Ltd.), JP-135 (manufactured by JOHOKU CHEMICAL CO., LTD), ADEKA STAB 2112 (manufactured by ADEKA Corporation), JPP-2000 (manufactured by JOHOKU CHEMICAL CO., LTD), WESTON 618 (manufactured by General Electric), ADEKA STAB PEP-24G (manufactured by ADEKA Corporation), ADEKA STAB PEP-36 (manufactured by ADEKA Corporation), ADEKA STAB HP-10 (manufactured by ADEKA Corporation), SAND-STAB P-EPQ (manufactured by Sandoz), PHOSPHITE 168 (manufactured by Ciba Specialty Chemicals, Inc.), and the like.

[0220] Specific examples of the sulfur-based antioxidant include dilauryl-3,3'-thiodipropionate, dimyristyl-3,3'-thiodipropionate, distearyl-3,3'-thiodipropionate, pentaerythritol tetrakis(3-laurylthiopropionate), and the like. Examples of commercially available products of the sulfur-based antioxidant include SUMILIZER TPL (manufactured by Sumitomo Chemical Co., Ltd.), YOSHINOX DLTP (manufactured by YOSHITOMI PHARMACEUTICAL INDUSTRIES, LTD.), ANTIOX L (manufactured by NOF CORPORATION), SUMILIZER TPM (manufactured by Sumitomo Chemical Co., Ltd.), YOSHINOX DMTP (manufactured by YOSHITOMI PHARMACEUTICAL INDUSTRIES, LTD.), ANTIOX M (manufactured by NOF CORPORATION), SUMILIZER TPS (manufactured by Sumitomo Chemical Co., Ltd.), YOSHINOX DSTP (manufactured by YOSHITOMI PHARMACEUTICAL INDUSTRIES, LTD.), ANTIOX S (manufactured by NOF CORPORATION), ADEKA STAB AO-412S (manufactured by ADEKA Corporation), SEENOX 412S (manufactured by SHIPRO KASEI KAISHA, LTD.), SUMILIZER TDP (manufactured by Sumitomo Chemical Co., Ltd.), and the like.

[0221] The content of the antioxidant in the coating solution is preferably about 0.01% to 5% by mass.

(Drying)

[0222] In the method for manufacturing an organic semiconductor film of the present invention, the dropped coating solution is slowly dried so as to cause the precipitation of crystals of the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000, thereby forming a semiconductor active layer.

[0223] From the viewpoint of the film quality, it is preferable that the coating solution is air-dried on the heated substrate A and then dried under reduced pressure.

[0224] The temperature of the substrate A at the time of air drying is preferably 20°C to 100°C, and more preferably 50°C to 80°C.

[0225] The air drying is preferably performed for 0.5 hours to 20 hours, and more preferably performed for 1 hour to 10 hours.

[0226] The temperature at the time of drying under reduced pressure is preferably 20°C to 100°C, and more preferably 40°C to 80°C.

[0227] The drying under reduced pressure is preferably performed for 1 hour to 20 hours, and more preferably performed for 2 hours to 10 hours.

[0228] The pressure at the time of drying under reduced pressure is preferably 10^{-6} Pa to 10^{-2} Pa, and more preferably 10^{-5} Pa to 10^{-3} Pa.

[0229] In the method for manufacturing an organic semiconductor film of the present invention, crystals of the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 are precipitated.

[0230] Whether or not the crystals have been precipitated can be checked by observation using a polarizing microscope.

[Organic semiconductor material for non-light-emitting organic semiconductor device]

[0231] The present invention also relates to an organic semiconductor material for a non-light-emitting organic semiconductor device containing the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

(Non-light-emitting organic semiconductor device)

[0232] In the present specification, a "non-light-emitting organic semiconductor device" refers to a device which is not used for the purpose of emitting light. Particularly, a "non-light-emitting organic semiconductor device" refers to a device which is not used for the purpose of emitting visible light. The non-light-emitting organic semiconductor device preferably uses an electronic element having a layered structure consisting of films. The non-light-emitting organic semiconductor device includes an organic transistor, an organic photoelectric conversion element (a solid-state imaging element used for a photosensor, a solar cell used for energy conversion, or the like), a gas sensor, an organic rectifying element, an organic inverter, an information recording element, and the like. The organic photoelectric conversion element can be used for a photosensor (solid-state imaging element) and for energy conversion (a solar cell). Among these, an organic photoelectric conversion element and an organic transistor are preferable, and an organic transistor is more preferable. That is, the organic semiconductor material for a non-light-emitting organic semiconductor device of the present invention

is preferably a material for an organic transistor as described above.

(Organic semiconductor material)

5 **[0233]** In the present specification, the "organic semiconductor material" is an organic material showing characteristics of a semiconductor. Just as a semiconductor composed of an inorganic material, the organic semiconductor is classified into a p-type (hole-transporting) organic semiconductor material conducting holes as carriers and an n-type (electron-transporting) organic semiconductor material conducting electrons as carriers.

10 **[0234]** The compound of the present invention may be used as any of the p-type organic semiconductor material and the n-type organic semiconductor material, but is preferably used as the p-type. The ease with which the carriers flow in the organic semiconductor is represented by a carrier mobility μ . The higher the carrier mobility μ , the better. The carrier mobility μ is preferably equal to or greater than 1×10^{-3} cm²/Vs, more preferably equal to or greater than 1×10^{-1} cm²/Vs, particularly preferably equal to or greater than 3×10^{-1} cm²/Vs, more particularly preferably equal to or greater than 5×10^{-1} cm²/Vs, and even more particularly preferably equal to or greater than 1 cm²/Vs. The carrier mobility μ can be determined by the characteristics of the prepared field effect transistor (FET) element or by a time-of-flight (TOF) measurement method.

[Organic semiconductor film for non-light-emitting organic semiconductor device]

20 **[0235]** An organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention contains the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

[0236] The organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention is preferably manufactured by the method for manufacturing an organic semiconductor film of the present invention.

25 (Material)

[0237] The present invention also relates to the organic semiconductor film for a non-light-emitting organic semiconductor device containing the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

30 **[0238]** For the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention, an aspect is also preferable in which the film contains the compound, which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000, and does not contain a polymer binder.

[0239] Furthermore, the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention may contain the compound, which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000, and a polymer binder.

35 **[0240]** Examples of the polymer binder include an insulating polymer such as polystyrene, polycarbonate, polyarylate, polyester, polyamide, polyimide, polyurethane, polysiloxane, polysulfone, polymethyl methacrylate, polymethyl acrylate, cellulose, polyethylene, or polypropylene, a copolymer of these, rubber or a thermoplastic elastomer such as ethylene-propylene rubber, acrylonitrile-butadiene rubber, hydrogenated nitrile rubber, fluoro-rubber, a perfluoro elastomer, a tetrafluoroethylene-propylene copolymer, an ethylene-propylene-diene copolymer, styrene-butadiene rubber, polychloroprene, polyneoprene, butyl rubber, a methyl/phenyl silicone resin, a methyl/phenylvinyl/silicone resin, a methyl/vinyl/silicone resin, a fluorosilicone resin, acryl rubber, ethylene acryl rubber, chlorosulfonated polyethylene, chloropolyethylene, an epichlorohydrin copolymer, a polyisoprene-natural rubber copolymer, polyisoprene rubber, a styrene-isoprene block copolymer, a polyester-urethane copolymer, a polyether-urethane copolymer, a polyether ester thermoplastic elastomer, and polybutadiene rubber, a photoconductive polymer such as polyvinylcarbazole or polysilane, a conductive polymer such as polythiophene, polypyrrole, polyaniline, or poly p-phenylenevinylene, and a semiconductor polymer described in, for example, Chemistry of Materials, 2014, 26, 647.

[0241] One kind of polymer binder may be used singly, or plural kinds thereof may be used in combination.

40 **[0242]** The organic semiconductor material may be uniformly mixed with the polymer binder. Alternatively, the organic semiconductor material and the polymer binder may be totally or partially in a phase separation state. From the viewpoint of the charge mobility, a structure, in which the organic semiconductor and the binder are in a phase separation state along the film thickness direction in the film, is the most preferable because then the binder does not hinder the organic semiconductor from moving a charge.

45 **[0243]** Considering the mechanical strength of the film, a polymer binder having a high glass transition temperature is preferable. However, for the purpose of imparting flexibility to the film, a polymer binder having a low glass transition temperature is preferable. Considering the charge mobility, a polymer binder having a structure not containing a polar group and a conductive polymer are preferable.

[0244] The amount of the polymer binder used is not particularly limited. However, in the organic semiconductor film

for a non-light-emitting organic semiconductor device of the present invention, the amount of the polymer binder used is preferably within a range of 0% to 95% by mass, more preferably within a range of 10% to 90% by mass, even more preferably within a range of 20% to 80% by mass, and particularly preferably within a range of 30% to 70% by mass.

[0245] In the present invention, because the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 has the aforementioned structure, an organic film having excellent film quality can be obtained. Specifically, because the compound obtained in the present invention has excellent crystallinity, a sufficient film thickness can be obtained, and the obtained organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention has excellent quality.

[0246] In addition, in a case where the organic semiconductor film for a non-light-emitting organic semiconductor device of the present invention is manufactured by the method for manufacturing an organic semiconductor film of the present invention, the organic semiconductor film becomes an organic film having excellent film quality.

Examples

[0247] Hereinafter, the characteristics of the present invention will be more specifically explained by describing examples and comparative examples. The materials, the amount thereof used, the proportion thereof, the content of treatment, the treatment procedure, and the like described in the following examples can be appropriately modified within a range that does not depart from the gist of the present invention. Accordingly, the scope of the present invention is not limited to the following specific examples.

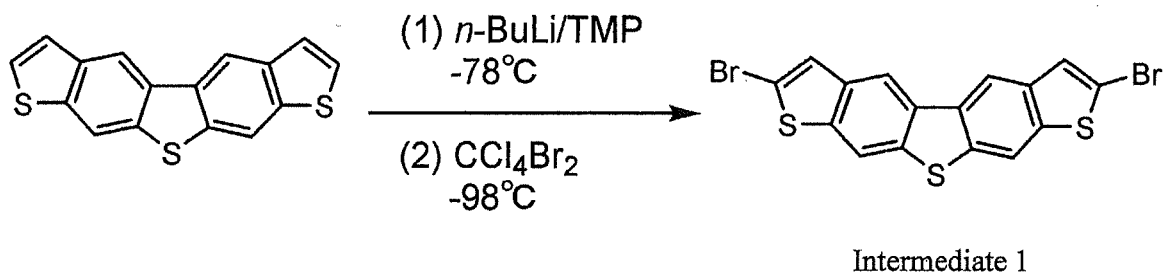
[Example 1 and Comparative Examples 1 to 5]

<Synthesis method>

[0248] A compound 1 of the present invention was synthesized according to the following scheme.

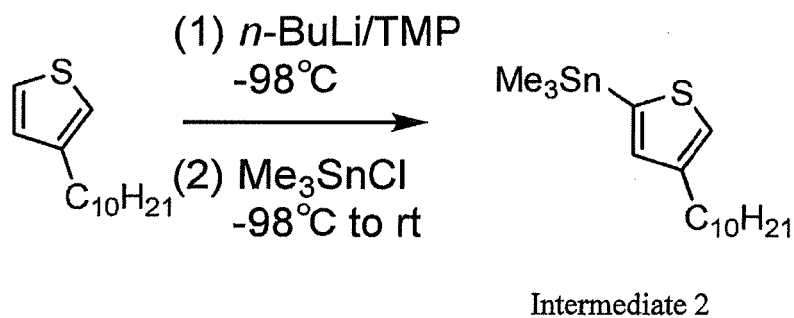
Synthesis of Intermediate 1

[0249]



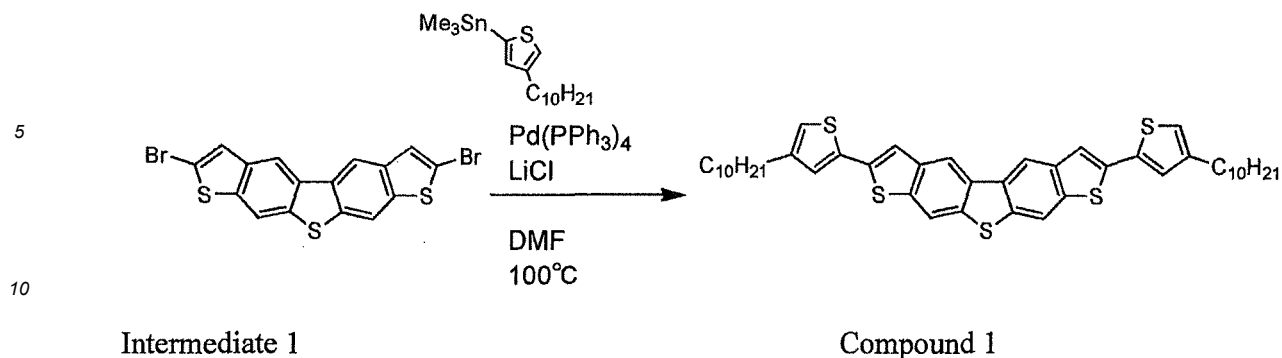
Synthesis of Intermediate 2

[0250]



Synthesis of compound 1

[0251]



(Synthesis of intermediate 1)

15 **[0252]** 23.1 ml of tetrahydrofuran was added to 3.93 ml of tetramethylpiperidine (TMP), followed by stirring at -78°C , and 13.8 ml of n-butyllithium (1.6 M hexane solution) was added thereto. Then, the mixture was heated to 0°C and stirred for 1 hour, thereby preparing a lithium reagent.

20 **[0253]** 100 ml of tetrahydrofuran was added to 2.969 g (10 mmol) of thieno[3,2-f:4,5-f']bis[1]benzothiophene, followed by stirring at -78°C , and the aforementioned lithium reagent was added dropwise thereto at -78°C by using a cannula. After 2 hours, the reaction solution was cooled to -98°C , and a solution obtained by dissolving 9.76 g (30 mmol) of dibromodichloroethane in 30 ml of tetrahydrofuran was added dropwise thereto by using a cannula. Then, the reaction solution was slowly heated to room temperature from -98°C and stirred for 15 hours. After the reaction solution was cooled to 0°C , water was added thereto, and the precipitate was separated by filtration. The solid separated by filtration

25 was recrystallized from 1,1,2,2-tetrachloroethane, thereby obtaining 3.95 g (8.70 mmol) of a target compound (intermediate 1). The obtained compound was identified by $^1\text{H-NMR}$.
 $^1\text{H-NMR}$ (Tetrachloroethane- d_2 , 400 MHz) δ : 7.46 (2H, s), 8.12 (2H, s), 8.45 (2H, s)

(Synthesis of intermediate 2)

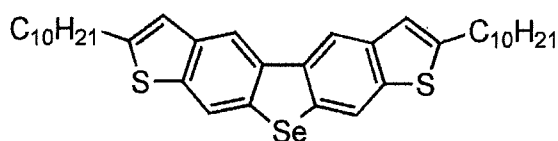
30 **[0254]** 30 ml of tetrahydrofuran was added to 4.49 g (20 mmol) of 3-decylthiophene, followed by stirring at -98°C , and 21 mmol of a lithium reagent prepared in the same manner as described above was added thereto, followed by stirring for 2 hours. Then, a solution obtained by dissolving 4.58 g (23.0 mmol) of trimethyltin chloride in 30 ml of tetrahydrofuran was added dropwise to the reaction solution, and the reaction solution was slowly heated to room temperature from -98°C , followed by stirring for 15 hours. Thereafter, water was added to the reaction solution, and extraction was performed using ethyl acetate, followed by purification through distillation, thereby obtaining 6.04 g (15.6 mmol) of a target compound (intermediate 2).

(Synthesis of compound 1)

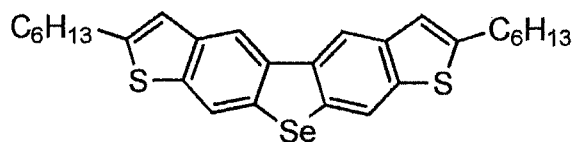
40 **[0255]** 7.5 ml of N,N-dimethylformamide was added to 341 mg (0.75 mmol) of the intermediate 1, 755 mg (1.95 mmol) of the intermediate 2, and 83 mg (1.95 mmol) of lithium chloride, followed by deaeration. Then, 43 mg (0.0375 mmol) of tetrakis(triphenylphosphine) palladium (0) was added thereto, followed by heating for 15 hours at 100°C and stirring. After the reaction ended, the reaction solution was cooled to room temperature, and the precipitated solid was separated by filtration and washed with N,N-dimethylformamide. The solid was dissolved in o-dichlorobenzene at 120°C and subjected to hot filtration through silica and celite, and the filtrate was concentrated, thereby obtaining a solid. The obtained solid was recrystallized from o-dichlorobenzene, thereby obtaining 476 mg (0.642 mmol) of a target compound (compound 1). The structure of the compound 1 was identified by $^1\text{H-NMR}$, and the results are as follows.

45 $^1\text{H-NMR}$ (tetrachloroethane- d_2 , 400 MHz) δ : 0.86 (6H, t), 1.25-1.32 (28H, m), 1.62-1.73 (4H, m), 2.60 (4H, t), 6.93 (2H, s), 7.16 (2H, s), 7.50 (2H, s), 8.18 (2H, s), 8.48 (2H, s).

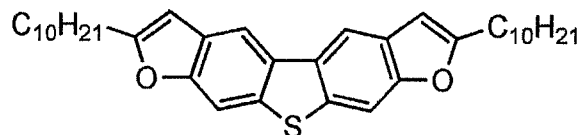
50 **[0256]** Compounds 2 to 12 having the following structures were synthesized according to the synthesis methods which will be described later.



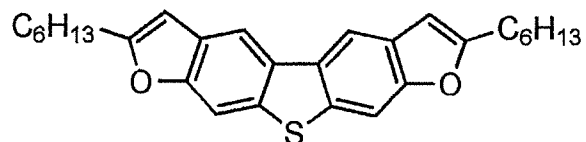
Compound 2



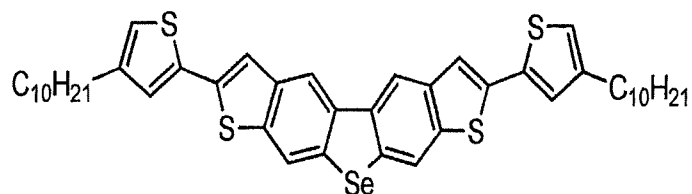
Compound 3



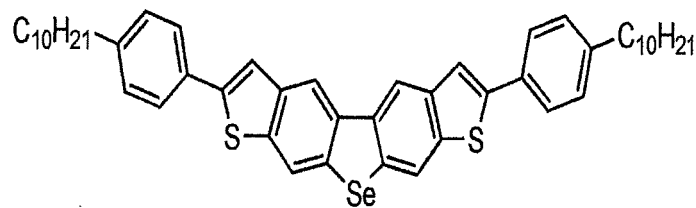
Compound 4



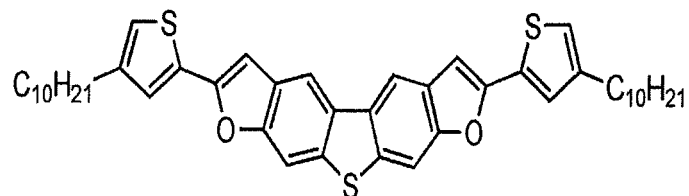
Compound 5



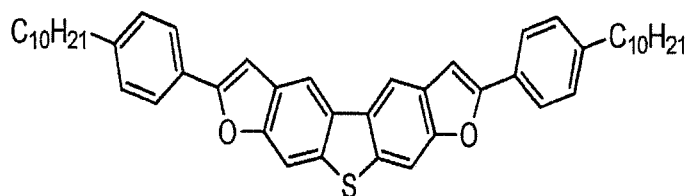
Compound 6



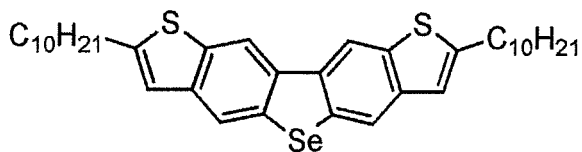
Compound 7



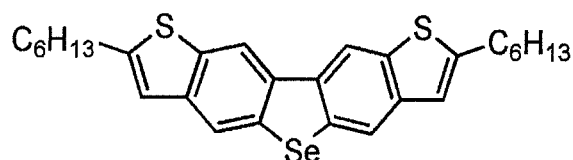
Compound 8



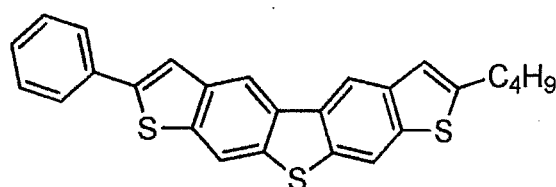
Compound 9



Compound 10



Compound 11

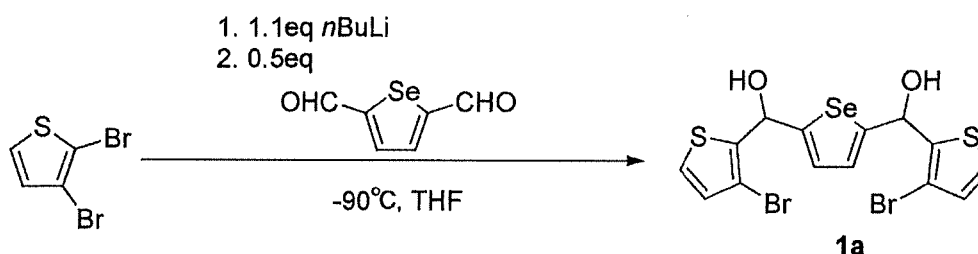


Compound 12

(Synthesis of compound 2)

-Synthesis of intermediate 1a-

[0257]

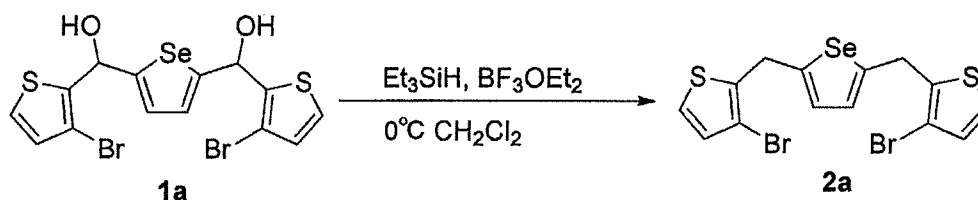


[0258] A 2,3-dibromothiophene *n*-butyllithium solution (15.9 g, 65.8 mmol) was dissolved in 120 ml of diethylether. Then, *n*-butyllithium (1.6 M solution) was added dropwise to the solution that was being stirred at -90°C. After 30 minutes, a solution obtained by dissolving 2,5-selenophene dicarboxaldehyde (6.00 g, 32.1 mmol) in 50 ml tetrahydrofuran was added dropwise thereto, followed by stirring for 20 minutes at -78°C, and then the reaction solution was heated to room temperature. The reaction solution was quenched with water, and an organic layer was extracted using diethylether and dried over magnesium sulfate. The organic layer was concentrated using an evaporator, thereby obtaining an intermediate 1a (12.9 g) as a target substance in the form of brown oil. The obtained crude target substance was used for the next reaction without being further purified.

¹H-NMR (CDCl₃, 400 MHz) δ: 7.28 (d, *J* = 5.2 Hz, 2H), 7.04 (d, *J* = 5.2 Hz, 2H), 6.93 (d, *J* = 5.2 Hz, 2H), 6.31 (s, 2H).

-Synthesis of Intermediate 2a-

[0259]

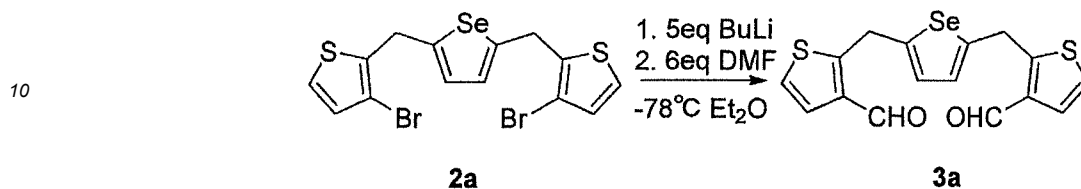


[0260] The intermediate 1a (12.9 g) and triethylsilane (15.4 ml, 96.2 mmol) were dissolved in 70 ml of dichloroethane and cooled to 0°C. To the obtained solution, boron trifluoride/etherate (11.9 ml, 96.2 mmol) was added dropwise, followed by stirring for 30 minutes. Then, the reaction solution was quenched with water, and an organic layer was extracted using ethyl acetate and dried over magnesium sulfate. The crude substance obtained after concentration was purified by column chromatography (hexane:ethyl acetate = 95:5), thereby obtaining an intermediate 2a (9.20 g, 19.1 mmol, 60% yield for 2 steps) as a target substance in the form of yellow oil.

$^1\text{H-NMR}$ (CDCl_3 , 400 MHz) δ : 7.16 (d, $J = 5.2$ Hz, 2H), 6.92 (d, $J = 5.2$ Hz, 2H), 6.86 (s, 2H), 4.28 (s, 4H).

-Synthesis of intermediate 3a-

5 [0261]



15 [0262] n-Butyllithium (1.6 M solution) (58.5 ml, 93.5 mmol) was cooled to -78°C . At this point in time, a solution obtained by dissolving the intermediate 2a (9.00 g, 18.7 mmol) in 240 ml of diethylether was added dropwise thereto, followed by stirring for 30 minutes. Then, N,N-dimethylformamide (8.7 ml, 112 mmol) was added dropwise thereto. After being stirred for 20 minutes at -78°C , the reaction solution was heated to room temperature, then quenched with water, and subjected to extraction using diethylether, and the extract was dried over magnesium sulfate. Through concentration,

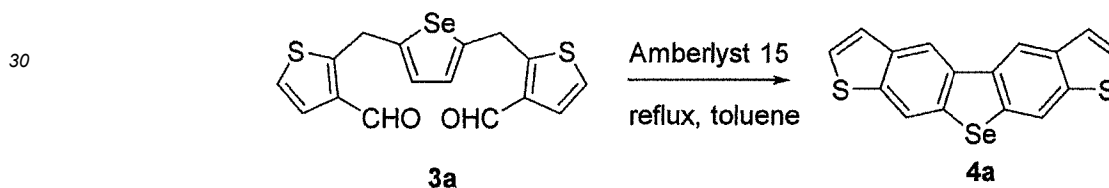
20 an intermediate 3a (6.50 g) as a target substance in the form of red oil was obtained. The obtained crude target substance was used for the next reaction without being further purified.

$^1\text{H-NMR}$ (CDCl_3 , 400 MHz) δ : 10.0 (s, 2H), 7.40 (d, $J = 4.8$ Hz, 2H), 7.15 (d, $J = 4.8$ Hz, 2H), 6.88 (s, 2H), 4.68 (s, 4H).

-Synthesis of intermediate 4a-

25

[0263]



35

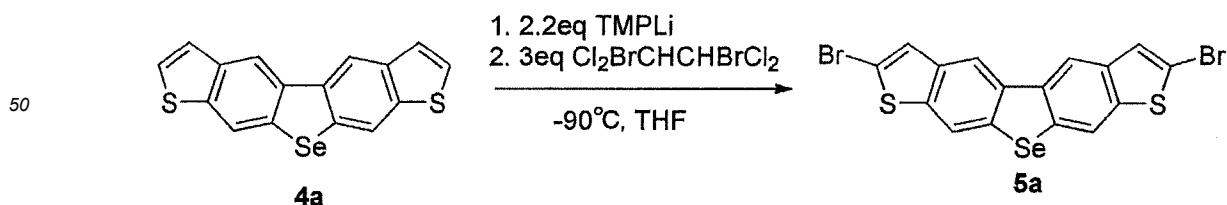
[0264] The intermediate 3a (6.50 g) was dissolved in 350 ml of toluene, and AMBERLYST (registered trademark) 15 hydrogen form dry (15.0 g) was added thereto, followed by reflux for 2 hours. The reaction solution was separated by filtration, and the filtrate was concentrated and then recrystallized from toluene/methanol, followed by purification by column chromatography (toluene), thereby obtaining an intermediate 4a (2.35 g, 6.84 mmol, 36% yield for 2 steps) as a target substance in the form of white solid.

40

$^1\text{H-NMR}$ (CDCl_3 , 400 MHz) δ : 8.63 (s, 2H), 8.31 (d, $J = 0.8$ Hz, 2H), 7.46 (m, 4H).

-Synthesis of intermediate 5a-

45 [0265]



55 [0266] The intermediate 4a (2.00 g, 5.83 mmol) and 58 ml of tetrahydrofuran were stirred at -90°C . At this point in time, 20 ml of a tetrahydrofuran solution of lithium tetramethyl piperidine (12.8 mmol) was added dropwise thereto, followed by stirring for 30 minutes. A solution obtained by dissolving dibromotetrachloroethane (5.69 g, 17.5 mmol) in 20 ml of tetrahydrofuran was added dropwise thereto, followed by stirring for 20 minutes at -78°C , and then the reaction

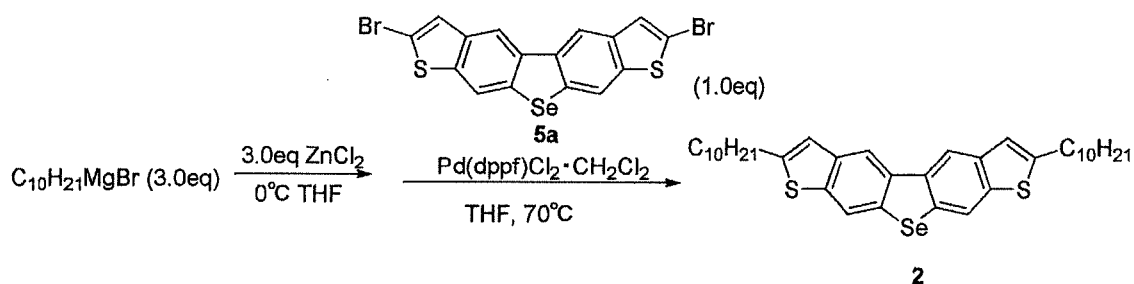
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solution was heated to room temperature. The reaction solution was quenched with water and subjected to extraction using dichloroethane, and then the extract was dried over magnesium sulfate. After concentration, the extract was recrystallized from tetrahydrofuran/methanol, thereby obtaining an intermediate 5a (2.21 g, 4.41 mmol, 76% yield) as a target substance in the form of white solid.

¹H-NMR (CDCl₃, 400 MHz) δ: 8.46 (s, 2H), 8.16 (s, 2H), 7.45 (s, 2H).

-Synthesis of compound 2-

[0267]

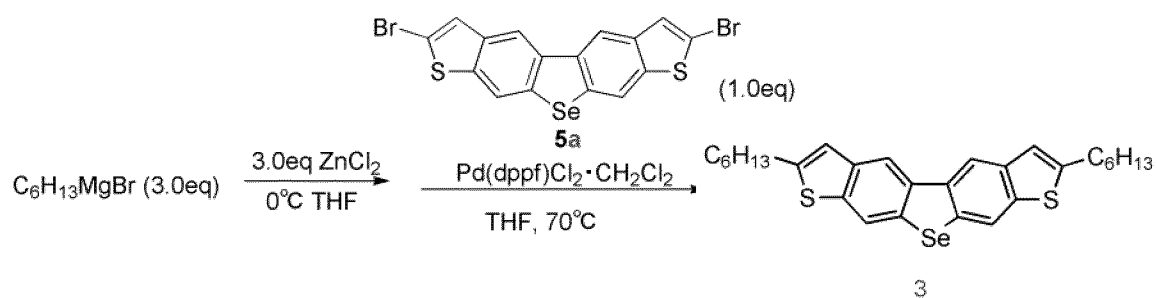


[0268] A zinc (II) chloride solution (1.0 mol/L tetrahydrofuran solution, 1.50 ml) was added to a n-decyl magnesium bromide solution (1.0 mol/L in diethylether, 1.50 ml, 1.50 mmol) used as a reactant at 0°C, followed by stirring for 15 minutes. Then, intermediate 5a (250 mg, 0.45 mmol) and a 1,1-bis(diphenylphosphino)ferrocene dichloropalladium (II)/dichloroethane adduct (20.2 mg, 0.025 mmol) were added thereto. The reaction solution was stirred for 1 hour at 70°C, followed by concentration and purification by column chromatography (hexane/chloroform = 95/5), thereby obtaining a compound 2 (102 mg, 0.16 mmol, 33% yield) as a target substance in the form of white solid.

¹HNMR (CDCl₃, 400 MHz) δ: 8.43 (s, 2H), 8.17 (s, 2H), 7.10 (s, 2H), 2.93 (t, J = 7.6 Hz, 4H), 1.78 (quint, J = 6.4 Hz, 4H), 1.46-1.27 (m, 28H), 0.88 (t, J = 6.8 Hz, 6H).

(Synthesis of compound 3)

[0269]



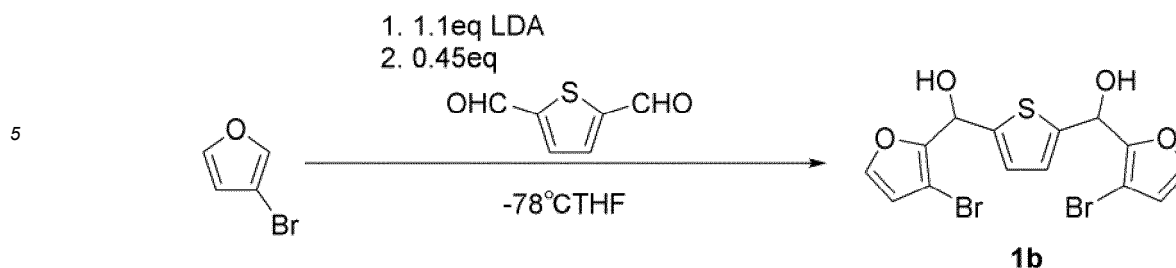
[0270] A compound 3 as a white solid was obtained in the same manner as used for synthesizing the compound 2, except that, as a reactant, a n-hexylmagnesium bromide solution was used instead of n-decylmagnesium bromide.

¹H-NMR (CDCl₃, 400 MHz) δ: 8.43 (s, 2H), 8.17 (s, 2H), 7.11 (s, 2H), 2.93 (t, J = 7.2 Hz, 4H), 1.79 (quint, J = 7.6 Hz, 4H), 1.43-1.40 (m, 4H), 1.40-1.26 (m, 4H), 0.91 (t, J = 6.8 Hz, 6H).

(Synthesis of compound 4)

-Synthesis of intermediate 1b-

[0271]

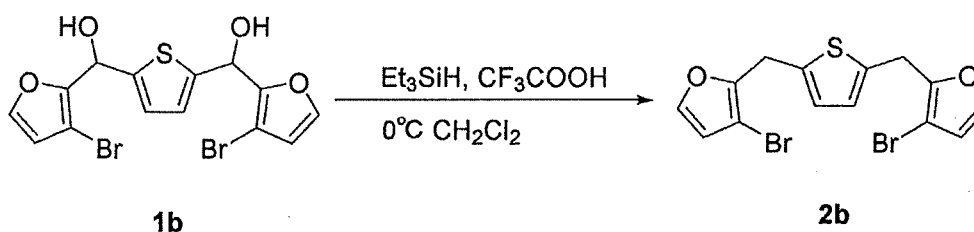


[0272] 2-Bromofuran (14.0 g, 95.3 mmol) was dissolved in 30 ml of tetrahydrofuran and cooled to -78°C. Thereafter, a lithium diisopropylamide (1.5 mol/L tetrahydrofuran/ethylbenzene/heptane, 69.9 ml, 104.8 mmol) solution was added dropwise thereto, followed by stirring for 30 minutes, and then 70 ml of a tetrahydrofuran solution containing 2,5-thiophene dicarboxaldehyde (6.01 g, 42.9 mmol) was added dropwise thereto. After being stirred for 20 minutes, the reaction solution was heated to room temperature and quenched with water. Then, the reaction solution was subjected to extraction by using diethylether, and the extract was dried over magnesium sulfate and then concentrated, thereby obtaining an intermediate 1b (19.6 g) as a target substance in the form of brown oil. The obtained crude target substance was used for the next reaction without being further purified.

¹H-NMR (CDCl₃, 400 MHz) δ: 7.39 (d, J = 1.6 Hz, 2H), 6.82 (d, J = 1.6 Hz, 2H), 6.44 (d, J = 1.6 Hz, 2H), 6.11 (s, 2H).

-Synthesis of intermediate 2b-

[0273]

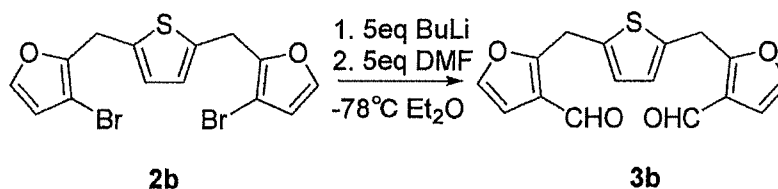


[0274] 500 ml of a dichloroethane solution containing the intermediate 1b (19.6 g) and triethylsilane (32.0 ml, 200 mmol) was cooled to 0°C. At this point in time, trifluoroacetic acid (15.3 ml, 200 mmol) was added dropwise thereto, followed by stirring for 30 minutes. The reaction solution was quenched with water and subjected to extraction by using ethyl acetate, and the extract was dried over magnesium sulfate. After concentration, the extract was purified by column chromatography (hexane/chloroform = 9/1), thereby obtaining an intermediate 2b (3.67 g, 9.13 mmol, 23% yield for 2 steps) as a target substance in the form of yellow oil.

¹H-NMR (CDCl₃, 400 MHz) δ: 7.28 (d, J = 1.6 Hz, 2H), 6.66 (s, 2H), 6.36 (d, J = 1.6 Hz, 2H), 4.08 (s, 4H).

-Synthesis of intermediate 3b-

[0275]



[0276] A n-butyllithium solution (1.6 mol/L heptane solution, 20.9 ml, 32.3 mmol) was diluted with 81.9 ml of diethylether and cooled to -78°C. At this point in time, a solution obtained by dissolving the intermediate 2b (2.60 g, 6.47 mmol) in 81.9 ml of diethylether was added dropwise thereto, followed by stirring for 30 minutes. Thereafter, N,N-dimethylformamide (2.50 ml, 32.3 mmol) was added dropwise thereto, followed by stirring for 20 minutes, and then heated to room temperature. The reaction solution was quenched with water and subjected to extraction by using diethylether, and then

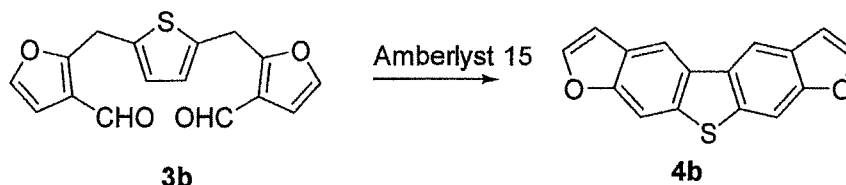
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the extract was dried over magnesium sulfate and concentrated, thereby obtaining the intermediate 3b (3.05 g) as a target substance in the form of red oil. The obtained crude target substance was used for the next reaction without being further purified.

$^1\text{H-NMR}$ (CDCl_3 , 400 MHz) δ : 9.94 (s, 2H), 7.34 (d, $J = 2.4$ Hz, 2H), 6.72 (s, 2H), 6.71 (d, $J = 2.4$ Hz, 2H), 4.40 (s, 4H).

-Synthesis of intermediate 4b-

[0277]

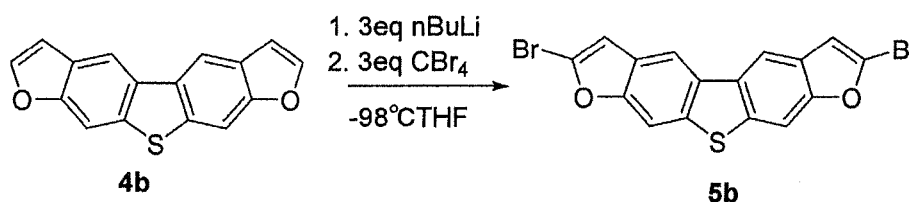


[0278] The intermediate 3b (3.05 g) was dissolved in 115 ml of toluene, and AMBERLYST (registered trademark) 15 hydrogen form dry (4.97 g) was added thereto, followed by reflux for 2 hours. The reaction solution was separated by filtration, and the filtrate was concentrated and then recrystallized from dichloroethane/acetonitrile, thereby obtaining an intermediate 4b (634 mg, 2.40 mmol, 37% yield for 2 steps) as a target substance in the form of white solid.

$^1\text{H-NMR}$ (CDCl_3 , 400 MHz) δ : 8.33 (s, 2H), 7.90 (d, $J = 0.8$ Hz, 2H), 6.67 (d, $J = 0.8$ Hz, 2H), 6.90 (m, 2H).

-Synthesis of intermediate 5b-

[0279]

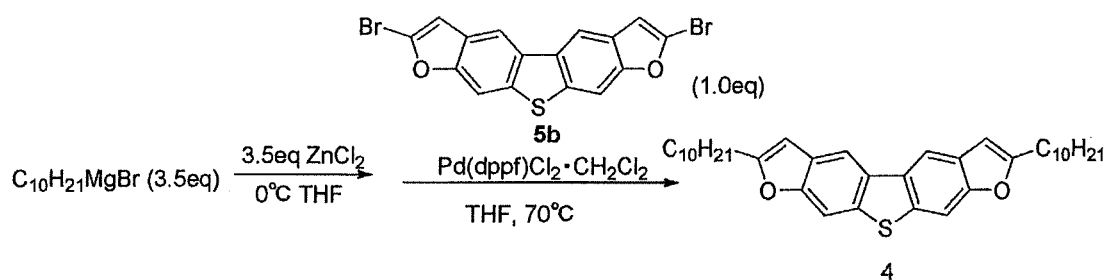


[0280] The intermediate 4b (450 mg, 1.7 mmol) and 25 ml of tetrahydrofuran were stirred at -90°C . At this point in time, n-butyllithium (1.6 mol/L heptane solution, 3.19 ml) was added dropwise thereto, followed by stirring for 30 minutes. 10 ml of a tetrahydrofuran solution containing carbon tetrabromide (2.26 g, 6.80 mmol) was added dropwise thereto, followed by stirring for 20 minutes at -78°C , and then heated to room temperature. The reaction solution was quenched with water and subjected to extraction by using dichloroethane, and the extract was dried over magnesium sulfate. After concentration, the extract was recrystallized from dichloroethane/ethyl acetate, thereby obtaining an intermediate 5b (558 mg, 1.32 mmol, 78% yield) as a target substance in the form of white solid.

$^1\text{H-NMR}$ (CDCl_3 , 400 MHz) δ : 8.23 (d, $J = 1.6$ Hz, 2H), 7.87 (d, $J = 1.6$ Hz, 2H), 6.87 (d, $J = 0.8$ Hz, 2H).

-Synthesis of compound 4-

[0281]



[0282] A compound 4 was obtained in the same manner as used for obtaining compound 2, except that the intermediate

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5b was used as a raw material instead of the intermediate 5a. ¹H-NMR (CDCl₃, 400 MHz) δ: 8.19 (s, 2H), 7.79 (s, 2H), 6.50 (s, 2H), 2.80 (t, J = 7.2 Hz, 4H), 1.78 (quint, J = 7.2 Hz, 4H), 1.45-1.20 (m, 28H), 0.87 (t, J = 8.0 Hz, 6H).

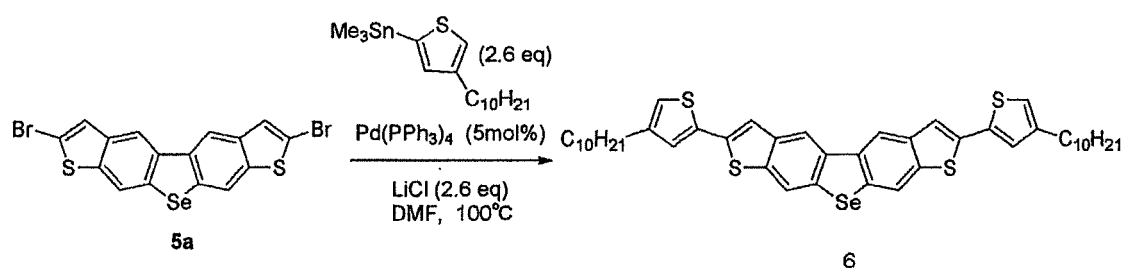
(Synthesis of compound 5)

[0283] A compound 5 was obtained in the same manner as used for obtaining the compound 4, except that n-hexyl magnesium bromide was used as a reactant instead of n-decyl magnesium bromide.

¹H-NMR (CDCl₃, 400 MHz) δ: 8.19 (s, 2H), 7.80 (s, 2H), 6.50 (s, 2H), 2.80 (t, J = 7.4 Hz, 4H), 1.78 (quint, J = 7.6 Hz, 4H), 1.45-1.25 (m, 12H), 0.90 (t, J = 7.2 Hz, 6H).

(Synthesis of compound 6)

[0284]

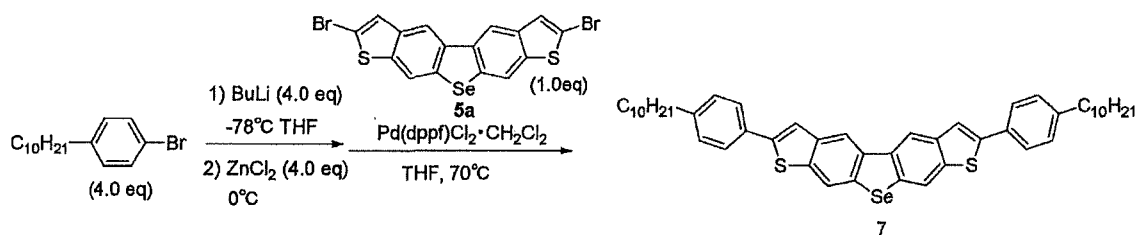


[0285] 4 ml of N,N-dimethylformamide was added to the intermediate 5a (200 mg, 0.40 mmol), and a lithium chloride solution (0.5 mol/L tetrahydrofuran solution, 2.0 ml, 2.6 mmol) and tetrakis(triphenylphosphine) palladium (0) (23 mg, 0.020 mmol) were added thereto, followed by stirring for 3 hours at 100°C. Then, the reaction solution was concentrated and purified by column chromatography (chloroform) and recrystallization (toluene), thereby obtaining a compound 6 (205 mg, 0.26 mmol, 65% yield) as a target substance in the form of white solid.

¹H-NMR (tetrachloroethane-d₂, 400 MHz) δ: 8.46 (s, 2H), 8.18 (s, 2H), 7.47 (s, 4H), 7.16 (s, 2H), 6.92 (s, 2H), 2.63 (t, J = 7.2 Hz, 4H), 1.69-1.67 (m, 4H), 1.45-1.30 (m, 28H), 0.89 (t, J = 6.0 Hz, 6H).

(Synthesis of compound 7)

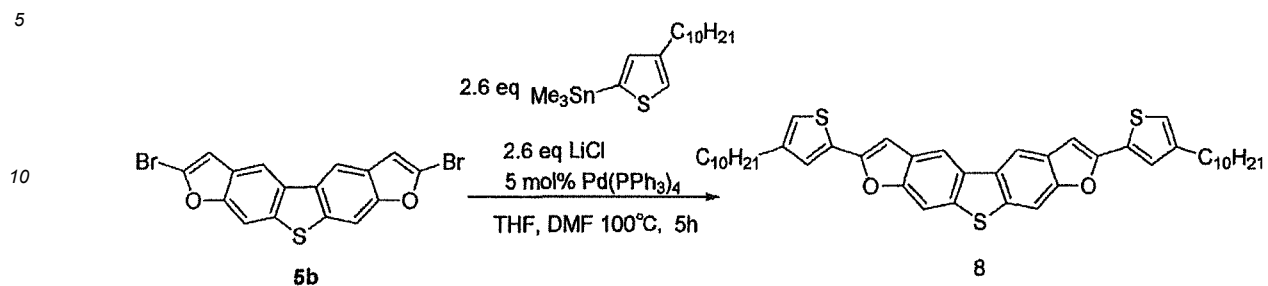
[0286]



[0287] 4-n-Decylphenyl bromide (475 mg, 1.6 mmol) and 1.0 ml of tetrahydrofuran were cooled to -78°C, and a n-butyllithium solution (2.6 mol/L hexane solution, 0.61 ml, 1.6 mmol) was added dropwise thereto, followed by stirring for 15 minutes. Then, a zinc (II) chloride solution (1.0 mol/L tetrahydrofuran solution, 1.60 ml) was added thereto, followed by stirring for 15 minutes at 0°C. To the reaction solution, the intermediate 5a (200 mg, 0.40 mmol), a 1,1-bis(diphenylphosphino)ferrocene dichloropalladium (II)/dichloroethane adduct (16.3 mg, 0.020 mmol) was added, followed by stirring for 1 hour at 70°C. After being concentrated, the reaction solution was subjected to column chromatography (chloroform) and then recrystallized (tetrahydrofuran), thereby obtaining a compound 7 (150 mg, 0.20 mmol, 50% yield) as a target substance in the form of white solid.

¹H-NMR (tetrachloroethane-d₂, 400 MHz) δ: 8.52 (s, 2H), 8.23 (s, 2H), 7.64 (d, J = 8.4 Hz, 4H), 7.61 (s, 2H), 7.25 (d, J = 8.0 Hz, 4H), 2.66 (t, J = 7.4 Hz, 4H), 1.71-1.65 (m, 4H), 1.45-1.29 (m, 28H), 0.89 (t, J = 6.0 Hz, 6H).

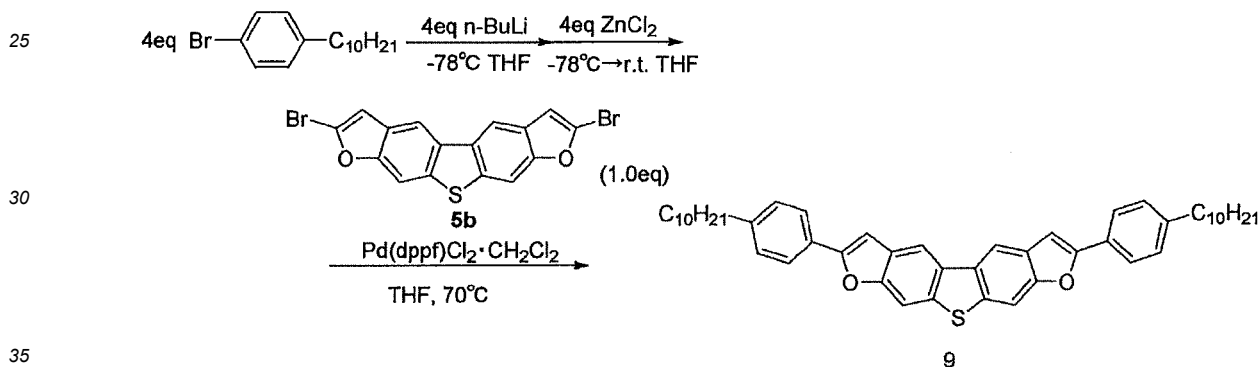
(Synthesis of compound 8)

[0288]

15 **[0289]** A compound 8 was obtained in the same manner as used for obtaining the compound 6, except that the intermediate 5b was used instead of the intermediate 5a.

¹H-NMR (tetrachloroethane-d₂, 400 MHz) δ : 8.24 (s, 2H), 7.87 (s, 2H), 7.75 (d, J = 8.0 Hz, 4H), 7.22 (d, J = 8.0 Hz, 4H), 7.04 (s, 2H), 2.59 (t, J = 8.0 Hz, 4H), 1.59 (quint, J = 6.5 Hz, 4H), 1.35-1.14 (m, 28H), 0.81 (t, J = 7.2 Hz, 6H).

20 (Synthesis of compound 9)

[0290]

[0291] A compound 9 was obtained in the same manner as used for obtaining the compound 7, except that the intermediate 5b was used instead of the intermediate 5a.

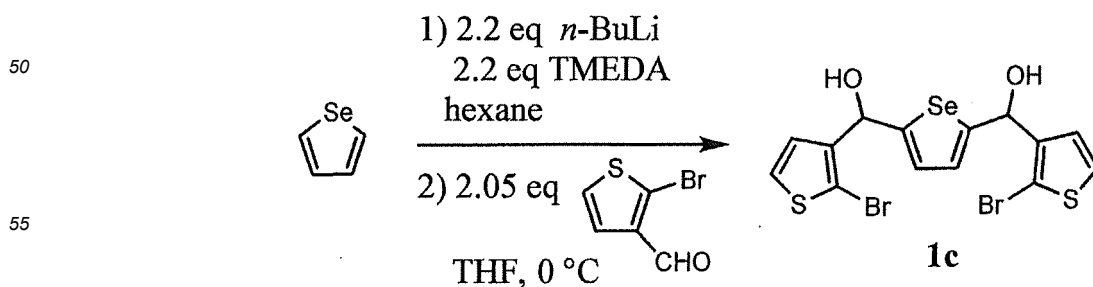
¹H-NMR (tetrachloroethane-d₂, 400 MHz) δ : 8.26 (s, 2H), 7.87 (s, 2H), 7.38 (s, 2H), 6.96 (s, 4H), 2.65 (t, J = 8.0 Hz, 4H), 1.68 (quint, J = 7.4 Hz, 4H), 1.41-1.20 (m, 28H), 0.88 (t, J = 7.2 Hz, 6H).

40

(Synthesis of compound 10)

-Synthesis of intermediate 1c-

45

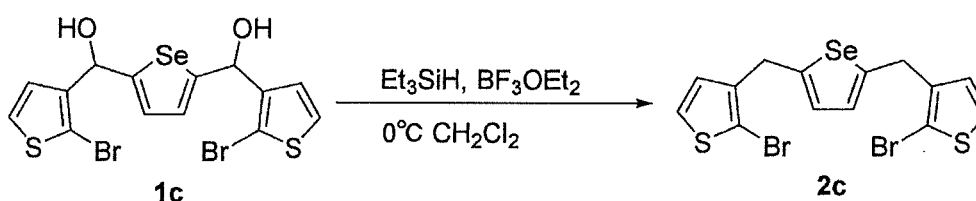
[0292]

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[0293] 115 ml of a hexane solution containing tetramethyl piperidine (7.7 ml, 51.6 mmol) was cooled to 0°C. At this point in time, n-butyllithium (1.6 mol/L hexane solution, 32 ml, 51.6 mmol) was added dropwise thereto, followed by stirring for 30 minutes. Thereafter, selenophenone (3.30 g, 25.2 mmol) was added dropwise thereto, followed by stirring for 1 hour at 0°C. Then, 115 ml of a tetrahydrofuran solution containing 2-bromo-3-thiophene carboxaldehyde (10.1 g, 52.9 mmol) was added dropwise thereto, followed by stirring for 20 minutes, and the reaction solution was heated to room temperature. The reaction solution was quenched with water and then subjected to extraction by using ethyl acetate, and an organic layer was dried over magnesium sulfate and concentrated, thereby obtaining an intermediate 1c (12.0 g) as a target substance in the form of brown oil. The obtained crude target substance was used for the next reaction without being further purified.

-Synthesis of intermediate 2c-

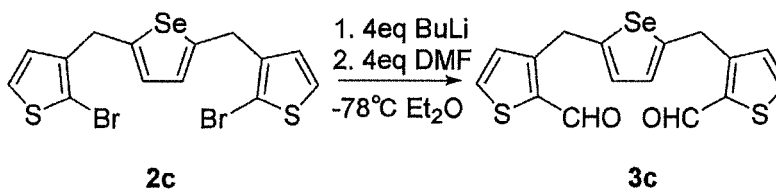
[0294]



[0295] An intermediate 2c was obtained in the same manner as used for obtaining the intermediate 2a, except that the intermediate 1c was used instead of the intermediate 1a. ¹H-NMR (CDCl₃, 400 MHz) δ: 7.22 (d, J = 4.8 Hz, 2H), 7.05 (d, J = 5.2 Hz, 2H), 6.82 (d, J = 5.2 Hz, 2H), 6.72-6.70 (m, 2H), 4.08 (s, 2H).

-Synthesis of intermediate 3c-

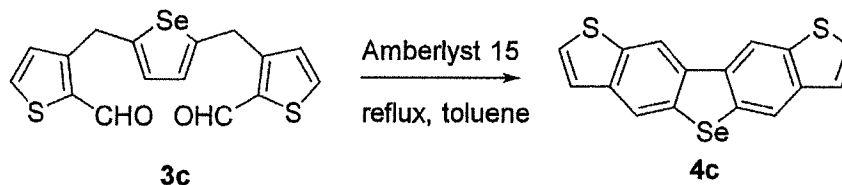
[0296]



[0297] An intermediate 3c was obtained in the same manner as used for obtaining the intermediate 3a, except that the intermediate 2c was used instead of the intermediate 2a. The obtained crude target substance was used for the next reaction without being further purified.

-Synthesis of intermediate 4c-

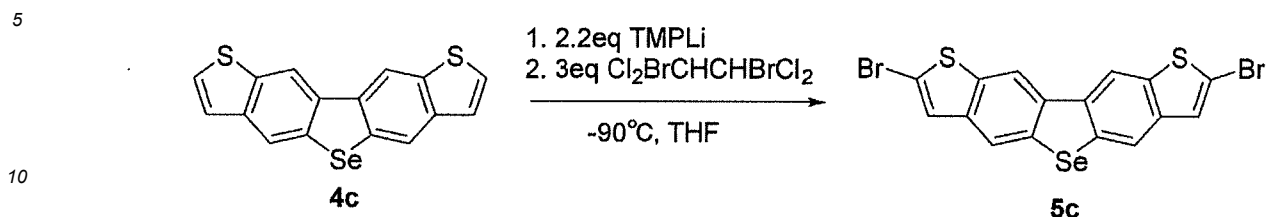
[0298]



[0299] An intermediate 4c was obtained in the same manner as used for obtaining the intermediate 4a, except that the intermediate 3c was used instead of the intermediate 3a. ¹H-NMR (CDCl₃, 400 MHz) δ: 8.67 (s, 2H), 8.26 (s, 2H), 7.53 (d, J = 5.6 Hz, 2H), 7.37 (d, J = 5.6 Hz, 2H).

-Synthesis of intermediate 5c-

[0300]

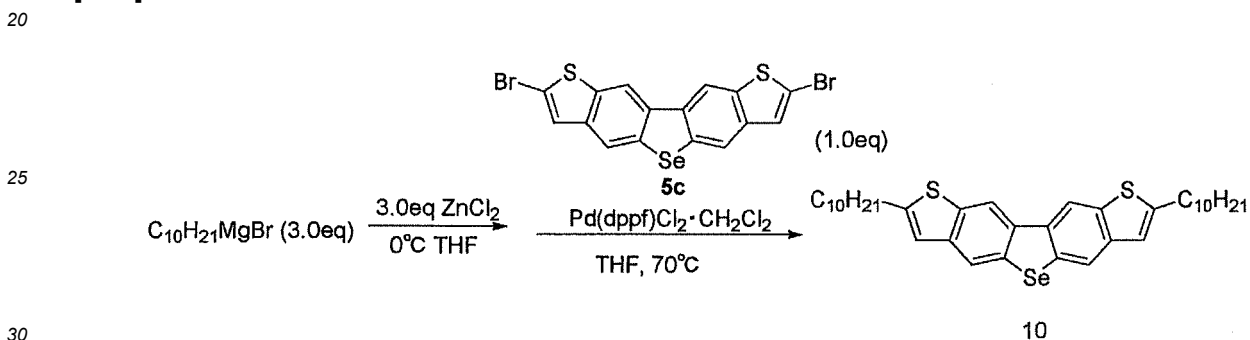


[0301] An intermediate 5c was obtained in the same manner as used for obtaining the intermediate 5a, except that the intermediate 4c was used instead of the intermediate 4a.

15 ¹H-NMR (CDCl₃, 400 MHz) δ: 8.47 (s, 2H), 8.13 (s, 2H), 7.36 (s, 2H).

-Synthesis of compound 10-

[0302]

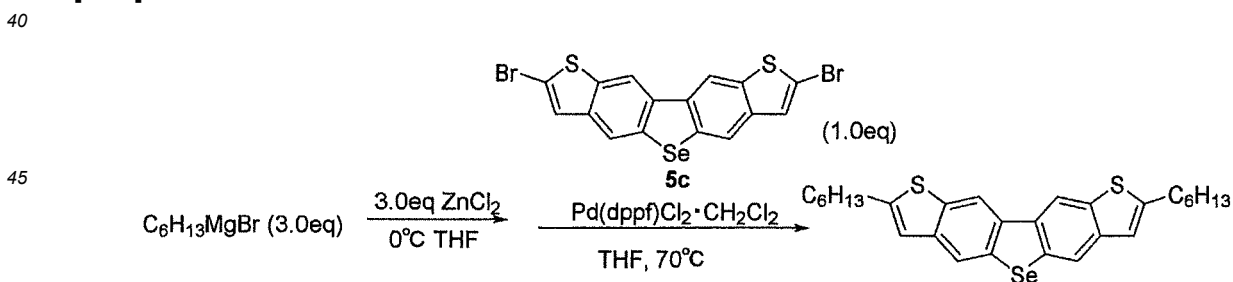


[0303] A compound 10 was obtained in the same manner as used for obtaining the compound 2, except that the intermediate 5c was used instead of the intermediate 5a.

35 ¹H-NMR (CDCl₃, 400 MHz) δ: 8.50 (s, 2H), 8.07 (s, 2H), 7.01 (s, 2H), 2.94 (t, J = 7.6 Hz, 4H), 1.82-1.74 (m, 4H), 1.42-1.27 (m, 28H), 0.88 (t, J = 6.8 Hz, 6H).

(Synthesis of compound 11)

[0304]



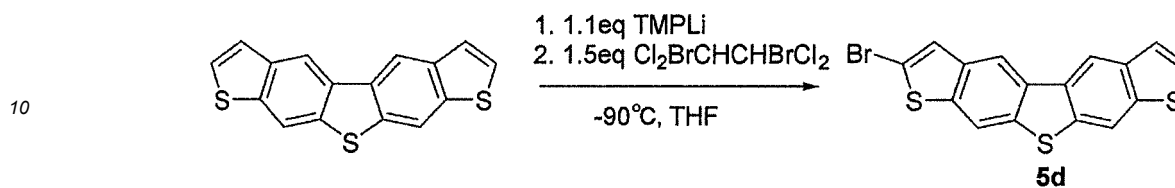
[0305] A compound 11 was obtained in the same manner as used for obtaining the compound 3, except that the intermediate 5c was used instead of the intermediate 5a.

55 ¹H-NMR (CDCl₃, 400 MHz) δ: 8.50 (s, 2H), 8.07 (s, 2H), 7.01 (s, 2H), 2.94 (t, J = 7.6 Hz, 4H), 1.82-1.74 (m, 4H), 1.43-1.32 (m, 12H), 0.90 (t, J = 6.4 Hz, 6H).

(Synthesis of compound 12)

-Synthesis of intermediate 5d-

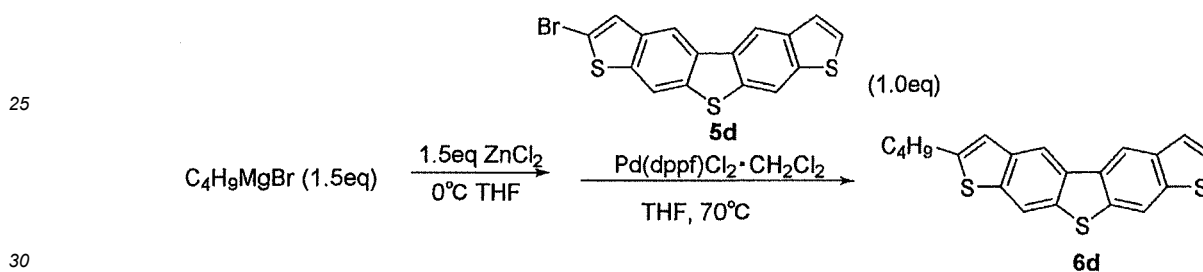
5 [0306]



15 [0307] An intermediate 5d was obtained in the same manner as used for obtaining the intermediate 1, except that the equivalents of an organic lithium reagent and the equivalents of dibromotetrachloroethane were reduced to 1.1 equivalents and 1.5 equivalents respectively.

-Synthesis of intermediate 6d-

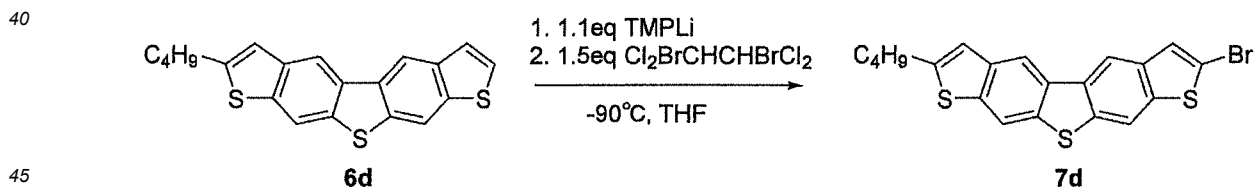
20 [0308]



35 [0309] An intermediate 6d was obtained in the same manner as used for obtaining the compound 2, except that the intermediate 5d was used instead of the intermediate 5a such that the equivalents of an organic zinc reagent and a palladium catalyst halved.

-Synthesis of intermediate 7d-

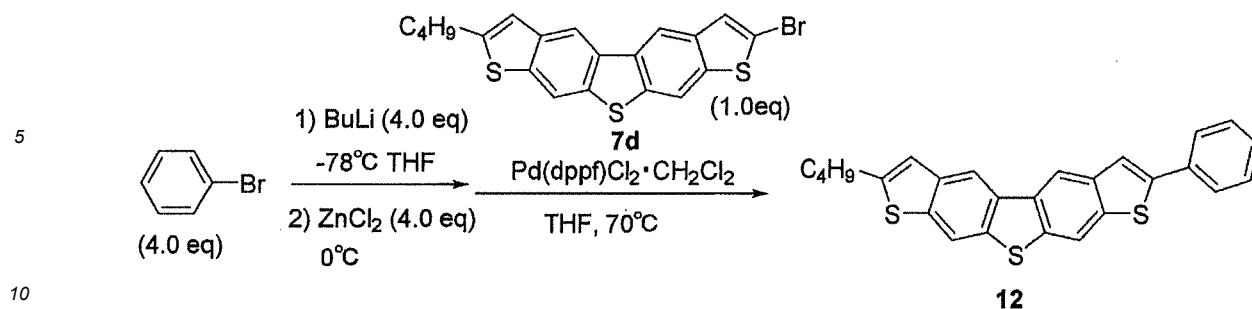
40 [0310]



[0311] An intermediate 7d was obtained in the same manner as used for obtaining the intermediate 5d, except that the intermediate 6d was used instead of the material of the intermediate 5d.

-Synthesis of compound 12-

55 [0312]



[0313] A compound 12 was obtained in the same manner as used for obtaining the compound 7, except that the intermediate 7d was used as a raw material instead of the intermediate 5a, and bromobenzene was used as a reactant instead of 4-n-decylphenyl bromide. Through mass spectrometry, it was confirmed that the obtained the compound 12 was a target compound.

APCI-MS m/z; 429.0760 (M + 1)

[0314] A comparative compound 1 having the following structure was synthesized according to the synthesis method described in J. Org. Chem. 2005, 70, 4502.

20 Comparative compound 1

[0315]

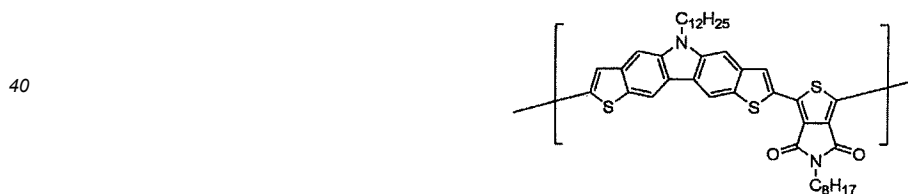


30 [0316] The following comparative compounds 2 to 4 were synthesized with reference to JP2013-235903A, CN102206225A, and WO2011/126225A respectively. The comparative compounds 2 and 3 were measured by gel permeation chromatography (GPC), and as a result, it was confirmed that they have a weight-average molecular weight (Mw) of 40,000. The comparative compound 4 is a compound 49 described in WO2011/126225A.

[0317] The comparative compound 5 was synthesized with reference to Tetrahedron 66 (2010) 8778-8784.

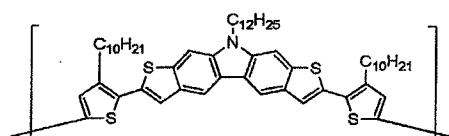
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Comparative compound 2

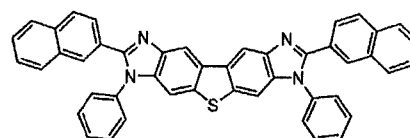


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Comparative compound 3

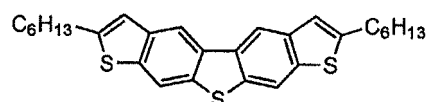


Comparative compound 4



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Comparative compound 5



<Preparation/evaluation of element>

[0318] Through high-performance liquid chromatography, it was confirmed that the materials used for preparing elements had purity (area ratio for absorption intensity at 254 nm) of equal to or higher than 99.0%.

<Formation of semiconductor active layer (organic semiconductor layer) by using compound alone>

[0319] Each of the aforementioned compounds 1 to 12 and comparative compounds 1 to 5 was prepared into a 0.1% by mass solution by using anisole as a solvent and then heated to 50°C. The solution was used as a coating solution for an organic semiconductor device.

[0320] In Examples 1 to 12 and Comparative Examples 1 to 5, an organic semiconductor film was formed by the method shown in Figs. 4A to 4C. The details are as follows.

[0321] A 25 mm × 25 mm substrate prepared by forming a thermally oxidized SiO₂ film having a thickness of 200 nm on the surface of an n-type silicon substrate (thickness: 0.4 mm) was used as a substrate A. The surface of the thermally oxidized film of the substrate A was cleaned with ultraviolet (UV)-ozone and then treated with β-phenethyltrimethoxysilane.

[0322] On the surface of the substrate A treated with β-phenethyltrimethoxysilane, a member B was placed on the central portion of the substrate A as shown in Fig. 4A such that the substrate A and the member B contacted each other. As the member B, a substance made of glass and having a size of 10 mm (length) × 2 mm (width) × 5 mm (height) was used. The transverse direction (X-axis direction) in Fig. 4A is the width direction of the member B; the vertical direction (Z-axis direction) in Fig. 4A is the height direction of the member B; and the vertical direction (Y-axis direction) in Fig. 4B2 is the longitudinal direction of the member B.

[0323] The substrate was heated to 50°C, and one drop (about 0.05 ml) of the coating solution prepared by the method described above was placed onto the substrate by using a pipette from the lateral side of the member B such that the drop contacted both of the substrate A and the member B as shown in Fig. 4A. As a result, as shown in Figs. 4B1 and 4B2, the coating solution was dropped onto a portion within the surface of the substrate A. In the interface between the coating solution and the substrate B, a concave meniscus was formed.

[0324] As shown in Fig. 4C, in a state where the substrate A and the member B were caused to remain in contact with each other, and the positional relationship between the substrate A and the member B were maintained, the coating solution was air-dried. Then, the coating solution was dried under reduced pressure for 8 hours at 60°C at a pressure of 10⁻³ MPa such that crystals of any one of the compounds 1 to 12 and the comparative compounds 1 to 5 were precipitated, thereby forming an organic semiconductor film. Whether or not crystals were precipitated was checked by observation using a polarizing microscope.

[0325] The obtained organic semiconductor film was used as a semiconductor active layer and covered with a mask. Then, F4-TCNQ with a thickness of 1 nm as a charge injection acceptor and a gold electrode with a thickness of 40 nm were vapor-deposited thereon, thereby obtaining an organic transistor element for measuring FET characteristics. The obtained organic transistor element was used as organic transistor elements (hereinafter, referred to as elements 1 to 12 and comparative elements 1 to 5 as well) of Examples 1 to 12 and Comparative Examples 1 to 5.

<Evaluation>

[0326] By using a semiconductor parameter analyzer (4156C manufactured by Agilent Technologies) connected to a semi-automatic prober (AX-2000 manufactured by Vector Semiconductor Co., Ltd.), the FET characteristics of the organic transistor elements of Examples 1 to 12 and Comparative Examples 1 to 5 were evaluated under a normal pressure/atmosphere.

[0327] The obtained results are shown in the following Table 36.

(a) Carrier mobility

[0328] Between the source electrode and the drain electrode of each organic film transistor element (FET element), a voltage of -80 V was applied, and the gate voltage was varied within a range of 20 V to -100 V. In this way, a carrier mobility μ was calculated using the following equation showing a drain current I_d.

$$I_d = (w/2L)\mu C_i(V_g - V_{th})^2$$

[0329] (In the equation, L represents a gate length, W represents a gate width, C_i represents a capacity of the insulating layer per unit area, V_g represents a gate voltage, and V_{th} represents a threshold voltage.)

[Table 36]

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Note
Element 1	Compound 1	2.3	Present invention
Element 2	Compound 2	2.0	Present invention
Element 3	Compound 3	2.3	Present invention
Element 4	Compound 4	1.4	Present invention
Element 5	Compound 5	1.3	Present invention
Element 6	Compound 6	1.7	Present invention
Element 7	Compound 7	1.7	Present invention
Element 8	Compound 8	1.4	Present invention
Element 9	Compound 9	1.3	Present invention
Element 10	Compound 10	1.5	Present invention
Element 11	Compound 11	1.4	Present invention
Element 12	Compound 12	1.4	Present invention
Comparative element 1	Comparative compound 1	0.1	Comparative Example
Comparative element 2	Comparative compound 2	0.01	Comparative Example
Comparative element 3	Comparative compound 3	0.006	Comparative Example
Comparative element 4	Comparative compound 4	0.02	Comparative Example
Comparative element 5	Comparative compound 5	1.0	Comparative Example

[0330] From the above Table 36, it was understood that the organic transistor element of each of the examples using the compound of the present invention has high carrier mobility and can be preferably used as an organic semiconductor material.

[0331] In contrast, it was understood that the organic transistor elements in which the comparative compounds 1 to 5 not being included in the range of Formula (1) were used as organic semiconductor materials in the semiconductor active layer have low carrier mobility.

[Examples 13 to 24 and Comparative Examples 6 to 8]

<Preparation of bottom gate/bottom contact-type element>

[0332] In Examples 13 to 24 and Comparative Examples 6 to 8, a bottom gate/bottom contact-type organic transistor element was prepared. The details are described below.

[0333] An anisole solution containing 0.1% by mass of the compound 1 was heated to 100°C, and in a nitrogen atmosphere, the solution was cast onto a substrate for measuring FET characteristics heated to 90°C, thereby obtaining a non-light-emitting organic transistor element 2. As the substrate for measuring FET characteristics, a silicon substrate having a bottom gate/bottom contact structure was used which included chromium/gold (gate width $W = 100 \text{ nm}$, gate length $L = 100 \text{ }\mu\text{m}$) arranged to form a comb pattern as source and drain electrodes and included SiO_2 (film thickness: 200 nm) as an insulating layer. The obtained element 13 was taken as an organic transistor element of Example 13.

[0334] Elements 14 to 24 and comparative elements 6 to 8 were prepared in the same manner as used for preparing the element 13, except that any one of the compounds 2 to 12 or the comparative compounds 1, 2, or 5 was used instead of the compound 1. The obtained elements 14 to 24 and the comparative elements 6 to 8 were taken as organic transistor elements of Examples 14 to 24 and Comparative Examples 6 to 8.

<Evaluation>

[0335] For the elements 13 to 24 and the comparative elements 6 to 8, FET characteristics of an organic transistor element were evaluated in the same manner as in Example 1. The results are shown in the following Table 37.

[Table 37]

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Note
Element 13	Compound 1	0.56	Present invention
Element 14	Compound 2	0.50	Present invention
Element 15	Compound 3	0.50	Present invention
Element 16	Compound 4	0.45	Present invention
Element 17	Compound 5	0.45	Present invention
Element 18	Compound 6	0.55	Present invention
Element 19	Compound 7	0.50	Present invention
Element 20	Compound 8	0.48	Present invention
Element 21	Compound 9	0.42	Present invention
Element 22	Compound 10	0.48	Present invention
Element 23	Compound 11	0.45	Present invention
Element 24	Compound 12	0.50	Present invention
Comparative element 6	Comparative compound 1	0.03	Comparative Example
Comparative element 7	Comparative compound 2	< 0.001	Comparative Example
Comparative element 8	Comparative compound 5	0.3	Comparative Example

[Examples 25 to 36 and Comparative Examples 9 to 11]

<Preparation of bottom gate/bottom contact-type element using polymer binder>

[0336] A bottom gate/bottom contact-type element 25 was prepared in the same manner as in Example 13, except that, in Example 13, a material (material 1') containing the compound 1 and poly α -methylstyrene at a mass ratio of 1:1 was used instead of the compound 1. The obtained element 25 was taken as an organic transistor element of Example 25.

[0337] Elements 26 to 36 and comparative elements 9 to 11 were prepared in the same manner as used for preparing the element 25, except that, in preparing the element 25, any one of the compounds 2 to 12 or the comparative compounds 1, 2, and 5 was used instead of the compound 1. The obtained elements 26 to 36 and comparative elements 9 to 11 were taken as organic transistor elements of Examples 26 to 36 and Comparative Examples 9 to 11. The materials containing each of the compounds 2 to 12 and poly α -methylstyrene at a mass ratio 1:1 were named to materials 2' to 12' respectively.

<Evaluation>

[0338] For the elements 25 to 36 and the comparative elements 9 to 11, FET characteristics of an organic transistor element were evaluated in the same manner as in Example 1. The results are shown in the following Table 38.

[Table 38]

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Note
Element 25	Material 1'	0.90	Present invention
Element 26	Material 2'	0.88	Present invention
Element 27	Material 3'	0.90	Present invention
Element 28	Material 4'	0.58	Present invention
Element 29	Material 5'	0.52	Present invention
Element 30	Material 6'	0.75	Present invention

(continued)

Element No.	Organic semiconductor material	Carrier mobility (cm ² /Vs)	Note
5 Element 31	Material 7'	0.70	Present invention
Element 32	Material 8'	0.48	Present invention
Element 33	Material 9'	0.45	Present invention
10 Element 34	Material 10'	0.50	Present invention
Element 35	Material 11'	0.45	Present invention
Element 36	Material 12'	0.58	Present invention
15 Comparative element 9	Comparative compound 1 and poly α -methylstyrene	0.02	Comparative Example
Comparative element 10	Comparative compound 2 and poly α -methylstyrene	< 0.001	Comparative Example
20 Comparative element 11	Comparative compound 5 and poly α -methylstyrene	0.21	Comparative Example

[0339] From the above Tables 37 and 38, it was understood that the organic transistor element of each example using the compound of the present invention exhibits high carrier mobility even in a case where the element is used in a bottom gate/bottom contact-type element and even in a case where a polymer binder is used, and that the organic transistor element can be preferably used as an organic semiconductor material.

[0340] In contrast, it was understood that the organic transistor element, in which the comparative compound 1, 2, or 5 not being included in the range of Formula (1) is used as an organic semiconductor material in a semiconductor active layer, exhibits low carrier mobility.

Explanation of References

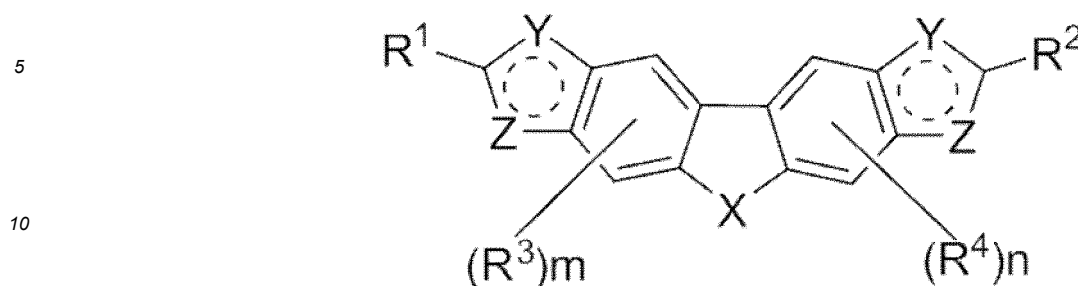
[0341]

- 11: substrate
- 12: electrode
- 13: insulator layer
- 14: semiconductor active layer (organic substance layer, organic semiconductor layer)
- 15a, 15b: electrode
- 31: substrate
- 32: electrode
- 33: insulator layer
- 34a, 34b: electrode
- 35: semiconductor active layer (organic substance layer, organic semiconductor layer)
- 41: coating solution
- 42: substrate A
- 43: member B

Claims

1. An organic transistor comprising a semiconductor active layer which is represented by the following Formula (1) and has a molecular weight of equal to or less than 3,000;

Formula (1)



in Formula (1),

X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR⁵;

Y and Z each independently represent CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷, two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other;

a ring containing Y and Z is an aromatic heterocycle;

any one of R¹ and R² and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups;

any one of R³ and R⁴ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R², R⁵, R⁶, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

R³ and R⁴ each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, in a case where m is 2, R³'s may be the same as or different from each other, and in a case where n is 2, R⁴'s may be the same as or different from each other;

m and n each independently represent an integer of 0 to 2;

here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷ are excluded;

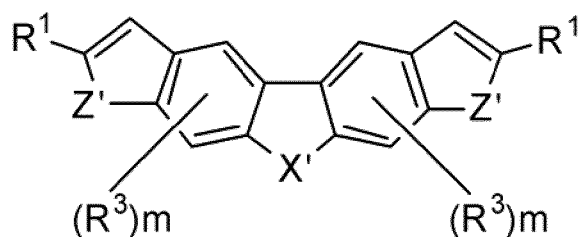
in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R¹ and R² are a hydrogen atom is excluded;

in a case where X is a sulfur atom, Y is CH, Z is a sulfur atom, and both of R¹ and R² are an alkyl group, one of R¹ and R² and the aromatic heterocycle containing Y and Z are bonded to each other through the group A of divalent linking groups; and

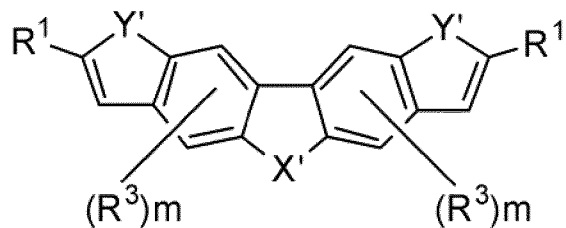
a case where both of R¹ and R² are a hydrogen atom, and both of m and n are 0 is excluded.

2. The organic transistor according to claim 1, wherein in Formula (1), both of m and n are 0.
3. The organic transistor according to claim 1 or 2, wherein in Formula (1), each of R¹ and R² is independently an alkyl group having 20 or less carbon atoms, an aryl group having 20 or less carbon atoms, or a heteroaryl group having 20 or less carbon atoms.
4. The organic transistor according to any one of claims 1 to 3, wherein the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 is a compound which is represented by the following Formula (2) or (3) and has a molecular weight of equal to or less than 3,000;

Formula (2)



Formula (3)



in Formulae (2) and (3),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

each of Y' and Z' is independently selected from NR⁷, an oxygen atom, a sulfur atom, and a selenium atom; a ring containing Y' and Z' is an aromatic heterocycle;

R¹ and the aromatic heterocycle containing Y' and Z' may be bonded to each other through the following group A of divalent linking groups;

R³ and a benzene ring may be bonded to each other through the following group A of divalent linking groups; the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other;

each R³ independently represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and in a case where m is 2, R³'s may be the same as or different from each other;

each m is independently an integer of 0 to 2;

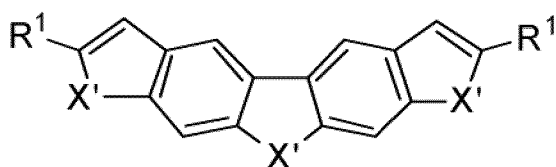
here, a case where both of Y' and Z' are NR⁷ is excluded;

in a case where X', Z', and R¹ in Formula (2) are a sulfur atom, a sulfur atom, and an alkyl group respectively, R¹ and the aromatic heterocycle containing Z' are bonded to each other through the group A of divalent linking groups; and

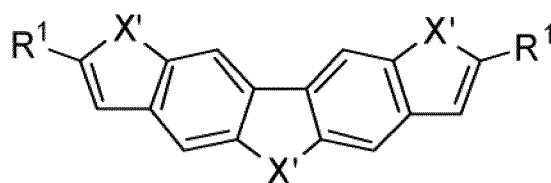
a case where R¹ is a hydrogen atom and all of m's are 0 is excluded.

5. The organic transistor according to any one of claims 1 to 4, wherein the compound which is represented by Formula (1) and has a molecular weight of equal to or less than 3,000 is a compound which is represented by the following Formula (4) or (5) and has a molecular weight of equal to or less than 3,000;

Formula (4)



Formula (5)



in Formulae (4) and (5),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

R¹ and an aromatic heterocycle containing X' may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

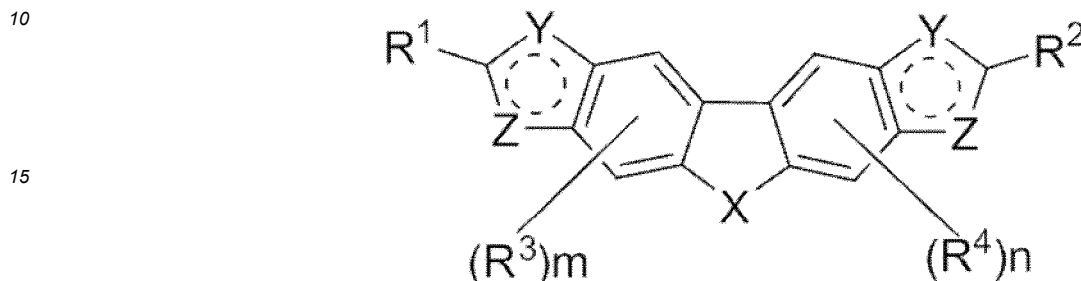
R¹ represents an aryl group having a linear aliphatic hydrocarbon group or a heteroaryl group having a linear

aliphatic hydrocarbon group

R⁸ represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other.

- 5 6. A compound which is represented by the following Formula (1A) and has a molecular weight of equal to or less than 3,000;

Formula (1A)



in Formula (1A),

X represents an oxygen atom, a sulfur atom, a selenium atom, a tellurium atom, or NR⁵;

Y and Z each independently represent CR⁶, an oxygen atom, a sulfur atom, a selenium atom, a nitrogen atom, or NR⁷, two Y's may be the same as or different from each other, and two Z's may be the same as or different from each other;

a ring containing Y and Z is an aromatic heterocycle;

any one of R¹ and R² and the aromatic heterocycle containing Y and Z may be bonded to each other through the following group A of divalent linking groups;

any one of R³ and R⁴ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R², R⁵, R⁶, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

R³ and R⁴ each independently represent an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, in a case where m is 2, R³'s may be the same as or different from each other, and in a case where n is 2, R⁴'s may be the same as or different from each other;

m and n each independently represent an integer of 0 to 2;

here, a case where both of Y and Z are CR⁶ and a case where both of Y and Z are any one of a nitrogen atom and NR⁷ are excluded;

a case where X is NR⁵, Y is a nitrogen atom, and Z is an oxygen atom is excluded;

in a case where X is NR⁵, Y is CR⁶, and Z is a sulfur atom, a case where both of R¹ and R² are a hydrogen atom is excluded;

in a case where X is a sulfur atom, Y is CH, Z is a sulfur atom, and both of R¹ and R² are an alkyl group, one of R¹ and R² and the aromatic heterocycle containing Y and Z are bonded to each other through the group A of divalent linking groups; and

a case where both of R¹ and R² are a hydrogen atom, and both of m and n are 0 is excluded.

- 50 7. The compound according to claim 6,
wherein in Formula (1A), both of m and n are 0.
8. The compound according to claim 6 or 7,
wherein in Formula (1A), each of R¹ and R² is independently an alkyl group having 20 or less carbon atoms, an aryl group having 20 or less carbon atoms, or a heteroaryl group having 20 or less carbon atoms.
- 55 9. The compound according to any one of claims 6 to 8,
wherein the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than

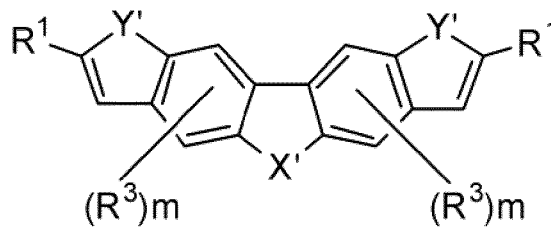
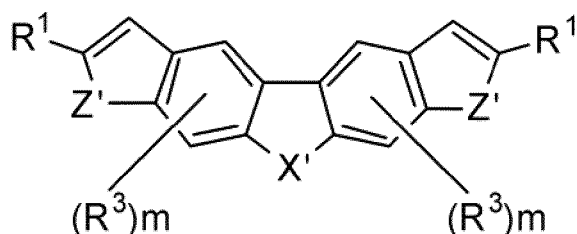
3,000 is a compound which is represented by the following Formula (2) or (3) and has a molecular weight of equal to or less than 3,000;

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Formula (2)

Formula (3)

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in Formulae (2) and (3),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

each of Y' and Z' is independently selected from NR⁷, an oxygen atom, a sulfur atom, and a selenium atom;

20

a ring containing Y' and Z' is an aromatic heterocycle;

R¹ and the aromatic heterocycle containing Y' and Z' may be bonded to each other through the following group A of divalent linking groups;

R³ and a benzene ring may be bonded to each other through the following group A of divalent linking groups;

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the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹, R⁷, and R⁸ each independently represent a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other;

30

each R³ independently represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and in a case where m is 2, R³'s may be the same as or different from each other;

each m is independently an integer of 0 to 2;

here, a case where both of Y' and Z' are NR⁷ is excluded;

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in a case where X', Z', and R¹ in Formula (2) are a sulfur atom, a sulfur atom, and an alkyl group respectively, R¹ and the aromatic heterocycle containing Z' are bonded to each other through the group A of divalent linking groups; and

a case where R¹ is a hydrogen atom and all of m's are 0 is excluded.

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10. The compound according to any one of claims 6 to 9,

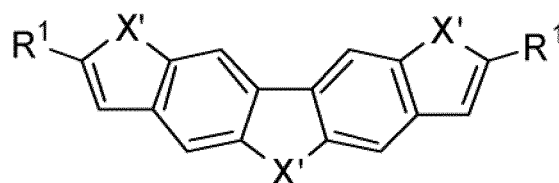
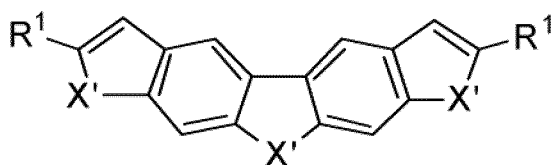
wherein the compound which is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is a compound which is represented by the following Formula (4) or (5) and has a molecular weight of equal to or less than 3,000;

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Formula (4)

Formula (5)

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in Formulae (4) and (5),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom;

R¹ and an aromatic heterocycle containing X' may be bonded to each other through the following group A of divalent linking groups;

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the group A of divalent linking groups represents any one of divalent linking groups -O-, -S-, -NR⁸-, -CO-, -SO-, and -SO₂- or represents a divalent linking group in which two or more of these divalent linking groups are bonded to each other;

R¹ represents an aryl group having a linear aliphatic hydrocarbon group or a heteroaryl group having a linear aliphatic hydrocarbon group

R⁸ represents a hydrogen atom, an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent, and two or more R¹'s may be the same as or different from each other.

11. An organic semiconductor material for a non-light-emitting organic semiconductor device containing the compound according to any one of claims 6 to 10 that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

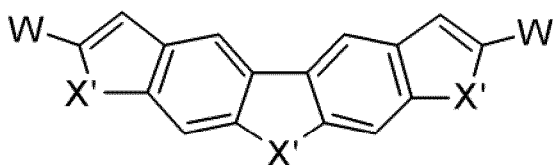
12. A coating solution for a non-light-emitting organic semiconductor device containing the compound according to any one of claims 6 to 10 that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

13. A method for manufacturing an organic transistor, comprising:
a step of preparing a semiconductor active layer by coating a substrate with the coating solution for a non-light-emitting organic semiconductor device according to claim 12 and drying the coating solution.

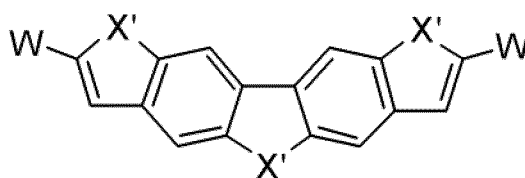
14. An organic semiconductor film for a non-light-emitting organic semiconductor device containing the compound according to any one of claims 6 to 10 that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000.

15. A method for synthesizing an organic semiconductor material,
wherein a compound represented by the following Formula (6) or (7) is reacted with a compound represented by Formula (8) by heating in the presence of a transition metal catalyst and an organic solvent such that the compound according to any one of claims 6 to 10 that is represented by Formula (1A) and has a molecular weight of equal to or less than 3,000 is synthesized;

Formula (6)

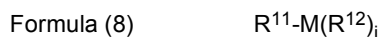


Formula (7)



in Formulae (6) and (7),

each X' independently represents an oxygen atom, a sulfur atom, or a selenium atom; and
each W independently represents a halogen atom or a perfluoroalkylsulfonyloxy group;



R¹¹ represents an alkyl group, an alkenyl group, an alkynyl group, an aryl group, or a heteroaryl group and may further have a substituent;

M represents magnesium, silicon, boron, tin, or zinc;

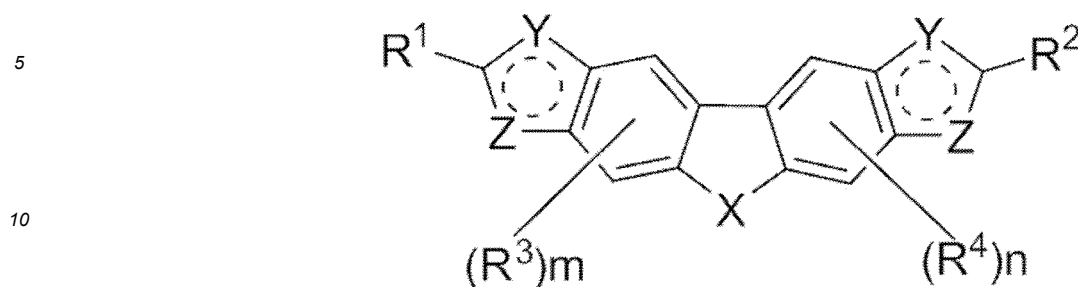
each R¹² independently represents a halogen atom, an alkyl group, an alkenyl group, an alkynyl group, an alkoxy group, or a hydroxyl group, and R¹²'s may be the same as or different from each other and may form a ring; and

i represents an integer of 1 to 3 and equals a valency of M - 1, here, in a case where M is boron, i may be 3.

Patentansprüche

1. Organischer Transistor, umfassend eine aktive Halbleiterschicht, die durch die folgende Formel (1) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist;

Formel (1)



15 in Formel (1),

stellt X ein Sauerstoffatom, ein Schwefelatom, ein Selenatom, ein Telluratom oder NR⁵ dar,
stellen Y und Z jeweils unabhängig voneinander CR⁶, ein Sauerstoffatom, ein Schwefelatom, ein Selenatom,
ein Stickstoffatom oder NR⁷ dar, können zwei Y die gleichen oder voneinander verschieden sein und können
zwei Z die gleichen oder voneinander verschieden sein;

20 ist ein Y und Z enthaltender Ring ein aromatischer Heterozyklus;

können jedes von R¹ und R² und der Y und Z enthaltende aromatische Heterozyklus durch die folgende Gruppe
A zweiwertiger Linkergruppen aneinandergebunden sein,
können jedes von R³ und R⁴ und ein Benzolring durch die folgende Gruppe A zweiwertiger Linkergruppen
aneinandergebunden sein,

25 stellt die Gruppe A zweiwertiger Linkergruppen eine der zweiwertigen Linkergruppen -O-, -S-, -NR⁸-, -CO-, -SO-
und -SO₂- oder eine zweiwertige Linkergruppe, in welcher zwei oder mehr dieser zweiwertigen Linkergruppen
aneinandergebunden sind, dar;

stellen R¹, R², R⁵, R⁶, R⁷ und R⁸ jeweils unabhängig voneinander ein Wasserstoffatom, eine Alkylgruppe, eine
Alkenylgruppe, eine Alkynylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen
Substituenten aufweisen;

stellen R³ und R⁴ jeweils unabhängig voneinander eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe,
eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substituenten aufweisen;

können, falls m 2 ist, die R³ die gleichen oder voneinander verschieden sein, und

können, falls n 2 ist, die R⁴ die gleichen oder voneinander verschieden sein,

35 stellen m und n jeweils unabhängig voneinander eine ganze Zahl von 0 bis 2 dar,
wobei hierbei ein Fall, dass Y und Z beide CR⁶ sind, und ein Fall, dass Y und Z beide eines aus einem Stick-
stoffatom oder NR⁷ sind, ausgeschlossen sind;

wobei in einem Fall, dass X NR⁵ ist, Y CR⁶ ist und Z ein Schwefelatom ist, ein Fall, dass R¹ und R² beide ein
Wasserstoffatom sind, ausgeschlossen ist;

40 wobei in einem Fall, dass X ein Schwefelatom ist, Y CH ist, Z ein Schwefelatom ist und R¹ und R² beide eine
Alkylgruppe sind, eines von R¹ und R² und der Y und Z enthaltende aromatische Ring durch eine Gruppe A
zweiwertiger Linkergruppen aneinandergebunden sind, und

wobei ein Fall, dass R¹ und R² beide ein Wasserstoffatom sind und m und n beide 0 sind, ausgeschlossen ist.

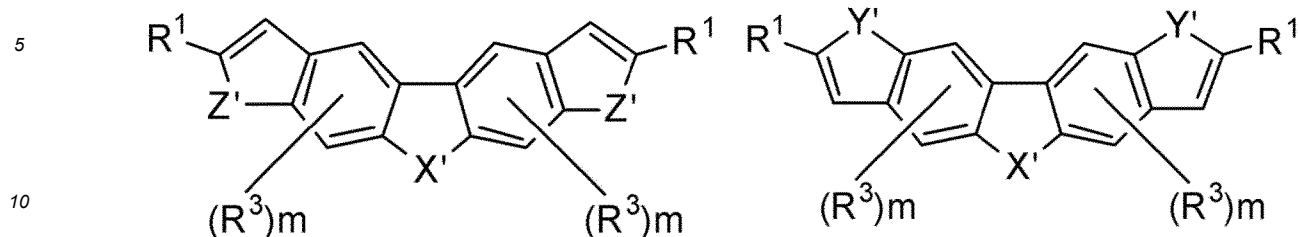
45 **2.** Organischer Transistor gemäß Anspruch 1,
wobei in Formel (1) m und n beide 0 sind.

3. Organischer Transistor gemäß Anspruch 1 oder 2,
wobei in Formel (1) jedes von R¹ und R² unabhängig voneinander eine Alkylgruppe mit 20 oder weniger Kohlen-
stoffatomen, eine Arylgruppe mit 20 oder weniger Kohlenstoffatomen oder eine Heteroarylgruppe mit 20 oder weniger
Kohlenstoffatomen darstellt.

4. Organischer Transistor gemäß einem der Ansprüche 1 bis 3,
wobei die Verbindung, die durch die Formel (1) dargestellt wird und ein Molekulargewicht von 3000 oder weniger
aufweist, eine Verbindung ist, die durch die folgende Formel (2) oder (3) dargestellt wird und ein Molekulargewicht
von 3000 oder weniger aufweist;

Formel (2)

Formel (3)



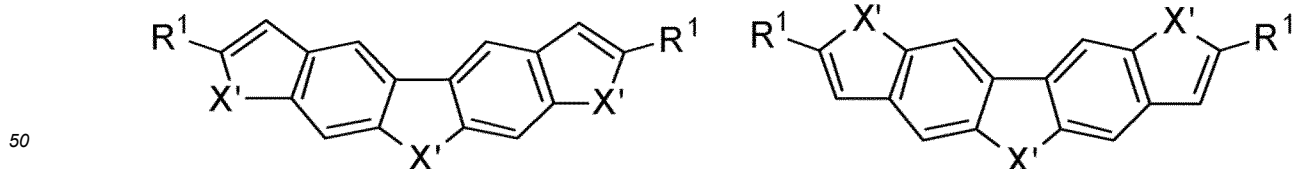
in Formeln (2) und (3)

- 15 stellen die X' jeweils unabhängig voneinander ein Sauerstoffatom, ein Schwefelatom oder ein Selenatom dar;
sind die Y' und die Z' jeweils unabhängig voneinander ausgewählt aus NR^7 , einem Sauerstoffatom, einem
Schwefelatom und einem Selenatom;
ist ein Y' und Z' enthaltender Ring ein aromatischer Heterozyklus;
können R^1 und der Y' und Z' enthaltende aromatische Heterozyklus durch die folgende Gruppe A zweiwertiger
20 Linkergruppen aneinandergelungen sein;
können R^3 und ein Benzolring durch die folgende Gruppe A zweiwertiger Linkergruppen aneinandergelungen
sein,
stellt die Gruppe A zweiwertiger Linkergruppen eine der zweiwertigen Linkergruppen $-O-$, $-S-$, $-NR^8-$, $-CO-$, $-SO-$
25 und $-SO_2-$ oder eine zweiwertige Linkergruppe, in welcher zwei oder mehr dieser zweiwertigen Linkergruppen
aneinandergelungen sind, dar;
stellen R^1 , R^7 und R^8 jeweils unabhängig voneinander ein Wasserstoffatom, eine Alkylgruppe, eine Alkenyl-
gruppe, eine Alkynylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substi-
tuenten aufweisen, und können zwei oder mehr der R^1 die gleichen oder voneinander verschieden sein;
stellen die R^3 jeweils unabhängig voneinander eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe, eine
30 Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substituenten aufweisen, und können,
falls $m \geq 2$ ist, die R^3 die gleichen oder voneinander verschieden sein,
sind die m jeweils unabhängig voneinander eine ganze Zahl von 0 bis 2;
wobei hierbei ein Fall, dass Y' und Z' beide NR^7 sind, ausgeschlossen ist;
wobei in einem Fall, dass X' , Z' und R^1 in Formel (2) ein Schwefelatom, ein Schwefelatom beziehungsweise
35 eine Alkylgruppe sind, R^1 und der Z' enthaltende aromatische Heterozyklus durch eine Gruppe A zweiwertiger
Linkergruppen aneinandergelungen sind; und
wobei ein Fall, dass R^1 ein Wasserstoffatom ist und die m alle 0 sind, ausgeschlossen ist.

5. Organischer Transistor gemäß einem der Ansprüche 1 bis 4,
40 wobei die Verbindung, die durch die Formel (1) dargestellt wird und ein Molekulargewicht von 3000 oder weniger
aufweist, eine Verbindung ist, die durch die folgende Formel (4) oder (5) dargestellt wird und ein Molekulargewicht
von 3000 oder weniger aufweist;

Formel (4)

Formel (5)



in Formeln (4) und (5)

- 55 stellen die X' jeweils unabhängig voneinander ein Sauerstoffatom, ein Schwefelatom oder ein Selenatom dar;
können R^1 und ein X' enthaltender aromatischer Heterozyklus durch die folgende Gruppe A zweiwertiger Link-
kergruppen aneinandergelungen sein;
stellt die Gruppe A zweiwertiger Linkergruppen eine der zweiwertigen Linkergruppen $-O-$, $-S-$, $-NR^8-$, $-CO-$, $-SO-$

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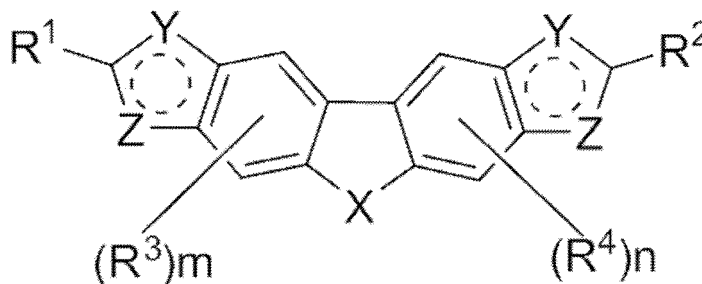
und -SO₂- oder eine zweiwertige Linkergruppe, in welcher zwei oder mehr dieser zweiwertigen Linkergruppen aneinandergebunden sind, dar;

stellt R¹ eine Arylgruppe mit einer linearen aliphatischen Kohlenstoffgruppe oder eine Heteroarylgruppe mit einer linearen aliphatischen Kohlenstoffgruppe dar

stellt R⁸ ein Wasserstoffatom, eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und kann ferner einen Substituenten aufweisen, und können zwei oder mehr der R¹ die gleichen oder voneinander verschieden sein.

6. Verbindung, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist;

Formel (1A)



in Formel (1A)

stellt X ein Sauerstoffatom, ein Schwefelatom, ein Selenatom, ein Telluratom oder NR⁵ dar,

stellen Y und Z jeweils unabhängig voneinander CR⁶, ein Sauerstoffatom, ein Schwefelatom, ein Selenatom, ein Stickstoffatom oder NR⁷ dar, können zwei Y die gleichen oder voneinander verschieden sein und können zwei Z die gleichen oder voneinander verschieden sein;

ist ein Y und Z enthaltender Ring ein aromatischer Heterozyklus;

können jedes von R¹ und R² und der Y und Z enthaltende aromatische Heterozyklus durch die folgende Gruppe A zweiwertiger Linkergruppen aneinandergebunden sein,

können jedes von R³ und R⁴ und ein Benzolring durch die folgende Gruppe A zweiwertiger Linkergruppen aneinandergebunden sein,

stellt die Gruppe A zweiwertiger Linkergruppen eine der zweiwertigen Linkergruppen -O-, -S-, -NR⁸-, -CO-, -SO- und -SO₂- oder eine zweiwertige Linkergruppe, in welcher zwei oder mehr dieser zweiwertigen Linkergruppen aneinandergebunden sind, dar;

stellen R¹, R², R⁵, R⁶, R⁷ und R⁸ jeweils unabhängig voneinander ein Wasserstoffatom, eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substituenten aufweisen;

stellen R³ und R⁴ jeweils unabhängig voneinander eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substituenten aufweisen;

können, falls m 2 ist, die R³ die gleichen oder voneinander verschieden sein, und

können, falls n 2 ist, die R⁴ die gleichen oder voneinander verschieden sein,

stellen m und n jeweils unabhängig voneinander eine ganze Zahl von 0 bis 2 dar,

wobei hierbei ein Fall, dass Y und Z beide CR⁶ sind, und ein Fall, dass Y und Z beide eines aus einem Stickstoffatom oder NR⁷ sind, ausgeschlossen sind;

wobei ein Fall, dass X NR⁵ ist, Y ein Stickstoffatom ist und Z ein Sauerstoffatom ist, ausgeschlossen ist;

wobei in einem Fall, dass X NR⁵ ist, Y CR⁶ ist und Z ein Schwefelatom ist, ein Fall, dass R¹ und R² beide ein Wasserstoffatom sind, ausgeschlossen ist;

wobei in einem Fall, dass X ein Schwefelatom ist, Y CH ist, Z ein Schwefelatom ist und R¹ und R² beide eine Alkylgruppe sind, eines von R¹ und R² und der Y und Z enthaltende aromatische Ring durch eine Gruppe A zweiwertiger Linkergruppen aneinandergebunden sind, und

wobei ein Fall, dass R¹ und R² beide ein Wasserstoffatom sind und m und n beide 0 sind, ausgeschlossen ist.

7. Verbindung gemäß Anspruch 6, wobei in Formel (1A) m und n beide 0 sind.

8. Verbindung gemäß Anspruch 6 oder 7,
wobei in Formel (1A) jedes von R^1 und R^2 unabhängig voneinander eine Alkylgruppe mit 20 oder weniger Kohlenstoffatomen, eine Arylgruppe mit 20 oder weniger Kohlenstoffatomen oder eine Heteroarylgruppe mit 20 oder weniger Kohlenstoffatomen darstellt.

5

9. Verbindung gemäß einem der Ansprüche 6 bis 8,
wobei die Verbindung, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist, eine Verbindung ist, die durch die folgende Formel (2) oder (3) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist;

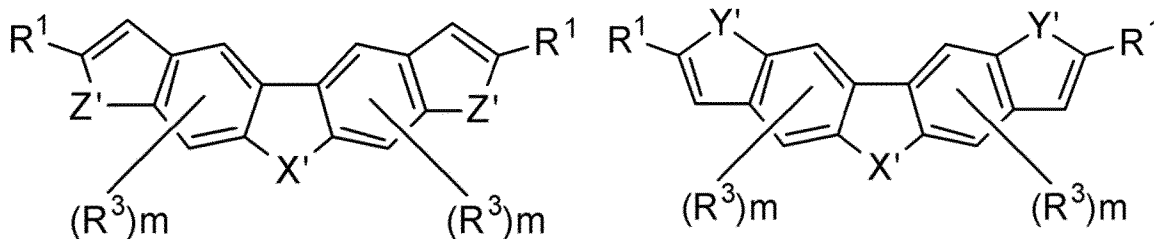
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Formel (2)

Formel (3)

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in Formeln (2) und (3)

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stellen die X' jeweils unabhängig voneinander ein Sauerstoffatom, ein Schwefelatom oder ein Selenatom dar;
sind die Y' und die Z' jeweils unabhängig voneinander ausgewählt aus NR^7 , einem Sauerstoffatom, ein Schwefelatom und einem Selenatom;

ist ein Y' und Z' enthaltender Ring ein aromatischer Heterozyklus;

30

können R^1 und der Y' und Z' enthaltende aromatische Heterozyklus durch die folgende Gruppe A zweiwertiger Linkergruppen aneinandergelungen sein;

können R^3 und ein Benzolring durch die folgende Gruppe A zweiwertiger Linkergruppen aneinandergelungen sein,

35

stellt die Gruppe A zweiwertiger Linkergruppen eine der zweiwertigen Linkergruppen $-O-$, $-S-$, $-NR^8-$, $-CO-$, $-SO-$ und $-SO_2-$ oder eine zweiwertige Linkergruppe, in welcher zwei oder mehr dieser zweiwertigen Linkergruppen aneinandergelungen sind, dar;

stellen R^1 , R^7 und R^8 jeweils unabhängig voneinander ein Wasserstoffatom, eine Alkylgruppe, eine Alkenylgruppe, eine Alkylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substituenten aufweisen, und können zwei oder mehr der R^1 die gleichen oder voneinander verschieden sein;

40

stellen die R^3 jeweils unabhängig voneinander eine Alkylgruppe, eine Alkenylgruppe, eine Alkylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und können ferner einen Substituenten aufweisen, und können, falls $m \geq 2$ ist, die R^3 die gleichen oder voneinander verschieden sein,

sind die m jeweils unabhängig voneinander eine ganze Zahl von 0 bis 2;

wobei hierbei ein Fall, dass Y' und Z' beide NR^7 sind, ausgeschlossen ist;

45

wobei in einem Fall, dass X' , Z' und R^1 in Formel (2) ein Schwefelatom, ein Schwefelatom beziehungsweise eine Alkylgruppe sind, R^1 und der Z' enthaltende aromatische Heterozyklus durch eine Gruppe A zweiwertiger Linkergruppen aneinandergelungen sind; und

wobei ein Fall, dass R^1 ein Wasserstoffatom ist und die m alle 0 sind, ausgeschlossen ist.

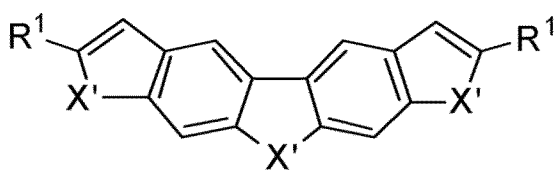
10. Verbindung gemäß einem der Ansprüche 6 bis 9,

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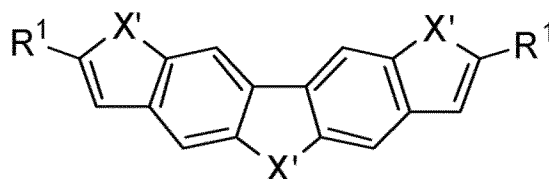
wobei die Verbindung, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist, eine Verbindung ist, die durch die folgende Formel (4) oder (5) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist;

55

Formel (4)



Formel (5)



in Formeln (4) und (5)

stellen die X' jeweils unabhängig voneinander ein Sauerstoffatom, ein Schwefelatom oder ein Selenatom dar; können R¹ und ein X' enthaltender aromatischer Heterozyklus durch die folgende Gruppe A zweiwertiger Linkergruppen aneinandergelagert sein;

stellt die Gruppe A zweiwertiger Linkergruppen eine der zweiwertigen Linkergruppen -O-, -S-, -NR⁸-, -CO-, -SO- und -SO₂- oder eine zweiwertige Linkergruppe, in welcher zwei oder mehr dieser zweiwertigen Linkergruppen aneinandergelagert sind, dar;

stellt R¹ eine Arylgruppe mit einer linearen aliphatischen Kohlenwasserstoffgruppe oder eine Heteroarylgruppe mit einer linearen aliphatischen Kohlenwasserstoffgruppe dar

stellt R⁸ ein Wasserstoffatom, eine Alkylgruppe, eine Alkenylgruppe, eine Alkylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und kann ferner einen Substituenten aufweisen, und können zwei oder mehr der R¹ die gleichen oder voneinander verschieden sein.

11. Organisches Halbleitermaterial für ein nicht-lichtemittierendes organisches Halbleiterbauelement, enthaltend die Verbindung gemäß einem der Ansprüche 6 bis 10, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist.

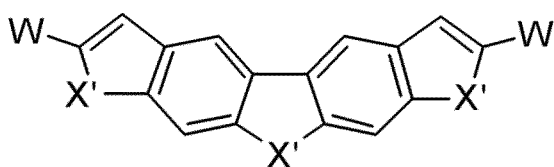
12. Beschichtungslösung für ein nicht-lichtemittierendes organisches Halbleiterbauelement, enthaltend die Verbindung gemäß einem der Ansprüche 6 bis 10, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist.

13. Verfahren zur Herstellung eines organischen Transistors, umfassend:
einen Schritt des Herstellens einer aktiven Halbleiterschicht durch Beschichten eines Substrats mit der Beschichtungslösung für ein nicht-lichtemittierendes organisches Halbleiterbauelement gemäß Anspruch 12 und des Trocknens der Beschichtungslösung.

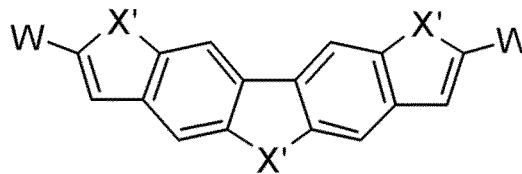
14. Organischer Halbleiterfilm für ein nicht-lichtemittierendes organisches Halbleiterbauelement, enthaltend die Verbindung gemäß einem der Ansprüche 6 bis 10, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist.

15. Verfahren zur Synthese eines organischen Halbleitermaterials, wobei eine Verbindung, die durch die folgende Formel (6) oder (7) dargestellt wird, mit einer Verbindung, die durch Formel (8) dargestellt wird, durch Erhitzen in der Gegenwart eines Übergangsmetallkatalysators und eines organischen Lösungsmittels zur Reaktion gebracht wird, sodass die Verbindung gemäß einem der Ansprüche 6 bis 10, die durch die Formel (1A) dargestellt wird und ein Molekulargewicht von 3000 oder weniger aufweist, synthetisiert wird;

Formel (6)



Formel (7)



in Formeln (6) und (7),

stellen die X' jeweils unabhängig voneinander ein Sauerstoffatom, ein Schwefelatom oder ein Selenatom dar;
stellen die W jeweils unabhängig voneinander ein Halogenatom oder eine Perfluoralkylsulfonyloxygruppe dar;

Formel (8) $R^{11}-M(R^{12})_i$

5

R¹¹ stellt eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe, eine Arylgruppe oder eine Heteroarylgruppe dar und kann ferner einen Substituenten aufweisen,

M stellt Magnesium, Silizium, Bor, Zinn oder Zink dar;

die R¹² stellen jeweils unabhängig voneinander ein Halogenatom, eine Alkylgruppe, eine Alkenylgruppe, eine Alkynylgruppe, eine Alkoxygruppe oder eine Hydroxygruppe dar, und die R¹² können die gleichen oder voneinander verschieden sein und können einen Ring bilden; und

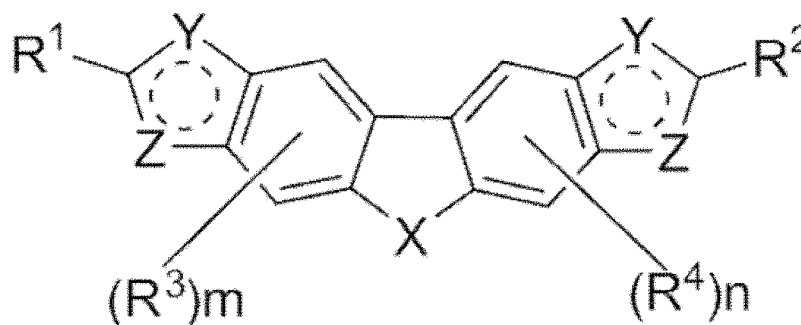
i stellt eine ganze Zahl von 1 bis 3 dar und entspricht einer Valenz von M-1, hierbei kann, falls M Bor ist, i 3 sein.

15 Revendications

1. Transistor organique comprenant une couche active semi-conductrice qui est représentée par la Formule (1) suivante et a un poids moléculaire égal ou inférieur à 3 000;

20

Formule (1)



25

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dans la Formule (1),

35

X représente un atome d'oxygène, un atome de soufre, un atome de sélénium, un atome de tellure, ou NR⁵ ;
Y et Z représentent chacun indépendamment CR⁶, un atome d'oxygène, un atome de soufre, un atome de sélénium, un atome d'azote, ou NR⁷, deux Y peuvent être identiques ou différents l'un de l'autre, et deux Z peuvent être identiques ou différents l'un de l'autre ;

40

un cycle contenant Y et Z est un hétérocycle aromatique ;

l'un quelconque parmi R¹ et R² et l'hétérocycle aromatique contenant Y et Z peuvent être liés l'un à l'autre par l'intermédiaire du groupe A suivant parmi des groupes de liaison divalente ;

l'un quelconque parmi R³ et R⁴ et un cycle benzénique peuvent être liés l'un à l'autre par l'intermédiaire du groupe A suivant parmi des groupes de liaison divalente ;

45

le groupe A parmi des groupes de liaison divalente représente l'un quelconque des groupes de liaison divalente -O-, -S-, -NR⁸-, -CO-, -SO- et -SO₂- ou représente un groupe de liaison divalente dans lequel deux ou plus de deux de ces groupes de liaison divalente sont liés les uns aux autres ;

R¹, R², R⁵, R⁶, R⁷, et R⁸ représentent chacun indépendamment un atome d'hydrogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peuvent en outre avoir un substituant ;

50

R³ et R⁴ représentent chacun indépendamment un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peuvent en outre avoir un substituant, dans un cas où m est égal à 2, les R³ peuvent être identiques ou différents l'un de l'autre, et dans un cas où n est égal à 2, les R⁴ peuvent être identiques ou différents l'un de l'autre ;

55

m et n représentent chacun indépendamment un nombre entier allant de 0 à 2 ; ici, un cas où Y et Z sont tous deux CR⁶ et un cas où Y et Z sont tous deux l'un quelconque parmi un atome d'azote et NR⁷ sont exclus ;

dans un cas où X est NR⁵, Y est CR⁶, et Z est un atome de soufre, un cas où R¹ et R² sont tous deux un atome d'hydrogène est exclu ;

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dans un cas où X est un atome de soufre, Y est CH, Z est un atome de soufre, et R¹ et R² sont tous deux un groupe alkyle, l'un parmi R¹ et R² et l'hétérocycle aromatique contenant Y et Z sont liés l'un à l'autre par l'intermédiaire du groupe A parmi des groupes de liaison divalente ; et un cas où R¹ et R² sont tous deux un atome d'hydrogène, et m et n sont tous deux égaux à 0 est exclu.

5

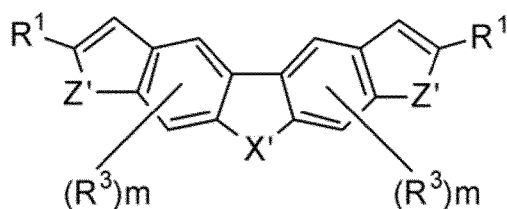
2. Transistor organique selon la revendication 1, dans lequel dans la Formule (1), m et n sont tous deux égaux à 0.

3. Transistor organique selon la revendication 1 ou 2, dans lequel dans la Formule (1), chacun parmi R¹ et R² est indépendamment un groupe alkyle ayant 20 atomes de carbone ou moins, un groupe aryle ayant 20 atomes de carbone ou moins, ou un groupe hétéroaryle ayant 20 atomes de carbone ou moins.

4. Transistor organique selon l'une quelconque des revendications 1 à 3, dans lequel le composé qui est représenté par la Formule (1) et a un poids moléculaire égal ou inférieur à 3 000 est un composé qui est représenté par la Formule (2) ou (3) suivante et a un poids moléculaire égal ou inférieur à 3 000 ;

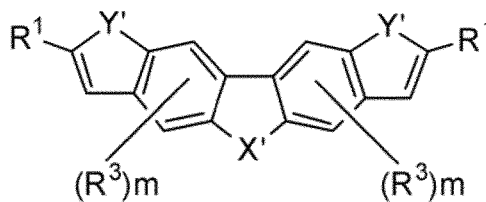
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Formule (2)



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Formule (3)



dans les Formules (2) et (3),

30

chaque X' représente indépendamment un atome d'oxygène, un atome de soufre, ou un atome de sélénium ; chacun parmi Y' et Z' est choisi indépendamment parmi NR⁷, un atome d'oxygène, un atome de soufre, et un atome de sélénium ;

un cycle contenant Y' et Z' est un hétérocycle aromatique ;

R¹ et l'hétérocycle aromatique contenant Y' et Z' peuvent être liés l'un à l'autre par l'intermédiaire du groupe A suivant parmi des groupes de liaison divalente ;

R³ et un cycle benzénique peuvent être liés l'un à l'autre par le groupe A suivant parmi des groupes de liaison divalente ;

40

le groupe A parmi des groupes de liaison divalente représente l'un quelconque des groupes de liaison divalente -O-, -S-, -NR⁸-, -CO-, -SO- et -SO₂- ou représente un groupe de liaison divalente dans lequel deux ou plus de deux de ces groupes de liaison divalente sont liés les uns aux autres ;

R¹, R⁷ et R⁸ représentent chacun indépendamment un atome d'hydrogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peuvent en outre avoir un substituant, et deux ou plus de deux R¹ peuvent être identiques ou différents les uns des autres ;

45

chaque R³ représente indépendamment un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peut en outre avoir un substituant, et dans un cas où m est égal à 2, les R³ peuvent être identiques ou différents l'un de l'autre ;

chaque m est indépendamment un nombre entier allant de 0 à 2 ;

ici, un cas où Y' et Z' sont tous deux NR⁷ est exclu ;

50

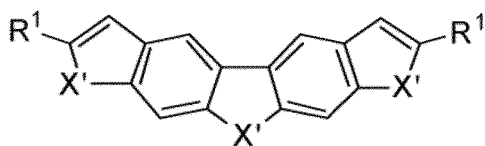
dans un cas où X', Z', et R¹ dans la Formule (2) sont respectivement un atome de soufre, un atome de soufre, et un groupe alkyle, R¹ et l'hétérocycle aromatique contenant Z' sont liés l'un à l'autre par le groupe A parmi des groupes de liaison divalente ; et

un cas où R¹ est un atome d'hydrogène et tous les m sont égaux à 0 est exclu.

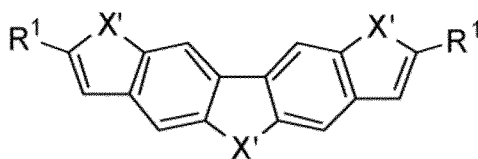
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5. Transistor organique selon l'une quelconque des revendications 1 à 4, dans lequel le composé qui est représenté par la Formule (1) et a un poids moléculaire égal ou inférieur à 3 000 est un composé qui est représenté par la Formule (4) ou (5) suivante et a un poids moléculaire égal ou inférieur à 3 000 ;

Formule (4)



Formule (5)



dans les Formules (4) et (5),

chaque X' représente indépendamment un atome d'oxygène, un atome de soufre, ou un atome de sélénium ;
R¹ et un hétérocycle aromatique contenant X' peuvent être liés l'un à l'autre par le groupe A suivant parmi des groupes de liaison divalente ;

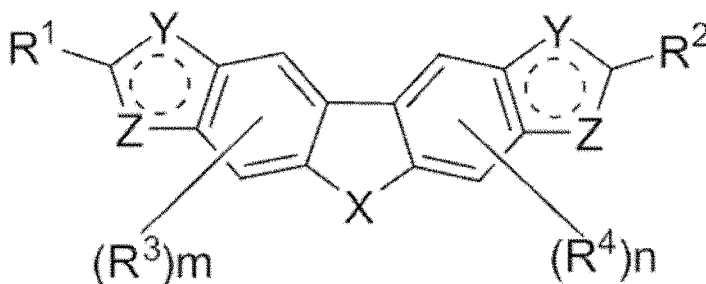
le groupe A parmi des groupes de liaison divalente représente l'un quelconque des groupes de liaison divalente -O-, -S-, -NR⁸-, -CO-, -SO- et -SO₂- ou représente un groupe de liaison divalente dans lequel deux ou plus de deux de ces groupes de liaison divalente sont liés les uns aux autres ;

R¹ représente un groupe aryle ayant un groupe hydrocarboné aliphatique linéaire ou un groupe hétéroaryle ayant un groupe hydrocarboné aliphatique linéaire

R⁸ représente un atome d'hydrogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peut en outre avoir un substituant, et deux ou plus de deux R¹ peuvent être identiques ou différents les uns des autres.

6. Composé qui est représenté par la Formule (1A) suivante et a un poids moléculaire égal ou inférieur à 3 000 ;

Formule (1A)



dans la Formule (1A),

X représente un atome d'oxygène, un atome de soufre, un atome de sélénium, un atome de tellure, ou NR⁵ ;
Y et Z représentent chacun indépendamment CR⁶, un atome d'oxygène, un atome de soufre, un atome de sélénium, un atome d'azote, ou NR⁷, deux Y peuvent être identiques ou différents l'un de l'autre, et deux Z peuvent être les identiques ou différents l'un de l'autre ;

un cycle contenant Y et Z est un hétérocycle aromatique ;

l'un quelconque parmi R¹ et R² et l'hétérocycle aromatique contenant Y et Z peuvent être liés l'un à l'autre par l'intermédiaire du groupe A suivant parmi des groupes de liaison divalente ;

l'un quelconque parmi R³ et R⁴ et un cycle benzénique peuvent être liés l'un à l'autre par l'intermédiaire du groupe A suivant parmi des groupes de liaison divalente ;

le groupe A de groupes de liaison divalente représente l'un quelconque des groupes de liaison divalente -O-, -S-, -NR⁸-, -CO-, -SO- et -SO₂- ou représente un groupe de liaison divalente dans lequel deux ou plus de deux de ces groupes de liaison divalente sont liés les uns aux autres ;

R¹, R², R⁵, R⁶, R⁷, et R⁸ représentent chacun indépendamment un atome d'hydrogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peuvent en outre avoir un substituant ;

R³ et R⁴ représentent chacun indépendamment un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peuvent en outre avoir un substituant, dans un cas où m est égal à 2, les R³ peuvent être identiques ou différents l'un de l'autre, et dans un cas où n est égal à 2, les R⁴ peuvent être identiques ou différents l'un de l'autre ;

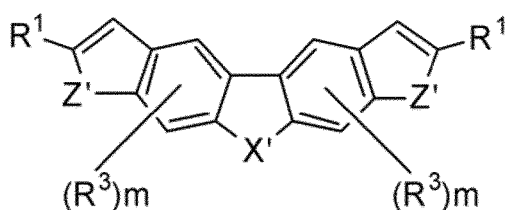
m et n représentent chacun indépendamment un nombre entier allant de 0 à 2 ;
 ici, un cas où Y et Z sont tous deux CR⁶ et un cas où Y et Z sont tous deux l'un quelconque parmi un atome d'azote et NR⁷ sont exclus ;
 un cas où X est NR⁵, Y est un atome d'azote et Z est un atome d'oxygène est exclu ;
 dans un cas où X est NR⁵, Y est CR⁶, et Z est un atome de soufre, un cas où R¹ et R² sont tous deux un atome d'hydrogène est exclu ;
 dans un cas où X est un atome de soufre, Y est CH, Z est un atome de soufre, et R¹ et R² sont tous deux un groupe alkyle, l'un parmi R¹ et R² et l'hétérocycle aromatique contenant Y et Z sont liés l'un à l'autre par l'intermédiaire du groupe A parmi des groupes de liaison divalente ; et
 un cas où R¹ et R² sont tous deux un atome d'hydrogène, et m et n sont tous deux égaux à 0 est exclu.

7. Composé selon la revendication 6,
 dans lequel, dans la Formule (1A), m et n sont tous deux égaux à 0.

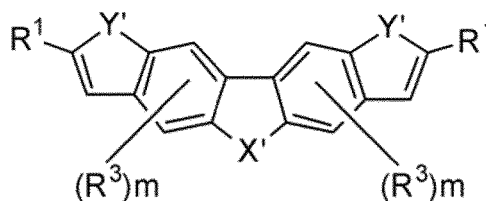
8. Composé selon la revendication 6 ou 7,
 dans lequel dans la Formule (1A), chacun parmi R¹ et R² est indépendamment un groupe alkyle ayant 20 atomes de carbone ou moins, un groupe aryle ayant 20 atomes de carbone ou moins, ou un groupe hétéroaryle ayant 20 atomes de carbone ou moins.

9. Composé selon l'une quelconque des revendications 6 à 8,
 dans lequel le composé qui est représenté par la Formule (1A) et a un poids moléculaire égal ou inférieur à 3 000 est un composé qui est représenté par la Formule (2) ou (3) suivante et a un poids moléculaire égal ou inférieur à 3 000 ;

Formule (2)



Formule (3)



dans les Formules (2) et (3),

chaque X' représente indépendamment un atome d'oxygène, un atome de soufre, ou un atome de sélénium ;
 chacun parmi Y' et Z' est choisi indépendamment parmi NR⁷, un atome d'oxygène, un atome de soufre, et un atome de sélénium ;

un cycle contenant Y' et Z' est un hétérocycle aromatique ;

R¹ et l'hétérocycle aromatique contenant Y' et Z' peuvent être liés l'un à l'autre par l'intermédiaire du groupe A suivant parmi des groupes de liaison divalente ;

R³ et un cycle benzénique peuvent être liés l'un à l'autre par le groupe A suivant parmi des groupes de liaison divalente ;

le groupe A parmi des groupes de liaison divalente représente l'un quelconque des groupes de liaison divalente -O-, -S-, -NR⁸-, -CO-, -SO- et -SO₂- ou représente un groupe de liaison divalente dans lequel deux ou plus de deux de ces groupes de liaison divalente sont liés les uns aux autres ;

R¹, R⁷ et R⁸ représentent chacun indépendamment un atome d'hydrogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peuvent en outre avoir un substituant, et deux ou plus de deux R¹ peuvent être identiques ou différents les uns des autres ;

chaque R³ représente indépendamment un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peut en outre avoir un substituant, et dans un cas où m est égal à 2, les R³ peuvent être identiques ou différents l'un de l'autre ;

chaque m est indépendamment un nombre entier allant de 0 à 2 ;

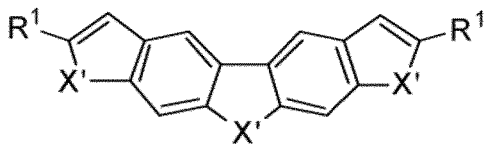
ici, un cas où Y' et Z' sont tous deux NR⁷ est exclu ;

dans un cas où X', Z', et R¹ dans la Formule (2) sont respectivement un atome de soufre, un atome de soufre, et un groupe alkyle, R¹ et l'hétérocycle aromatique contenant Z' sont liés l'un à l'autre par le groupe A parmi des groupes de liaison divalente ; et

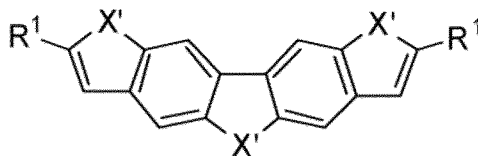
un cas où R¹ est un atome d'hydrogène et tous les m sont égaux à 0 est exclu.

10. Composé selon l'une quelconque des revendications 6 à 9,
dans lequel le composé qui est représenté par la Formule (1A) et a un poids moléculaire égal ou inférieur à 3 000
est un composé qui est représenté par la Formule (4) ou (5) suivante et a un poids moléculaire égal ou inférieur à
3 000 ;

Formule (4)



Formule (5)



dans les Formules (4) et (5),

chaque X' représente indépendamment un atome d'oxygène, un atome de soufre, ou un atome de sélénium ;
R¹ et un hétérocycle aromatique contenant X' peuvent être liés l'un à l'autre par le groupe A suivant parmi des
groupes de liaison divalente ;

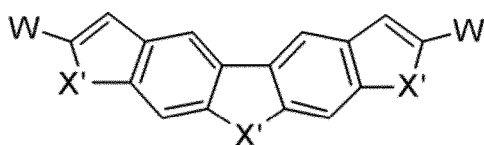
le groupe A parmi des groupes de liaison divalente représente l'un quelconque des groupes de liaison divalente
-O-, -S-, -NR⁸-, -CO-, -SO- et -SO₂- ou représente un groupe de liaison divalente dans lequel deux ou plus de
deux de ces groupes de liaison divalente sont liés les uns aux autres ;

R¹ représente un groupe aryle ayant un groupe hydrocarboné aliphatique linéaire ou un groupe hétéroaryle
ayant un groupe hydrocarboné aliphatique linéaire

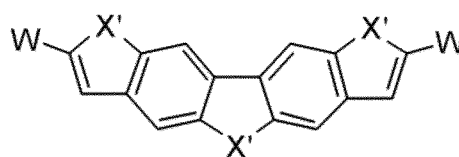
R⁸ représente un atome d'hydrogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe
aryle, ou un groupe hétéroaryle et peut en outre avoir un substituant, et deux ou plus de deux R¹ peuvent être
identiques ou différents les uns des autres.

11. Matériau semi-conducteur organique pour un dispositif à semi-conducteur organique non émetteur de lumière contenant le composé selon l'une quelconque des revendications 6 à 10 qui est représenté par la Formule (1A) et a un poids moléculaire égal ou inférieur à 3 000.
12. Solution de revêtement pour un dispositif à semi-conducteur organique non émetteur de lumière contenant le composé selon l'une quelconque des revendications 6 à 10 qui est représenté par la Formule (1A) et a un poids moléculaire égal ou inférieur à 3000.
13. Procédé de fabrication d'un transistor organique, comprenant :
une étape de préparation d'une couche active semi-conductrice par revêtement d'un substrat avec la solution de revêtement pour un dispositif à semi-conducteur organique non émetteur de lumière selon la revendication 12 et de séchage de la solution de revêtement.
14. Film semi-conducteur organique pour un dispositif à semi-conducteur organique non émetteur de lumière contenant le composé selon l'une quelconque des revendications 6 à 10 qui est représenté par la Formule (1A) et a un poids moléculaire égal ou inférieur à 3 000.
15. Procédé de synthèse d'un matériau semi-conducteur organique,
dans lequel un composé représenté par la Formule (6) ou (7) suivante est mis à réagir avec un composé représenté par la Formule (8) par chauffage en présence d'un catalyseur de métal de transition et d'un solvant organique de sorte que le composé selon l'une quelconque des revendications 6 à 10 qui est représenté par la Formule (1A) et a un poids moléculaire égal ou inférieur à 3 000 est synthétisé ;

Formule (6)



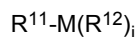
Formule (7)



dans les Formules (6) et (7),

chaque X' représente indépendamment un atome d'oxygène, un atome de soufre, ou un atome de sélénium ; et
chaque W représente indépendamment un atome d'halogène ou un groupe perfluoroalkylsulfonyloxy ;

Formule (8)



R¹¹ représente un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe aryle, ou un groupe hétéroaryle et peut en outre avoir un substituant ;

M représente du magnésium, silicium, bore, étain, ou zinc ;

chaque R¹² représente indépendamment un atome d'halogène, un groupe alkyle, un groupe alcényle, un groupe alcynyle, un groupe alcoxy, ou un groupe hydroxyle, et les R¹² peuvent être identiques ou différents les uns des autres et peuvent former un cycle ; et

i représente un nombre entier allant de 1 à 3 et est égal à une valence de M-1, ici, dans un cas où M est du bore, i peut être égal à 3.

FIG. 1

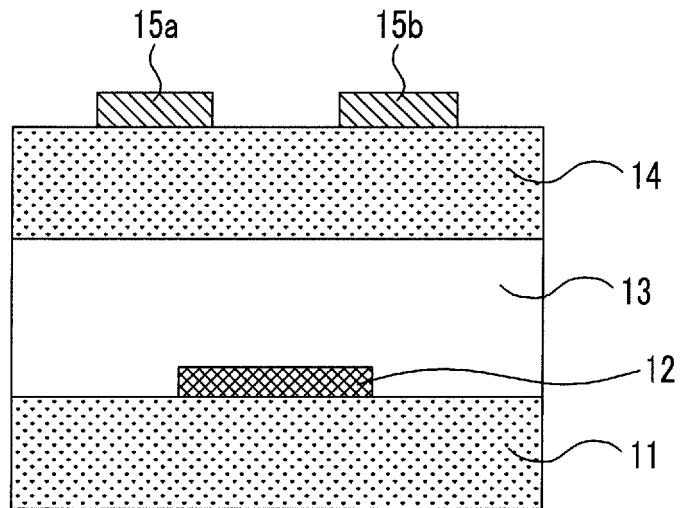


FIG. 2

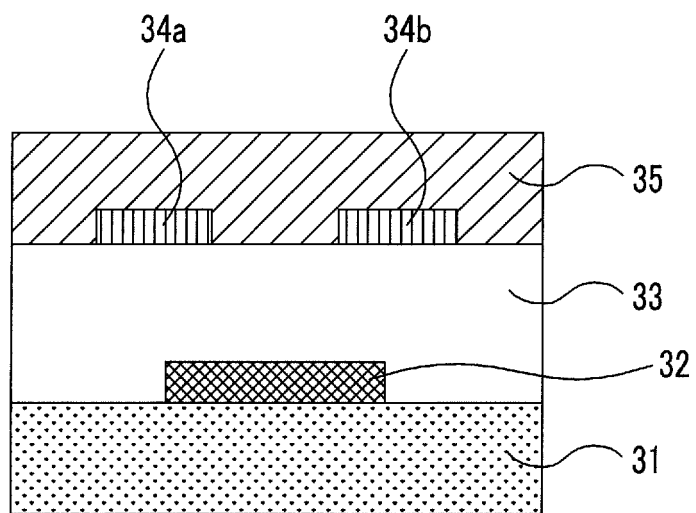


FIG. 3A

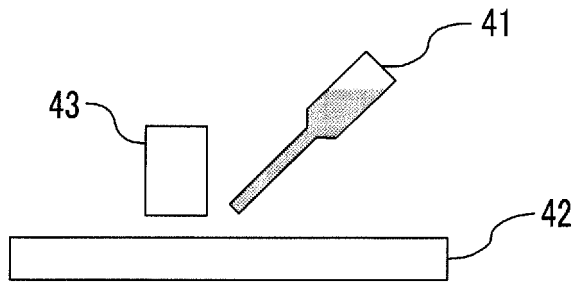


FIG. 3B

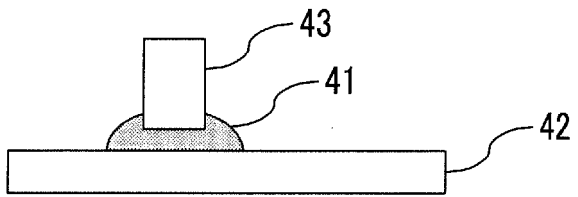


FIG. 3C

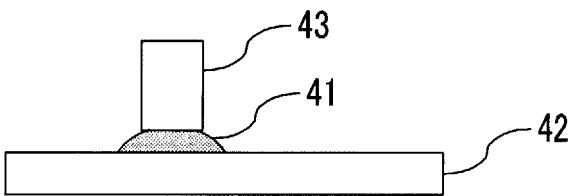


FIG. 4A

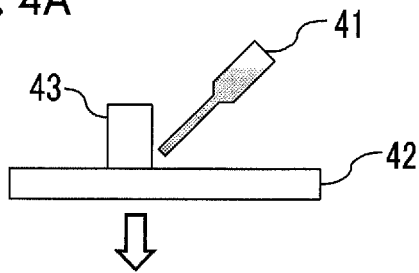


FIG. 4B1

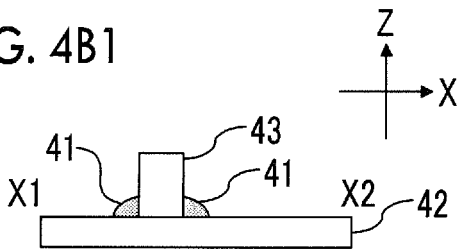


FIG. 4C

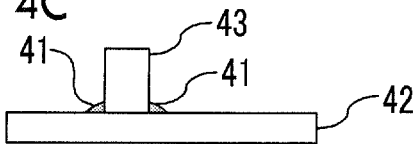
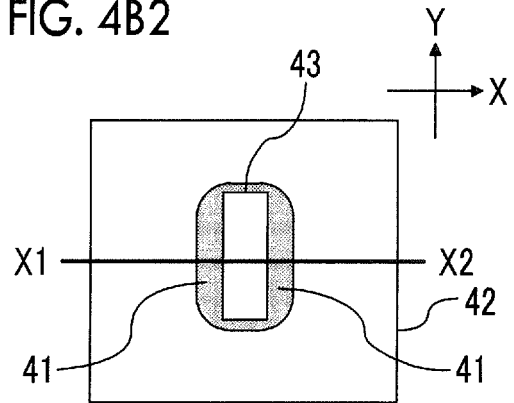


FIG. 4B2



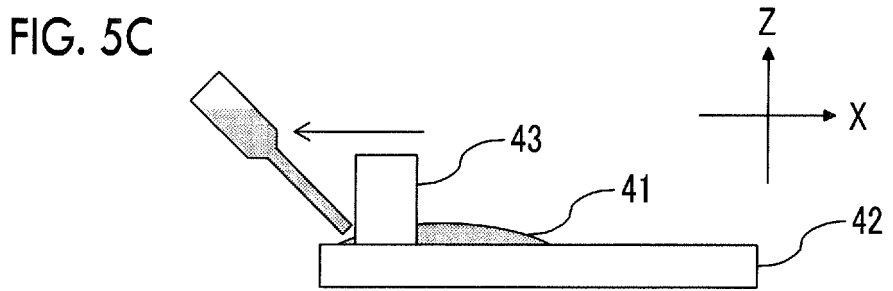
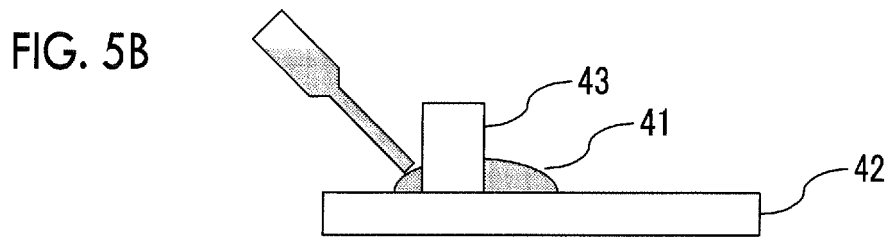
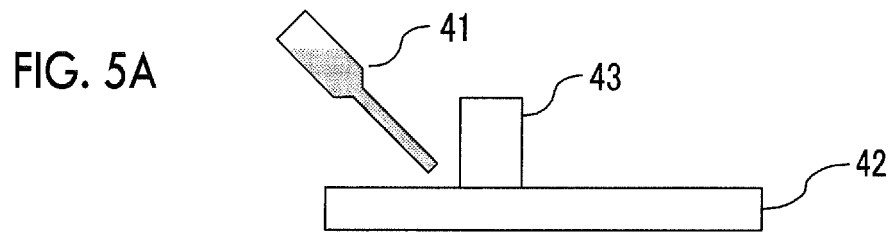
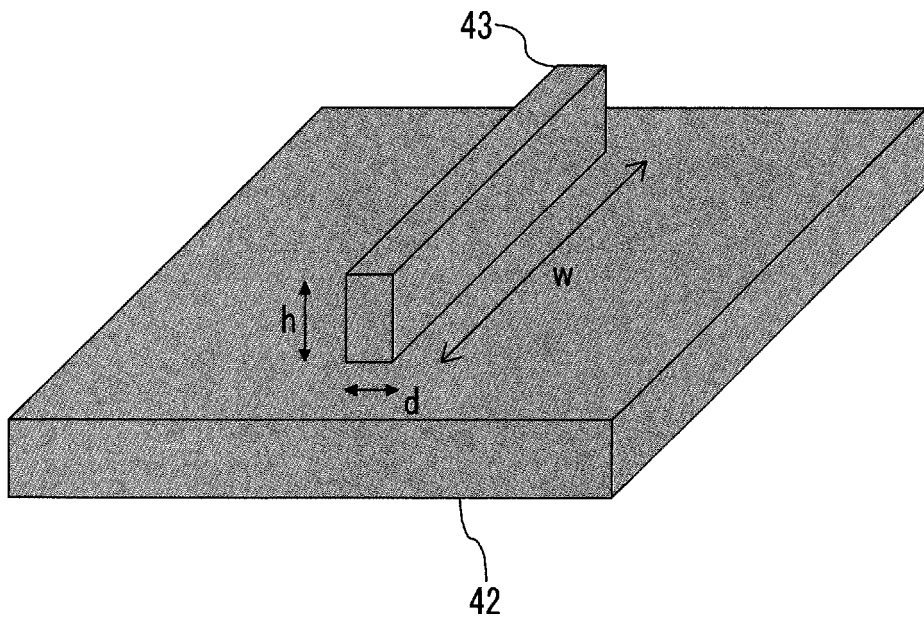


FIG. 6



REFERENCES CITED IN THE DESCRIPTION

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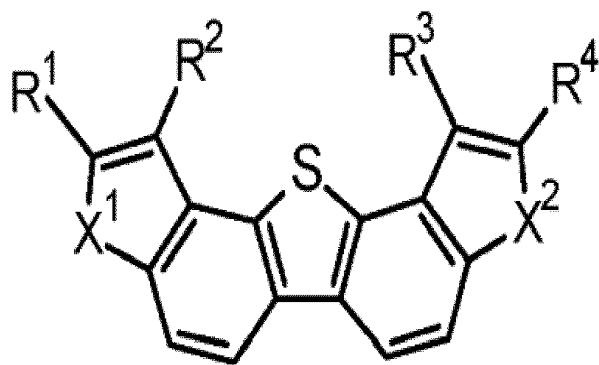
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- *Chemistry of Materials*, 2014, vol. 26, 647 [0240]
- *J. Org. Chem.*, 2005, vol. 70, 4502 [0314]

专利名称(译)	有机晶体管，化合物，用于非发光有机半导体器件的有机半导体材料，用于有机晶体管的材料，用于非发光有机半导体器件的涂布液，有机晶体管的制造方法，有机半导体膜的制造方法，有机半导体非发光有机半导体器件用薄膜和有机半导体材料的合成方法		
公开(公告)号	EP3125322B1	公开(公告)日	2020-04-15
申请号	EP2015770420	申请日	2015-03-26
[标]申请(专利权)人(译)	富士胶片株式会社 国立大学法人 东京大学		
申请(专利权)人(译)	富士胶片株式会社 东京大学		
当前申请(专利权)人(译)	富士胶片株式会社 东京大学		
[标]发明人	TSUYAMA HIROAKI NOMURA KIMIATSU USAMI YOSHIHISA FUKUZAKI EIJI KOYANAGI MASASHI KITAMURA TETSU WATANABE TETSUYA OKAMOTO TOSHIHIRO TAKEYA JUNICHI		
发明人	TSUYAMA HIROAKI NOMURA KIMIATSU USAMI YOSHIHISA FUKUZAKI EIJI KOYANAGI MASASHI KITAMURA TETSU WATANABE TETSUYA OKAMOTO TOSHIHIRO TAKEYA JUNICHI		
IPC分类号	H01L51/30 C07D493/14 C07D495/14 C07D497/14 C07D513/14 C07D517/14 C07D519/00 H01L21/336 H01L21/368 H01L29/786		
CPC分类号	C07D493/14 C07D495/14 C07D497/14 C07D513/14 C07D517/14 C07D519/00 C09B57/00 H01L51/0068 H01L51/0071 H01L51/0074 H01L51/0558 Y02E10/549 Y02P70/521 C09D5/24 H01L51/0003 H01L51/0545		
优先权	2014063111 2014-03-26 JP 2015049036 2015-03-12 JP		
其他公开文献	EP3125322A1 EP3125322A4		
外部链接	Espacenet		

摘要(译)

提供一种具有高载流子迁移率的有机晶体管，该半导体晶体管具有半导体活性层，该半导体活性层包含由下式表示的且分子量等于或小于3,000的化合物，该化合物，用于非轻型的有机半导体材料。发光有机半导体器件，用于有机晶体管的材料，用于非发光有机半导体器件的涂布液，用于制造有机晶体管的方法，用于制造有机半导体膜的方法，用于非有机半导体膜的有机半导体膜发光的有机半导体器件及其制造方法。（X表示氧，硫，硒或碲原子或NR 5；Y和Z分别表示CR 6，氧，硫，硒或氮原子或NR 7；含有Y和Z

的环为芳香族杂环 R¹和R²中的任何一个与包含Y和Z的芳族杂环或R³和R⁴中的任何一个与苯环可以通过特定的二价连接基团彼此键合；R¹，R²和 R⁵~R⁸分别表示氢原子，烷基，烯基，炔基，芳基或杂芳基；R³和R⁴分别表示烷基，烯基，炔基，芳基或杂芳基；并且m和n均为0至2的整数。)



1